CLASS 438, SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

SECTION I - CLASS DEFINITION

A. This class provides for manufacturing a semiconductor containing a solid-state device by a combination of operations wherein:

(1) no other class provides for the overall combination, and

(2) the intent is to use the electrical properties of the semiconductor in the device for at least one of the following purposes: (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

B. This class provides for a species of Class 427 operations involving:

(1) coating a substrate with a semiconductive material, or

(2) coating a semiconductive substrate or substrate containing a semiconductive region;

wherein the intent is to use the electrical properties of the semiconductor in a solid-state device for at least one of the following purposes: (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

C. This class provides for a species of Class 216 operations involving etching a semiconductive substrate or etching a substrate containing a semiconductive region, wherein the intent is to use the electrical properties of the semiconductor in a solid-state device for at least one of the following purposes:

(1) conducting or modifying an electrical current,

(2) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or

(3) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

D. This class provides for packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor, when <u>not</u> elsewhere provided, wherein there are:

(1) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor, or support (e.g., mounting, housing, lead frame, discrete heat sink, etc.),

(2) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or

(3) a step of treating an already packaged semiconductor substrate (e.g., coating, etching, etc.); if the following conditions are also met: (a) there is <u>significant</u> semiconductor chip structure (e.g., such as recited semiconductor junction, etc.) or named semiconductor device (e.g., DRAM, CMOS, EPROM, etc.), or (b) there is no significant semiconductor structure if also combined with a coating operation of this class (see B above) or etching operation of this class (see C above), and (c) the intent is to use the electrical properties of the semiconductor in a solid-state device for at least one of the following purposes: (i) conducting or modifying an electrical current, (ii) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (iii) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy;

(1) Note. When Class 438 coating (see B above) or etching operations (see C above) are <u>not</u> included, Class 29, following historical precedence, provides for processes of mounting, packaging, molding, or encapsulating of semiconductors having <u>no significant semiconductor chip structure</u> (e.g., merely recited as semiconductor chip, per se, etc.) when <u>not</u> elsewhere provided.

E. This is the generic class for operations <u>not</u> elsewhere provided for treating a semiconductive substrate or substrate containing a semiconductive region; wherein the intent is to use the semiconductor in a solid-state device for at least one of the following purposes:

(1) conducting or modifying an electrical current,

(2) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or

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(3) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

(1) Note. Lacking an indication that the semiconducting material is to be used for a purpose other than (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy; it will be assumed that the process meets the Class 438 definition.

(2) Note. For this class certain materials will be considered to be semiconductors even if there is no other indication that semiconducting properties are present. Thus, if the criteria set forth under the (1) Note is met that there is no indication that the material is to be used for a purpose other than (a), (b), or (c), the following materials are to be considered semiconductive: silicon, germanium, selenium, tellurium, gallium nitride, gallium phosphide, gallium arsenide, aluminum phosphide, aluminum arsenide, and mercury cadmium telluride.

SECTION II - LINES WITH OTHER CLASSES AND WITHIN THIS CLASS

Several classes provide for plural step operations for manufacturing semiconductor solid-state devices or components therefor. Combined operations for manufacturing semiconductor electrical devices or semiconductor-based components therefor having plural steps not encompassed by another class are proper for Class 438.

For example, while plural steps acceptable to Class 264 (e.g., injection molding and subsequent removal of flash, etc.) remain in Class 264, combinations of molding and adhesive bonding are provided for in Class 156, even though this involves multiple steps, one of which (i.e., molding) would be considered a Class 264 unit operation even if semiconductor material is involved. However, combinations of molding, adhesive bonding, and a Class 438 unit operation acting on a semiconductor substrate which is used for at least one of the following purposes: (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy, are considered proper for Class 438.

A. UNIT COATING OPERATIONS, COMBINED OPERATIONS INVOLVING COATING, AND PARTICLE BOMBARDMENT

The following search notes are intended to clarify the lines and distinctions for determining when coating operations are provided for in Class 438. Throughout this class, the term “coating” is used in the generic sense to include both surface coating and impregnation.

The unit coating operations in Class 438 may be viewed as a specie of a Class 427 process which was removed intact from Class 427 and transferred to Class 438 for the convenience of the searcher. Thus, plural step operations that were acceptable in Class 427 are now acceptable in Class 438 if the criteria for the semiconductor material as set forth hereinabove is met. Coating operations which do not meet the Class 438 definition may be classified in the classes identified in References to Other Classes, below.

B. UNIT ETCHING OPERATIONS AND COMBINED ETCHING OPERATIONS IN CLASS 438

In References to Other Classes, below, are search notes are intended to clarify the lines and distinctions for determining when an etching unit operation is provided for in Class 438. Throughout this class, the term “etching” is used in the generic sense to include the removal of a surface by chemical reaction or solvent action regardless of the composition thereof.

The unit etching operations in Class 438 may be viewed as a specie of a Class 216 process which was removed intact from Class 216 and transferred to Class 438 for the convenience of the searcher. Thus, plural step operations that were acceptable in Class 216 are now acceptable in Class 438 if the criteria for the semiconductor material as set forth hereinabove is met. Etching operations which do not meet the Class 438 definition may be found in References with Other Classes, below.

C. PACKAGING (E.G., WITH MOUNTING, ENCAPSULATING, ETC.) OR TREATMENT OF PACKAGED SEMICONDUCTOR

Packaging is a semiconductor art manufacturing term for integration, assembly, or surrounding of a semiconductive substrate (e.g., chip, die, etc.) with a permanent

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encasement, housing, capsule, or support. This is distinguished from package making found in Class 53 which is directed to preparing a manufactured product for passage through the channels of trade in a safe, convenient, and attractive condition, usually wrapped in a cover or in a container which is intended to be removed when the manufactured product is used.

Class 438 takes the following packaging or packaging related operations, if not elsewhere provided: (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor, or support (e.g., mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already packaged semiconductor substrate (e.g., coating, etching, etc.).

However, other manufacturing classes have established historic lines with Class 438 that must be considered when determining proper placement. These lines with external classes revolve around such concepts as: whether there is significant semiconductor device structure, whether there is a unit operation or a so-called "multi-step" operation, etc. The search notes in References to Other Classes, below, are intended to clarify these established lines and to alert the searcher to other classes for related searches.

D. LINE NOTES TO OTHER MANUFACTURING OPERATIONS

See References to Other Classes, below for lines clarifying the relationship of other chemical classes to Class 438. For many of the chemical classes, inclusion of metal casting, working or deforming, or fusion bonding step is <u>not</u> acceptable if combined with an operation of the chemical class.

E. LOCATION OF SEMICONDUCTOR COMPOUND, COMPOSITION, OR STOCK

Class 438 does not provide for compound, composition, or stock material produced or utilized by a Class 438 process. A process of manufacture or use of a compound or composition is usually classified with the compound or composition. The process of manufacturing a semiconductor compound or composition and the formation of a semiconductor device or semiconductor junction takes combined operations to Class 438.

Also see References to Other Classes, below, identifying this section.

F. LINE TO HEATING CLASSES

This class (438), will take the process of (a) heating of semiconductor material to modify the microstructure or electrical properties thereof, (b) combined operations involving heating of semiconductor material to modify the semiconductor structure or electrical properties when <u>not</u> provided in another class, or (c) heating of semiconductor substrates that affects only the nonsemiconductor region of the substrate when combined with other operations acceptable to Class 438 or combined with the establishment of device structure (e.g., connects, insulating regions, electrodes, etc.).

See References to Other Classes, below, identified as heating classes.

G. LINE NOTES TO ELECTRICAL CLASSES

See References to Other Classes, below.

SECTION III - REFERENCES TO OTHER CLASSES

SEE OR SEARCH CLASS:

29, Metal Working, especially subclasses 729+ for electrical device manufacturing apparatus, subclasses 829+ for the assembly of electrical components to an insulative base having a conductive path applied thereto, or formed thereon or therein (e.g., a printed circuit board). [See "Packaging (e.g., With Mounting, Encapsulating, etc.)" above]

(1) Note. When Class 438 coating (see "Unit Coating Operations, Combined Operations Involving Coating" above,) or etching operations (see "Unit Etching Operations And Combined Etching Operations") are <u>not</u> included, Class 29, subclasses 825+, following historical precedence, provides for processes of mounting, packaging, molding, or encapsulating of semiconductors having <u>no significant semiconductor chip structure</u> (e.g., merely recited as semiconductor chip, per se, etc.) when <u>not</u> elsewhere provided. If there is <u>no significant chip structure</u>, Class 29 takes as original (a) adhesive bonding combined with specified metal shaping steps or (b) adhesive bonding

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combined with mechanical joining, either broad or specific.

(2) Note. Multistep processes for packaging semiconductors having no significant semiconductor chip structure are proper for Class 156 when they claim: (a) adhesive bonding combined with shaping of nonmetals; (b) adhesive bonding combined with broad or nominally claimed metal shaping steps; or (c) adhesive bonding including steps for assembling the parts to be bonded are proper in Class 156.

53, Package Making, for passage through the channels of trade in a safe, convenient, and attractive condition, usually wrapped in a cover or in a container. In this context of trade, Class 53 provides for methods of: (a) encompassing, encasing, or completely surrounding goods or materials with a cover made from sheet stock, (b) partially encasing or surrounding goods and materials by a partial cover made from sheet stock, (c) assembling or securing a separate closure to an aperture of a preformed receptacle to complete encasement of contents, (d) depositing articles and arranging fluent materials in preformed receptacles, (e) partial or complete shaping of a cover about an article, and other related package making processes. (See "Packaging (E.g., With Mounting, Encapsulating, Etc.)" above)

(1) Note: If it cannot be perceived (a) whether the process is package making or (b) whether the process is manufacturing of a semiconductor device within or attached to a container, case, lead frame, heat sink, or enclosure as an integral part of the manufactured product; placement goes to Class 438 and Class 53 may be cross-referenced.

65, Glass Manufacturing, for processes of melting, shaping or forming, joining, or heat treating of glass. Glass is defined in the Class 65 definitions (Glossary) as an inorganic material generally including a glass former and having specific characteristics provided in the definition. Included in Class 65 is joining, per se, of glass to metal or glass. (See "Packaging (e.g., With Mounting, Encapsulating, etc.)" above)

(1) Note. Class 438 takes packaging or the packaging-related operation of semiconductor devices when glass melting, glass shaping, glass forming, or glass heat treating is combined with any coating, adhesive bonding, metal casting, metal working, or deforming, metal fusion bonding or other chemical manufacturing operation.

65, Glass Manufacturing, for processes of melting, shaping or forming, joining, or heat treating of glass. Glass is defined in the Class 65 definitions (Glossary) as an inorganic material generally including a glass former and having specific characteristics provided in the definition. It is noted that both silica and elemental silicon are also included for Class 65. Thus, melting, shaping, or fusion bonding of silicon dioxide, per se, or silicon, per se, is also considered proper for Class 65. Class 65 also takes combined operations whether preparatory or subsequent to the melting, shaping or forming, joining or heat treating of glass. Included in Class 65 is joining, per se, of glass to metal, spinning, per se, of glass fibers or joining through glass melting, per se, of glass fibers to substrates such as semiconductor substrates. (see "Line Notes To Other Manufacturing Operations," above)

(1) Note. Class 438, as the exception, takes the combination of Class 438 unit coating operation or Class 438 unit etching operation with glass melting, shaping or forming, joining, or heat treating. Moreover, Class 438 also takes the heat treating, per se, of Class 438 semiconductor material if for purposes of modifying the electrical properties thereof. Class 438 takes the mounting or packaging operation of semiconductor devices when glass melting, glass shaping, glass forming, or glass heat treating is combined with any coating, adhesive bonding, metal casting, metal working, or deforming, metal fusion bonding or other chemical manufacturing operation.

106, Compositions: Coating or Plastic, subclasses 1.05+ for metal-deposition or substrate-sensitizing compositions; subclasses 286.1+ for inorganic materials only containing at least one metal atom; subclass 286.8 for inorganic materials only; subclasses 287.1+ for silicon containing other than solely as silicon dioxide as a part of an aluminum-containing compound, and subclasses 400+ for materials or ingredients. (see "Location Of Semiconductor Compound, Composition, Or Stock" above.)

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117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefore, for processes of single crystal growth of semiconductor material upon a seed or substrate and perfecting operations combined therewith. See Class 117 definitions for examples of perfecting operations generally acceptable to Class 117. See particularly Class 117, Class Definition, (2) Note, Keywords and (3) Note, Indicative Terminology, for terms indicative of single crystal formation. Inclusion of a nonperfecting single crystal forming operation on a semiconductor substrate or producing a semiconductor product meeting the hereinabove requirements of a semiconductor material or the definition of a semiconductor substrate takes the original to Class 438, even if there is present a single crystal forming step. (Coating operation not meeting Class 438 definition)

(1) Note. When combined with single crystal formation, the following operations are acceptable in Class 438: (a) simultaneous formation of nonsingle crystalline regions intended to impart structure that will serve as a functional part of the semiconductive substrate or completed device, (b) prior or subsequent removal of a nonseed portion of the substrate in order to impart electrical device structure to the same (e.g., formation or a recess, trench, trough, ridge, mesa, stripe, etc.), or (c) prior or subsequent step acting to alter the composition of the semiconductor substrate so as to impart electrical device structure to the same.

134, Cleaning and Liquid Contact With Solids, especially subclass 1.2 and 1.3 for processes for cleaning a semiconductor substrate including the application of electrical or wave energy to the substrate. (Etching operation not meeting the Class 438 definition)

(1) Note. If the undesirable material to be removed from the semiconductor substrate resides other than on the surface thereof, the process is to be considered gettering of the substrate and thus is proper for Class 438.

148, Metal Treatment, for unit coating operations on metal, particularly subclasses 206+ wherein there is carburization or nitriding of a metal surface by chemical reaction or diffusion of an externally supplied source of carbon or nitrogen that reacts with the metal surface wherein the metal substrate remains as part of the coating and subclasses 240^+ wherein there is reactive coating of a metal substrate with an external reactant (e.g., oxygen, etc.) wherein the metal substrate remains as part of the coating. Class 148 also takes heat treatment of metallic compositions if during the heat treatment there is either a change in the internal physical structure (i.e., microstructure) or chemical properties. (Coating operation not meeting Class 438 definition)

(1) Note. Since in certain instances metallic compositions could be semiconductor material meeting the Class 438 criteria, placement will go to Class 438 over Class 148 if the material is identified or perceived as semiconductor material. If perceived, a mandatory cross is made in Class 148.

(2) Note. Reactive coating, per se, of a metal (i.e., not intended to be semiconductive) area on a semiconductive substrate (i.e., meeting the Class definition of semiconductor substrate in the Glossary) is original in Class 438. A mandatory cross is made in Class 148 if the only step is reactive coating of a metal portion of a semiconductive containing substrate.

(3) Note. Combination of Class 148 heat treatment of a metal substrate to modify or maintain the chemical property or microstructure of the metal with (a) additional manufacturing of semiconductor device structure or (b) with a Class 438 <u>coating</u> or etching operation takes the original to Class 438.

148, Metal Treatment, subclasses 33.1+ for semiconductor stock which must be essentially homogeneous and have at least two contiguous layers differing in the number of unbound electrons and/or differing in energy gap levels, which exhibit a junction between the layers. (see “Location of Semiconductor Compound, Composition, or Stock” above.)

148, Metal Treatment, for processes of heat treating metals. Class 148 takes heat treatment of metallic compositions if during the heat treatment there is either a change in the internal physical structure (i.e., microstructure) or chemical properties. Since in certain instances

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metallic compositions could be semiconductor material meeting the Class 438 criteria, placement will go to Class 438 over Class 148 if the material is identified or perceived as semiconductor material. If perceived, a mandatory cross is made in Class 148. (heating class)

156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 60 through 338 for processes of adhesively bonding and subclasses 701-719 and 930-932 for processes of delaminating, per se, while retaining identity as semiconductive. Multistep processes for packaging semiconductors having no significant semiconductor chip structure are proper for Class 156 when claiming (a) adhesive bonding combined with shaping of nonmetals, (b) adhesive bonding combined with broad or nominally claimed metal-shaping steps, or (c) adhesive bonding including steps for assembling the parts to be bonded. An adhesive bonding unit operation for packaging or mounting operations on semiconductor devices goes as original to Class 156. Adhesive bonding combined with Class 438 coating of a semiconductor substrate or Class 438 etching of a semiconductor substrate places the original in Class 438. (See Packaging (e.g., With Mounting, Encapsulating, etc.) above).

174, Electricity: Conductors and Insulators, subclasses 15.1 through 16.3 for fluid cooling of electrical conductors or insulator, subclasses 50-64 for housings with electric devices or mounting means, and subclasses 250-268 for printed circuit devices.

204, Chemistry: Electrical and Wave Energy, particularly subclasses 192.1 through 192.37 for sputter coating operations involving semiconductor material or substrates including a semiconductor region, even if the intent is to use the semiconductor material for (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy - Class 204 will take combinations of sputter coating with other chemical treating operations that involve (a) preparatory treatment of the substrate (e.g., etching, cleaning, etc.) or (b) subsequent perfecting treatment of the applied coating with the following exception noted (coating operation not meeting Class 438 definition); and subclasses 192.32-192.37, for sputter etching operations on semiconductor material and semiconductor containing substrates, even if the semiconductor is intended for electrical purposes - simultaneous sputter etching and chemical etching (e.g., as when utilizing a mixture of argon and halide gas, etc.) go as original in Class 204 (etching operation not meeting the Class 438 definition).

(1) Note. Creation of semiconductor structure (e.g., semiconductor active region, semiconductor junction, etc.) by subsequent treatment steps, even if limited to the Class 204 applied coating, will go to Class 438. Any subsequent operation that affects the substrate is not provided in Class 204 and is proper in Class 438. However, heat treatment of the Class 204 coating that causes interdiffusion limited to the interfacial region to perfect the bonding of the coating to the substrate is proper for Class 204.

(2) Note. Creation of semiconductor structure (e.g., semiconductor active region, semiconductor junction, etc.) by steps subsequent to sputter etching will go to Class 438.

205, Electrolysis: Processes, Compositions Used Therein, and Methods of Preparing the Compositions, particularly subclass 123, 124, and 157 for electrolytic coating operations on semiconductor or semiconductor devices (coating operation not meeting Class 438 definition), subclasses 334-639 for electrolytic synthesis of material, such as silicon, by passing an electrical current through a fused material, and subclass 656 for electrolytic erosion of a workpiece of non-uniform internal electrical characteristics (etching operation not meeting the Class 438 definition). Class 205 will take combinations of electrolytic coating with other chemical treating operations that involve (a) preparatory treatment of the substrate (e.g., etching, cleaning, etc.) or (b) subsequent perfecting treatment of the applied coating with the following exception noted (coating operation not meeting Class 438 definition).

216, Etching a Substrate: Processes, for chemical etching processes and perfecting operations therefor, including lithos:graphic steps, of semiconductor material that is to be utilized for nonelectrical properties. (Etching operation not meeting the Class 438 definition)

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(1) Note. This class provides for a species of Class 216 operations involving etching a semiconductive substrate or etching a substrate containing a semiconductive region; wherein the intent is to use the electrical properties of the semiconductor in a solid-state device for at least one of the following purposes: (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

(2) Note. Generic claims with a sole claimed specie of etching for Class 216 goes as original to Class 216. Generic claims with a sole disclosed specie of etching for Class 438 goes as original in Class 438. Generic claims with plural claimed etching specie wherein at least one of the claimed species does not belong in Class 438 goes as original in Class 216. Generic claims with plural disclosed etching specie one of which does not belong in Class 438 goes to Class 216 as original. Generic claims with no material specie claimed or disclosed goes as original in Class 216. When there is no generic claim and plural separately claimed etching specie, wherein at least one claim of which is Class 216 and one claim of which is Class 438, placement goes as original to Class 438 with a mandatory cross-reference to Class 216.

219, Electric Heating, subclasses 78.01+ for a process and apparatus for bonding by electrical current and pressure, and appropriate subclasses for electric heating of material, per se. However, inclusion of the criteria for Class 438 as set forth hereinabove takes the original to Class 438 even when electric heating is involved. (heating class)

228, Metal Fusion Bonding, appropriate subclasses for a process of fusion bonding and additional operations which are considered to be ancillary to the bonding (preheating, positioning, pretinning, etc.) of a semiconductive substrate; especially note subclass 123.1 and 179.1+. [See "Packaging (e.g., With Mounting, Encapsulating, etc.)" above]

250, Radiant energy, for methods <u>not</u> elsewhere provided of (a) using, generating, controlling, or detecting radiant energy, (b) combinations including such methods, and (c) subcombinations thereof. Particularly, see subclasses 492.2+ for processes of irradiation of semiconductor devices with no indication as to what occurs to the substrate. Class 250, subclasses 492.2+' generally relates to processes of exposing substrates to ion bombardment utilizing apparatus of Class 250 when limited to operating the apparatus in apparatus terms. Class 250 is also the generic home for processes of exposing substrates to ion bombardment. However, Class 438 provides for ion implantation of semiconductive substrate or substrate containing a semiconductive region and also ion implantation throughout the material mass to produce semiconductive material or to modify the semiconductive material. (Coating operation not meeting Class 438 definition)

250, Radiant Energy, for methods <u>not</u> elsewhere provided, of (a) using, generating, controlling, or detecting radiant energy, (b) combinations including such methods, and (c) subcombinations thereof. Particularly, see subclasses 492.2+ for processes of irradiation of semiconductor devices with no indication as to what occurs to the substrate. Class 250 subclasses 492.2+' generally relates to processes of exposing substrates to ion bombardment utilizing apparatus of Class 250 when limited to operating the apparatus in apparatus terms. Class 250 is also the generic home for processes of exposing substrates to ion bombardment. However, Class 438 takes chemically reactive ion etching of semiconductive substrate or substrate containing semiconductive region. (Etching operation not meeting the Class 438 definition)

250, Radiant Energy, for heating invisible radiant energy; subject matter of Class 438, per se, when no function other than heating is attributed to the process and for methods <u>not</u> elsewhere provided, of (a) using, generating, controlling, or detecting radiant energy, (b) combinations including such methods, and (c) subcombinations thereof. Particularly, see subclasses 492.2+ for processes of ion bombardment or irradiation of semiconductor devices, with no indication as to what occurs to the substrate. (heating class)

252, Compositions, for (a) subclasses 62.3+ for semiconductor compositions which have been uniformly doped or otherwise specialized for

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use as one layer which when combined with another such layer would provide an interface exhibiting barrier layer properties (e.g., as exists in Class 148, subclasses 33 through 33.6, stock wherein there is a semiconductor junction, etc.) and (b) subclasses 500+ for electrical conductive compositions. Also see the cross-reference art collection in Class 252, subclasses 950+' for doping agent source materials. (see "Location Of Semiconductor Compound, Composition, Or Stock" above.)

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), for active solid-state electronic device structure, per se. Subject matter may include one or more such devices combined with contacts or leads, or structures configured to be tested on a semiconductor chip, or merely semiconductor material without contacts or leads where the sole disclosed use is an active solid-state device. This subject matter does not include active solid-state devices combined with significant circuits. (electrical class)

264, Plastic and Nonmetallic Article Shaping or Treating: Processes, for a process (and steps perfecting same) of forming a composite by shaping a plastic or nonmetallic wherein a semiconducting containing preform is within a mold during the shaping operation (e.g., encapsulating, etc.). (See "Packaging (e.g., With Mounting, Encapsulating, etc.)" above)

361, Electricity: Electrical Systems and Devices, subclasses 679.01 through 679.61 for housing and mounting assemblies for electronic devices and components, and subclasses 736+ and 752+ for modules for printed circuits or housing or chassis for printed circuit boards. (electrical class).

376, Induced Nuclear Reactions: Processes, Systems, and Elements, particularly subclass 183 for a process of neutron bombardment, per se, of semiconductive material containing an element which is converted to a desired dopant by nuclear transmutation. Any combination of operations that goes beyond formation of the transmutated doped semiconductor material, per se, goes as original to Class 438 if it meets the criteria of the intent to use the electrical properties of the semiconductor in a solid-state device as set forth by the Class 438 definition. (Coating operation not meeting Class 438 definition)

376, Induced Nuclear Reactions: Processes, Systems, and Elements, subclasses 320+ for the direct conversion of the energy produced in a nuclear reaction into an electrical output by a one-step process or apparatus for accomplishing such a one-step process. (electrical class)

378, X-ray or Gamma Ray Systems or Devices, especially subclasses 34+ for X-ray or gamma-ray lithography. (electrical class)

382, Image Analysis, especially subclass 145 for a process limited to image analysis per se in manufacturing of an integrated circuit. However, inclusion of subject matter for Class 438 remains with Class 438 even if there is a step of image analysis.

385, Optical Waveguides, particularly, subclass 14 for a laser in integrated optical circuit, subclasses 129+ for a planar optical waveguide, and subclasses 141+ for a waveguide having a particular optical characteristic modifying chemical composition. The (13) Note of Class 385 indicates that miscellaneous manufacturing of optical wave guide devices <u>not</u> elsewhere provided are in Class 385. Thus, if the manufactured article is a semiconductor device, a Class 438 process controls over the Class 385 process even if an optical fiber is part of the device. (electrical class)

420, Alloys or Metallic Composition, for alloys or metallic compositions that may also exhibit semiconductor properties (e.g., gallium arsenide, etc.). (see "Location Of Semiconductor Compound, Composition, Or Stock" above.)

423, Chemistry of Inorganic Compounds, appropriate subclasses for inorganic compounds or elements used in the manufacture of semiconductor devices. (see "Location of Semiconductor Compound, Composition, or Stock" above.)

427, Coating Processes, for coating operations provided for in that class, particularly subclasses 457+ for a process of treating a coating with radiant energy; subclasses 487+ for polymerization of applied coating utilizing direct application of electrical, magnetic, wave, or particulate energy; subclasses 523+ for ion plating or ion implanting; subclasses 532+ for pretreatment of a substrate or posttreatment of a coated substrate utilizing electrical, magnetic, wave, or particulate energy; subclasses 569+ for deposition coating processes utilizing plasma; subclasses 580+ for deposition coating processes utilizing electrical discharge; sub-

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class 581 for coating processes utilizing chemical liquid deposition; subclass 582 for coating processes utilizing photo-initiated chemical vapor deposition; subclasses 585+ for coating processes utilizing chemical vapor deposition; subclass 591 for deposition coating utilizing induction or dielectric heating; subclasses 592+ for deposition coating utilizing resistance heating; subclasses 595+ for deposition coating utilizing electromagnetic or particulate radiation; subclasses 598+ for deposition coating utilizing magnetic field or force; subclass 600 for deposition coating utilizing sonic or ultrasonic energy. (Coating operation not meeting Class 438 definition)

(1) Note. Class 438 provides for a specie of Class 427 operations involving (a) coating a substrate with a semiconductive material or (b) coating a semiconductive substrate or substrate containing a semiconductive region; and wherein the intent is to use the electrical properties of the semiconductor in a solid state device for at least one of the following purposes: (i) conducting or modifying an electrical current, (ii) storing electrical energy for subsequent discharge within a microelectronic integrated circuit, or (iii) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy.

(2) Note. Generic claims with a sole claimed specie of coating for Class 438 goes as original to Class 438. Generic claims with a sole disclosed specie of coating for Class 438 goes as original in Class 438. Generic claims with plural claimed coating species wherein at least one of the claimed species does not belong in Class 438 goes as original in Class 427. Generic claims with plural disclosed coating species one of which does not belong in Class 438 goes to Class 427 as original. Generic claims with no material species claimed or disclosed goes as original in Class 427. When there is no generic claim and plural separately claimed coating specie, wherein at least one claim of which is Class 427 and one claim of which is Class 438, placement goes as original to Class 438 with a mandatory cross-reference to 427.

428, Stock Material or Miscellaneous Articles, appropriate subclasses for semiconductor stock material defined in terms of composition and structure, especially subclass 620. (see "Location of Semiconductor Compound, Composition, or Stock" above.)

429, Chemistry: Electrical Current Producing Apparatus, Product, and Process, especially subclass 7 for a combination including a nonbattery electrical component electrically connected within a cell casing other than testing or indicating components. (electrical class)

430, Radiation Imagery Chemistry: Process, Composition, or Product Thereof, particularly for initial lithos:graphic processes in semiconductor manufacture limited to (a) exposure imaging and developing and including preparatory operations to the exposure (e.g., as coating to form the resist, etc.) or (b) developing, per se, of subject matter of Class 430 substrates. When Class 430 exposure, imaging or developing are combined with etching or coating of a semiconductor substrate for purposes other than masking and commensurate with the Class 438 definition for manufacture of a semiconductor device as set forth hereinabove, the combination goes as original to Class 438 with the following exception noted. (Coating operation not meeting Class 438 definition)

(1) Note. Since Class 430 provides for processes of (a) coating, per se, of substrates, with a composition to produce a product to be used for electric or magnetic imagery and (b) processes of coating, per se, of substrate with a photosensitive composition for use in radiation imagery, coating or etching of semiconductor material limited to forming a product <u>intended</u> to be used for electric, magnetic, or radiation imagery is original in Class 430.

(2) Note. Although technically classifiable as an original in Class 438 according to the above paragraph, any multistep process involving significant Class 430 operations as a subcombination of the overall process should be cross-referenced to Class 430.

430, Radiation Imagery Chemistry: Process, Composition, or Product Thereof, particularly for initial lithos:graphic processes in semiconductor manufacture limited to (a) exposure imaging and developing and including preparatory operations to the exposure (e.g., as coating to

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form the resist, etc.) or (b) developing, per se, of subject matter of Class 430 substrates. When Class 430 exposure imaging or developing are combined with etching or coating of a semiconductor substrate commensurate with the Class 438 definition for manufacture of a semiconductor device as set forth hereinabove, the combination goes as original to Class 438 with the following exception noted. (Etching operation not meeting the Class 438 definition)

(1) Note. Since Class 430 provides for processes of (a) coating, per se, of substrates, with a composition to produce a product to be used for electric or magnetic imagery and (b) processes of coating per se of substrate with a photosensitive composition for use in radiation imagery, coating or etching of semiconductor material limited to forming a product intended to be used for electric, magnetic, or radiation imagery is original in Class 430.

(2) Note. Although technically classifiable as an original in Class 438 according to the above paragraph, any multistep process involving significant Class 430 operations as a subcombination of the overall process should be cross-referenced to Class 430.

432, Heating, for generic heating processes. However, inclusion of the criteria for Class 438 as set forth hereinabove takes the original to Class 438 even when generic heating is involved. (heating class)

439, Electrical Connectors, appropriate subclasses for features related or analogous to electrical contact or housing features of active solid-state devices (e.g., subclasses 271+ for sealing elements or subclasses 449+ for stress relief means for conductor to terminal joint. (electrical class)

501, Compositions: Ceramic, appropriate subclasses for ceramic compositions used in semiconductor devices. (see "Location of Semiconductor Compound, Composition, or Stock" above.)

505, Superconductor Technology: Apparatus, Material, Process, particularly subclass 330 for processes of manufacturing from high temperature (i.e., above 30 degrees Kelvin) superconductive material (a) superconductor devices or (b) semiconductor devices having superconductive components or connect lines. (see "Line Notes To Other Manufacturing Operations," above)

SECTION IV - GLOSSARY

Listed below are: (1) a compilation of acronyms, abbreviations, and technological terms pertaining to solid-state electrical devices, manufacturing processes, and related apparatus and compositions useful therefor and (2) the meaning to be given to the various "art" terms appearing in this class. These latter terms, some of which have been included in the glossary below, are the same as that generally accepted or in common usage. However, certain terms employed in this class and also included below have been assigned definitions which may be more restrictive or different from those in common usage since these terms are being utilized for distinguishing this class over other classes of related art.

A-SI

Amorphous silicon

ACT

Acoustic charge transport

ADC

Analog-to-digital converter

AES

Auger electron spectroscopy

ALE

Atomic layer epitaxy

ALEP

Angle-lapping edge profilometry

AMD

Active matrix display

AMG

Alternative-metal, virtual-ground (metallization)

APCVD

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Atmospheric-pressure CVD

APD

Avalanche photodiode

ARC

antireflective coating

ASG

Arsenosilicate glass

BBCO

Barium bismuth copper oxide (a HTSC)

BBD

Bucket brigade device

BBL

Buried bit-line

BED

Band edge discontinuity

BH

Buried heterostructure

BHF

Buffered hydrofluoric acid

BIC

Breakdown of insulator for conduction

BICFET

Bipolar inversion channel FET

BICMOS

Integrated bipolar and CMOS

BIMOS

Integrated bipolar and MOSFET

BJT

Bipolar junction transistor

BKBO

Barium potassium bismuth oxide (a HTSC)

BLM

Ball limiting metallization

BMD

Bulk micro defect

BOE

Buffered oxide etch

BOX

Buried oxide

BOXES

Buried oxide with etch stop

BPSG

Borophosphosilica glass

BPTEOS

borophosphoTEOS

BSD

Back side damage

BSE

buried storage electrode

BSG

Borosilica glass

BSQ

Bias sputter quartz

BST

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Barium strontium titanate

CAIBE

Chemically assisted ion beam etching

CBIC

Complementary bipolar IC

CBKR

Cross bridge Kelvin resistor (test structure)

CCB

Controlled collapse bonding

CCC

Corrugated capacitor cell

CCD

Charge coupled device

CDE

Chemical dry etching

CDI

Collector diffusion isolation

CEL

Contrast enhancement layer

CER

Contact end resistor (test structure)

CERDIP

ceramic DIP

CHANSTOP

channel stop isolation structure

CHEMFET

Chemically sensitive FET

CHL

Current hugging logic

CID

Charge injection device

CLSEG

Confined lateral SEG

CML

Current mode logic (i.e., ECL)

CMOS

Complementary (NMOS and PMOS) FETs

CMP

chemical-mechanical polishing/planarization

COB

(a) chip-on-board or (b) capacitor over bit-line

COD

Catastrophic optical damage

COG

Chip-on-glass

COMFET

Conductivity modulation FET (i.e., IGBT)

CSBH

Channeled substrate buried heterostructure

CSL

Coherent superlattice

CTD

Charge transfer device

CTSL

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Coherent tilted superlattice

CVD

Chemical vapor deposition

CZ

Czoshralski (melt pulling)

DADBS

diacetoxyditertiarybutoxysilane

DADIS

diacetoxydiisopropoxysilane

DBR

distributed Bragg reflector

DCG

dichromated gelatin

DCFL

direct-coupled FET logic

DCS

dichlorosilane

DDE

double diffused epitaxy

DDI

deep dielectric isolation

DEIS

dual electron injection structure

DEZ

diethylzinc

DFB

distributed feedback (laser)

DH

double-hetero

DHBT

double-hetero bipolar transistor

DHF

dilute hydrofluoric acid

DI

dielectric isolation

DIBL

drain induced barrier lowering

DIET

dielectrically encapsulated trench capacitor

DIP

dual-in-line package

DLP

double layer polysilicon

DLTS

deep level transient spectroscopy

DMAH

dimethylaluminumhydride

DMD

(a) depletion mode device (also D-mode or D-type) or (b) deformable mirror device

DMOS

double diffused MOS

DMS

dilute magnetic semiconductor

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DOES

doublehetero optoelectronic switch

DRAM

dynamic random-access memory

DSP

double stacked capacitor

DTL

diode-transistor logic

DUF

diffusion under film

DUT

device under test

DUV

deep ultraviolet

DZ

denuded zone

-E-

EAROM

electrically alterable read-only memory

EB

(a) extrinsic base or (b) electron beam

EBES

electron beam exposure system

EBIC

electron beam induced current

EBL

electron beam lithography

ECL

emitter coupled logic

ECR

electron cyclotron resonance

EDP

ethylene-diamine-pyrocatechol etchant

EDTA

ethylenediaminotetraacetic acid

EELS

electron energy loss spectroscopy

EEPROM

electrically erasable programmable read-only memory

EFG

edge-defined film-fed growth (also EDFFG or EDFG)

EG

extrinsic gettering

EGSI

electronic-grade silicon

EL

electroluminescent

ELO

epitaxial lateral overgrowth

EMD

enhancement mode device (also E-mode or E-type)

EMI

electromagnetic interference

EMP

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electron microprobe

EPB

epoxidated polybutadiene (an EB resist)

EPD

etch pit density

EPI

epitaxial (single crystalline) layer

EPP

ethylene-piperidine-pyrocatechol etchant

EPR

electron paramagnetic resonance

EPROM

erasable programmable read-only memory

EPS

effective punchthrough stopper

EPW

etchant mix of ethylenediamine, pyrocatechol, and water

ESCA

electron spectroscopy for chemical analysis

ESD

electrostatic discharge

ESR

(a) equivalent series resistance or (b) electron spin resonance

FAMOS

floating-gate avalanche-injection MOS

FASIC

folded bit-line adaptive sidewall isol. capacitor cell

FCT

field controlled thyristor

FEC

floating electrode capacitor

FED

field emission device

FET

field effect transistor

FIB

focused ion beam

FIPOS

full isolation by porous oxidized silicon

FLOTOX

floating gate tunnel oxide

FOX

field oxide

FPD

field programmable device

FPGA

field programmable gate array

FTIR

Fourier transform infrared spectroscopy

FUROX

fully recessed oxide isolation

GDMS

glow discharge mass spectroscopy

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GILD

gas immersion laser doping

GRIN-SCH

graded index separate confinement heterostructure

GTO

gate turn-off

HBT

heterojunction bipolar transistor

HDC

high dielectric constant

HDI

high density interconnects

HDMI

high density multilayer interconnects

HEMT

high electron mobility transistor (Hetero MESFET)

HET

hot electron transistor (bipolar)

HI-C

high capacitance

HIC

hybrid integrated circuit

HIMOS

(see COMFET)

HIPOX

high pressure oxidation

HMDS

hexamethyldisilizane

HNA

hetchant mix of hydrofluoric, nitric, and acetic acids

HPSC

half-V_{cc}sheath plate capacitor

HTO

high temperature oxide

HTSC

high temperature superconductor

IB

(a) intrinsic base or (b) ion beam

IBD

ion beam deposition

IC

integrated circuit

ICP

inductively coupled plasma

IG

intrinsic gettering

IGBT

insulated gate bipolar transistor (e.g., COMFET, HIMOS)

IGFET

insulated gate field effect transistor

IID

impurity induced disordering

I^2L

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integrated injection logic

IJP

ink jet printhead

ILB

inner lead bonding

ILD

interlayer dielectric

IMMA

ion microprobe mass analysis

IMPATT

impact ionization avalanche transist time (diode)

INS

intrinsic nondoped semiconductor

IR

infrared

ISFET

ion sensitive FET (i.e., CHEMFET)

ITO

indium tin oxide (a TCO)

IVEC

isolation vertical capacitor cell

JFET

junction field effect transistor (junction gate)

JOFET

Josephson junction field effect transistor

JTE

junction termination extension

KMER

Kodak metal etch resist

KPR

Kodak photo resist

KTFR

Kodak thin film resist

LAGB

low-angle grain boundary

LATID

large angle tilt implant drain

LB

(a) Langmuir-Blodgett or (b) laser beam

LCCD

leadless ceramic chip carrier

LCD

liquid crystal display

LDCC

leaded ceramic chip carrier

LDD

lightly doped drain

LEC

liquid encapsulated Czoshralski

LED

light emitting diode

LEED

low-energy electron diffraction

LEK

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liquid encapsulated Kyropoulus

LOCOS

local oxidation of silicon

LOPED

lift-off using edge detection

LPCVD

low-pressure chemical vapor deposition

LPE

liquid phase epitaxy

LRP

limited reaction processing

LSI

large scale integration

LSSL

lateral surface superlattice

LST

logic service terminal

LTCC

low temperature co-fired ceramic

LTG

low temperature growth

LTO

low temperature oxidation

MBE

molecular beam epitaxy

MCZ

magnetic Czoshralski

MCM

multichip module

MCT

(a) MOS controlled thyristor or (b) HgCdTe

MEM

micro-electromechanical

MESFET

metal semiconductor FET (Schottky gate)

MF^3R

modified fully-framed fully-recessed isolation

MGSI

metallurgical-grade silicon

MIM

metal-insulator-metal

MISFET

metal insulator semiconductor IGFET

MLEC

magnetic LEC

MLC

multilayer ceramic

MLO

multilayer oxide

MLR

multilayer resist

MMA

methyl methacrylate

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MMIC

monolithic microwave integrated circuit

MNOS

metal nitride/oxide IGFET

MOCVD

metal organic chemical vapor deposition

MODFET

modulation doped MESFET (i.e., HEMT)

MOMOM

metal-oxide-metal (tunnelling device)

MOSFET

metal oxide semiconductor IGFET

MQW

multiquantum well

MTF

mean time to failure

MTL

merged transistor logic (i.e., I^2L)

NDC

negative differential conductivity

NEA

negative electron affinity (e^-emitter)

NMA

N-methyl-acetamide

NMOS

n-channel MOSFET

NMP

n-methyl-pyrrolidone

NOVOLAK

Thermoplastic phenol-formaldehyde used as photoresist

NPN

(bipolar transistor)

NRD

nitridation retarded diffusion

NSAG

nonself-aligned gate

NTD

neutron transmutation doping

NVRAM

nonvolatile RAM

OBG

optical band gap

ODE

orientation dependent etching

OED

oxidation enhanced diffusion

OEIC

optoelectronic integrated circuit

OF

orientation flat

OISF

oxidation induced stacking fault

OMCVD

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organometallic CVD

OMCT

octamethylcyclotetrasiloxane

OMVPE

organometallic VPE

ORD

oxidation retarded diffusion

ORL

optical return loss

OSA

optical subassembly

OSF

(see OISF)

OTCR

over-the-cell routing

OTP

one-time programmable

OXSEF

oxygen-doped silicon epitaxial film

PAC

photoactive compound

PAP

peel apart

PBG

photonic band gap

PBL

polybuffered LOCOS

PBM

planarization blocking mask

PBN

pyrolytic boron nitride

PBT

permeable base transistor

PCB

printed circuit board

PCE

photoconductive element

PEB

postexposure baking

PECVD

plasma enhanced chemical vapor deposition

PEP

photo-engraving process

PFT

peeled film technology

PGA

(a) pin-grid array or (b) programmable gate array

PGMA

poly(glycidyl methacrylate) (an EB resist)

PHS

plated heat sink

PIC

photonic integrated circuit

PID

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programmable interconnect device (fuse/antifuse)

PIN

P-type layer, intrinsic layer, N-type layer

PIQ

thermosetting polyimide resin

PLA

programmable logic array

PLCC

plastic leaded chip carrier

PLDD

profiled LDD

PLM

pad limiting metallurgy

PLZT

lead lanthanate zirconate titanate

PMMA

polymethylmethacrylate

PMOS

p-channel MOSFET

PNP

(bipolar transistor)

POLYCIDE

polycrystalline silicide

POLYSI

polycrystalline silicon

PPL

poly pad LOCOS

PR

photoresist

PROM

programmable read only memory

PROPS

planarization with resist/oxide and polysilicon

PSD

photosensitive diode or dielectric

PSG

phosphosilica glass

PTC

positive temperature coefficient

PTH

plated through-hole

PUT

programmable unijunction transistor

PVD

physical vapor deposition

PWB

printed wiring board

PZT

lead zirconate titanate

QE

quantum efficiency

QFP

quad flat package

QUIP

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quad-in-line package

QW

quantum well

QWIP

quantum well infrared photodetector

RAM

random access memory

RBS

Rutherford backscattering

RBT

resonant tunneling bipolar transistor

RCT

reverse conducting thyristor

RED

radiation enhanced diffusion

RESURF

reduced surface field

RETT

resonant electron transfer triode

RF

radiofrequency

RHEED

reflected high energy electron diffraction

RHET

resonant tunneling hot electron transistor (bipolar)

RIBE

reactive ion beam etching

RIE

reactive ion etching

RISC

reduced instruction set computing

RMS

refined metallurgical silicon

ROI

recessed oxide isolation

ROM

read only memory

ROX

recessed oxide

RTA

rapid thermal anneal

RTP

rapid thermal processing

S**A**LICIDE

self-aligned s**i**licide

SAG

self-aligned gate

SAW

surface acoustic wave (pressure sensitive device)

SBD

Schottky barrier diode

SBH

Schottky barrier height

SBS

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silicon bilateral switch

SCCM

standard cubic centimeter per minute

SCM

single chip module

SCR

silicon controlled rectifier

SDFL

Schottky diode FET logic

SDHT

selectively doped heterostructure transistor (e.g., HEMT)

S-DIP

shrink DIP

SEED

self-enhanced electro-optical devices

SEG

selective epitaxial growth

SEL

(a)surface emitting laser or (b)state excitation by light

SELFOX

selective epitaxial layer field oxidation

SEM

scanning electron microscopy

SEOT

self-aligned epitaxy over trench

SEPOX

selective polysilicon oxidation

SER

soft error rate

SFFT

superconducting flux flow transistor

SGT

surrounding gate transistor

SI

silicon

SI

semi-insulating

SICOS

sidewall base contact structure

SILO

sealed interface local oxidation

SIMOX

separation by implanted oxygen

SIMS

secondary ion mass spectrometry

SIP

single-in-line package

SIPOS

semi-insulating polycrystalline oxygen-doped silicon

SIT

(a)static induct. thyristor or (b)static induct. trans.

SLM

spatial light modulator

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SLS

strained layer superlattice

SLT

solid logic technology

SMT

surface mount technology

SOG

spin-on glass

SOI

silicon on insulator

SOIC

small outline IC package

SOJ

small outline J-lead package

SOS

silicon on sapphire

SPE

solid phase epitaxy

SPOT

self-aligned planar oxidation technology

SPT

substrate plate trench capacitor

SQUID

superconductive quantum interference device

SRAM

static random access memory

SRO

stress relief oxide

SSDP

simultaneous single/polycrystalline deposition

SSI

small scale integration

SST

(a)super self-alignment tech. or (b)sealed sidewall tech.

STT

stacked transistor capacitor cell

SUBHET

superconducting base hot electron transistor

SUBSIT

superconducting base semiconductor isolated transistor

SWAMI

sidewall masked isolation

TAB

tape automated bonding

TAT

turn around time

TBES

tritertiarybutoxyethoxysilane

TBCO

thallium bismuth copper oxide (a HTSC)

TCE

trichloroethylene

TCM

thermal conduction module

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TCO

transparent conductive oxide

TDDB

time dependent dielectric breakdown

TEC

thermoelectric cooler

TED

transient enhanced diffusion

TEG

(a) triethylgallium or (b) test element group

TEM

transmission electron spectroscopy

TEOS

tetraethylorthosilane

TFR

thin film resistor

TFT

thin film transistor

TGZM

temperature gradient zone melting

TH

through-hole

TIBA

triisobutylaluminum

TLTR

transmission line tap resistor (test structure)

TMA

(a) trimethylaluminum or (b) trimethylantimony

TMAH

tetramethyl ammoniumhydroxide

TMAT

tetramethylamidotitanium

TMB

tetramethylborate

TMCTS

tetramethylcyclotetrasiloxane

TMG

trimethylgallium

TMOS

tetramethyloxysilane

TMP

trimethylphosphine

TMS

tetramethylsilane

TMT

tetramethyltin

TOFER

topos:graphic feature enhancement by RIE

TPF

thermoplastic film

TRAPPAT

trapped plasma avalanche tunnel transit (diode)

TSD

temperature sensing diode

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TSOP

thin small outline package

TTL

transistor-transistor logic

UHV

ultrahigh vacuum

UV

ultraviolet

VCNR

voltage controlled negative resistance

VGF

vertical gradient freeze (also VFG)

VHSIC

very high speed integrated circuit

VLE

vapor levitation epitaxy

VLSI

very large scale integration

VMOS

vertical MOS

VPE

vapor phase epitaxy

VSIS

V-channel substrate inner stripe

WSI

wafer scale integration

XRD

x-ray diffraction

YBCO

yttria barium copper oxide (a HTSC)

YSZ

yttria stabilized zirconia

ZDO

zero drain overlap

ZIP

zigzag-in-line package

ZMR

zone melt recrystallization

MC

microcrystalline

P

high resistivity intrinsic semiconductor

ACCEPTOR IMPURITY

An atom or ion different from or foreign to, but present in, a semiconductor material and which has insufficient valence electrons to complete the normal bonding arrangement in the semiconductor crystal structure. An acceptor impurity (also referred to as p-type) accepts an electron from an adjacent atom to create a positive charge carrier (i.e., a hole). A donor impurity (also referred to as n-type) provides an electron to the conduction band of the semiconductor.

ACTIVE SOLID-STATE DEVICE

An electronic device or component that is primarily made up of solid materials, usually semiconductors, which operates by the movement of charge carriers - electrons or holes - which undergo energy level changes within the material and can modify an input voltage to achieve rectification, amplification, or switching action. Active solid-state electronic devices include diodes, transistors, thyristors, etc., but exclude pure resistors,

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capacitors, inductors, or combinations solely thereof. The latter category is characterized as passive.

ALLOY JUNCTION

A fused junction produced by combining one or more elemental impurity metals with a semiconductor. Typical alloyed junctions include indium-germanium and aluminum-silicon.

AUTODOPING

The introduction via the vapor phase of impurities from an existing substrate region (and adjacent supports, e.g., susceptors, etc.) into another substrate region, typically during growth of the same.

AVALANCHE BREAKDOWN

A sudden change from high dynamic electrical resistance to very low dynamic resistance in a reverse biased semiconductor device (e.g., a reverse biased junction between p-type and n-type semiconductor materials) wherein current carriers are created by electrons or holes which have gained sufficient speed to dislodge valence electrons. Avalanche breakdown can cause structural damage to a semiconductor device.

BAND GAP

The difference between the energy levels of electrons bound to their nuclei (valence electrons) and the energy levels that allow electrons to migrate freely (conduction electrons). The band gap depends on the particular semiconductor involved.

BARRIER REGION OR LAYER

A region which extends on both sides of a semiconductor junction in which all carriers are swept away from the junction region. The region is depleted of carriers. This is also referred to as a depletion region. Not to be confused with diffusion barrier layers associated with metallization schemes for active solid state devices.

BINARY COMPOUND

A substance that always contains the same two elements in a fixed atomic ratio.

BIPOLAR

An active solid-state electronic device in which both positive and negative current carriers are used to support current flow.

BIPOLAR TRANSISTOR

An active solid-state electronic device with a base electrode and two or more junction electrodes in which both positive and negative current carriers are used to support current flow.

BIRD"S BEAK

The lateral encroachment of the localized oxidation region associated with a recessed oxide isolation structure.

BONDING PAD

A metallized area to which an external electrical connection is to be made.

BREAKDOWN

A sudden change from high dynamic electrical resistance to a very low dynamic resistance in a reverse biased semiconductor device (e.g., a reverse biased junction between p-type and n-type semiconductor materials) wherein reverse current increases rapidly for a small increase in reverse applied voltage, and the device behaves as if it had negative electrical resistance.

CAPACITOR

A component used in electrical and electronic circuits which stores a charge of electricity, usually for very brief periods of time, with the ability to rapidly charge and discharge. A capacitor is usually considered a passive component since it does not rectify, amplify, or switch and because charge carriers do not undergo energy level changes therein, although some active solid state devices function as voltage variable capacitors.

CHANNEL

A path for conducting current between a source and drain of a field effect transistor.

CHANNEL STOP

Means for limiting channel formation in a semiconductor device by surrounding the affected area with a ring of highly doped, low resistivity semiconductor material. In a field effect transistor, it is a region of highly doped material of the same type as the lightly doped substrate

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used to prevent leakage paths along the chip surface from developing. Also referred to as “chanstop.”

CHANNEL PINCH-OFF REGION

The location in a current channel portion of a field effect transistor (FET) where the current is reduced to a minimum value due to its diameter being reduced to a minimum.

CHARGE CARRIER

A mobile conduction electron or hole in a semiconductor.

CHARGE CONFINEMENT

Restriction of electrical charge carriers (e.g., electrons or holes) to specified locations (e.g., by quantum wells, gate electrode potentials, etc.).

CHARGE INJECTION DEVICE

A field effect device in which storage sites for packets of electric charge are induced at or below the surface of an active solid-state device by an electric field applied to the device and wherein carrier potential energy per unit charge minima are established at a given storage site and such charge packets are injected into the device substrate or into a data bus. This type device differs from a charge transfer device in that, in the latter, charge is transferred to adjacent charge storage sites in a serial manner, whereas, in a charge injection device, the charge is injected in a nonserial manner to the device substrate or to a data bus.

CHIP

A single crystal substrate of semiconductor material on which one or more active or passive solid-state electronic devices are formed. A chip may contain an integrated circuit. A chip is not normally ready for use until packaged and provided with external connectors.

CHIP CARRIER

A package with terminals, for solid-state electronic devices, including chips which facilitates handling of the chip during assembly of the chip to other electronic elements.

CLADDING BARRIER

A higher band gap material which encases a lower band gap material that defines the walls of a quantum well.

COHERENCE LENGTH

The typical distance an electron can travel before it is scattered (e.g., by a phonon, a defect, or an impurity, etc.).

COHERER

A term which encompasses both active and passive type devices, the passive type being a resistor whose resistance decreases when subjected to a high frequency signal, and the active type being a rectifier which is made up of active solid-state particles which conduct and rectify current when connected into a cohesive element but which loses that characteristic when the particles are separated (e.g., by shaking a container in which the particles are located, etc.).

COLLECTOR DIFFUSION ISOLATION (CDI)

An electrical isolation technology used for bipolar devices which employs an epitaxial layer, which forms transistor base regions, laid on a substrate of the same conductivity type (p or n) as the epitaxial layer, with an opposite conductivity type region, more heavily doped than the epitaxial base layer and located between the layer and the substrate, forming the collector and isolating the transistor from the substrate.

COMPOUND SEMICONDUCTOR

A semiconductor composed of a chemical compound formed of elements from two or more different groups of the chemical periodic chart (e.g., Group III (B, Al, Ga, In) and Group V (N, P, As, Sb) for the following compounds: AlP, AlAs, AlSb, GaP, GaAs, GaSb, InP, InAs, and InSb, or a compound of silicon and carbon (SiC)).

CONDUCTION BAND

A partially filled energy band in which electrons can move freely, permitting a material to carry electric current where electrons are the current carriers.

CONDUCTION ELECTRONS

In a conductor or n-type semiconductor, outer shell electrons that are bound so loosely that they can move

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freely in the conduction band of a solid material under the influence of an electric field.

CONNECTOR AREA

That portion of the electrical conductors (e.g., bonding pad, die bond, etc.) used for providing external electrical connections from a component to a chip or other component.

CONTACT

The point or part of a conductor which touches another electrical conductor or electrical component to carry electrical current to or from the conductor or electrical component.

CRYSTAL DEFECT

Any nonuniformity in a crystal lattice. There are four categories of crystal defects: (a) point defects, (b) line defects, (c) area defects, and (d) volume defects. Point defects include any foreign atom at a regular lattice site (i.e., substitutional site) or between lattice sites (i.e., interstitial site), antisite defects in compound semiconductors (e.g., Ga in As or As in Ga), missing lattice atoms, and host atoms located between lattice sites and adjacent to a vacant site (i.e., Frenkel defects). Line defects, also called edge or screw dislocations, include extra planes of atoms in a lattice. Area defects include twins or twinning (i.e., a change in crystal orientation across a lattice) and grain boundaries (i.e., a transition between crystals having no particular positional orientation to one another). Volume defects include precipitates of impurity or dopant atoms caused by volume mismatch between a host lattice and precipitates.

DEEP DEPLETION

The condition in which a depletion layer formed in a MOS active device due to voltage applied to the gate electrode of the device is deeper than the maximum depth at which inversion would normally be expected to occur at room temperature in a semiconductor device at the surface closest to the gate electrode, without formation of an inversion layer.

DEEP LEVEL CENTERS

Energy levels that can act as traps located in the forbidden band of a semiconductor material that are not near the conduction or valence band edges.

DEGENERATION

Doping of a semiconductor to such an extent that the Fermi level lies within the conduction band (i.e., N+ semiconductor) or within the valence band (i.e., P+ semiconductor). Also, in circuit applications, negative feedback between two or more active solid-state devices.

DEPLETION MODE

The operation of a field effect transistor having appreciable channel conductivity for zero gate-source voltage and whose channel conductivity may be increased or decreased according to the polarity of the applied gate-source voltage, by changing the gate-to-source voltage from zero to a finite value, resulting in a decrease in the magnitude of the drain current.

DEPLETION REGION

The region extending on both sides of a reverse biased semiconductor junction in which free carriers are removed from the vicinity of the junction. It is also called a space charge region, a barrier region, or an intrinsic semiconductor region.

DEVICE (ACTIVE)

The physical realization of an individual electrical element in a physically independent body which cannot be further divided without destroying its stated function. Examples are transistors, pnpn structures, and tunnel diodes.

DIE

A tiny piece of semiconductor material, separated from a semiconductor slice, on which one or more active electronic components are formed. Sometimes called a chip.

DIE BOND

Attachment of a semiconductor chip to a substrate or chip carrier or package, usually with an epoxy, eutectic, or solder alloy.

DIFFUSED JUNCTION

A junction between two different conductivity regions within a semiconductor and which is formed by diffusion of appropriate impurity atoms into the material.

DIFFUSION BARRIER

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An obstacle to the diffusion of atoms in a metallization scheme for an active solid-state device.

DIODE ISOLATION

A technique in which a high electrical resistance between an integrated circuit element and its substrate is achieved by surrounding the element with a reverse biased pn junction.

DIP (DUAL IN-LINE PACKAGE)

A chip carrier or package consisting of a plastic or ceramic body with two rows of vertical leads in which a semiconductor integrated circuit is assembled and sealed. The leads are typically inserted into a circuit board and secured by soldering.

DIRECT BAND GAP SEMICONDUCTOR

A semiconductor in which an electron transition from the conduction to the valence band, or vice versa, does not require a change in crystal momentum for electrons. Gallium arsenide is an example of a direct band gap semiconductor.

DISORDERED

Crystalline arrangement in which the different constituent atoms of a compound semiconductor randomly occupy lattice sites.

DISLOCATION

A line defect in a crystal, either of the edge type or screw type, in which the atoms are not arranged in a perfect latticelike structure. See CRYSTAL DEFECT for other examples of crystalline defects.

DMOSFET

Depletion-type metal oxide semiconductor field effect transistor. Such devices are normally in the on condition with no applied gate voltage.

DONOR IMPURITY

An element which when added to a semiconductor provides unbound or free electrons to the semiconductor which may serve as current carriers. Typically, donors are atoms which have more valence electrons than the atoms of the semiconductor material into which they are introduced in small quantities as an impurity or dopant. Since such donor impurities have more valence electrons than the semiconductor, a semiconductor doped with donor impurities is an n-type semiconductor.

DOPANT

An impurity added from an external source to a material by diffusion, coating, or implanting into a substrate, such as changing the properties thereof. In semiconductor technology, an impurity may be added to a semiconductor to modify its electrical properties or to a material to produce a semiconductor having desired electrical properties. N-type (negative) dopants (e.g., such as phosphorus for a group IV semiconductor) typically come from group V of the periodic table. When added to a semiconductor, n-type dopants create a material that contains conduction electrons. P-type (positive) dopants (e.g., such as boron for a group IV semiconductor) typically come from group III and result in conduction holes (i.e., vacancies in the electron shells).

DOPING OF SEMICONDUCTOR

Adding controlled amounts of conductivity modifying material, referred to as electrically active dopant or impurity, to a semiconductor material or to a material to produce a semiconductor having desired electrical properties for this class.

DOPING PROFILE

The point to point concentration throughout a semiconductor of an impurity atom doped into the semiconductor.

DOUBLE-DIFFUSED MOS (DMOS)

A metal oxide semiconductor having diffused junctions in which successive diffusions of different impurity types are made in the same well-defined region of the semiconductor.

DRAIN

The electrode of a field effect transistor which receives charge carriers which pass through the transistor channel from the source electrode.

DUAL GUARD-BAND ISOLATION

A type of electrical isolation of functional elements of an integrated circuit comprised of two distinct unused areas of chip surface area adjacent to the elements desired to be electrically isolated.

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DYNAMIC RANDOM ACCESS MEMORY (DRAM)

Solid-state memory in which the information decays over time and needs to be periodically refreshed.

ELECTROMIGRATION

Mass transport of ions (i.e., usually metal) in a material as a response to the passage of current through the material by momentum exchange between thermally activated ions and conduction electrons.

ELECTRON-HOLE PAIR

A positive charge carrier (i.e., hole) and a negative charge carrier (i.e., electron) considered together as being created or destroyed as part of one and the same event.

ENHANCEMENT MODE

The operation of a field effect transistor which has a channel formed therein between its source and drain regions and which normally does not conduct current through its channel with zero voltage applied to its gate electrode. Voltage of the correct polarity will accumulate minority carriers in the channel to permit conduction of current in the channel, thus turning on the transistor.

EPITAXIAL LATERAL OVERGROWTH

Process of epitaxial deposition through an exposed opening in an insulating layer with deposition continuing epitaxially over the insulating layer laterally from the opening.

EPITAXY

The controlled growth of a single crystal of one material on the surface of a crystal of the material (i.e., homo) or onto another substance (i.e., hetero) so that the crystal lattice of the base material controls the orientation of the atoms in the grown single crystal layer.

ESAKI DIODE

A heavily doped pn-junction diode where conduction occurs through the junction potential barrier due to a quantum mechanical effect even though the carriers which tunnel through the potential barrier do not have enough energy to overcome the potential barrier. Esaki tunneling involves a tunneling barrier formed by a macroscopic depletion layer between n-type and p-type regions. It does not involve a resonant tunneling barrier using controlled quantum confinement, a layer located between junctions, nor a thin superlattice layer.

EXTRINSIC SEMICONDUCTOR

A semiconductor whose charge carrier concentration and, therefore, electrical properties depend on impurity atoms introduced therein.

FACE BONDED

A chip mounting technique wherein semiconductor chips are provided with small mounting pads, turned face down, and bonded directly to conductors on a substrate.

FIELD EFFECT TRANSISTOR (FET)

A unipolar transistor in which current carriers are injected at a source terminal and pass to a drain terminal through a channel of semiconductor material whose conductivity depends largely on an electric field applied to the semiconductor from a control electrode. There are two main types of FETs, a junction FET and an insulated-gate FET. In the junction FET, the gate is isolated from the channel by a pn-junction. In an insulated-gate FET, the gate is isolated from the channel by an insulating layer so that the gate and channel form a capacitor with the insulating layer as the capacitor dielectric.

FIELD OXIDE

A thin (on a macroscopic scale) film made of an oxide of a material which overlies a device substrate to reduce parasitic capacitive coupling between conductors overlying the oxide and the substrate or devices below the oxide layer (e.g., in the substrate). See bird"s beak.

FLIP-CHIP

A term which describes the situation wherein a semiconductor device which has all terminations on one side thereof in the form of bump contacts, has a passivated surface, and has been flipped over and attached to a matching substrate.

FLOATING DIFFUSION

A region of a semiconductor device in which impurity atoms have been doped and which is electrically floating, that is, has no direct electrical connection.

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FLOATING GATE

A gate electrode that is electrically floating, that is, has no direct electrical connection.

FORBIDDEN ENERGY BAND

The energy band of a material which is located between a solid material"s conduction and valence bands. It is defined by the amount of energy that is needed to release an electron from its valence band to its conduction band. Electrons cannot exist in this gap. They are either below it, and bound to an atom, or above it, and able to move freely.

FRAME TRANSFER CCD

A charge coupled device area imager array with a separate image area, storage area, and read-out register area, the storage area being located between the image area and the readout area. This is distinguished from an interline- transfer CCD in which the sensing and storage/readout function areas are located next to each other.

GATE

The control electrode or control region that exerts an effect on a semiconductive region directly associated therewith, such that the conductivity characteristic of the semiconductor region is altered in a temporary manner, often resulting in an on-off type switching action. The control electrode or control region of a field effect transistor is located between the source and drain electrodes, and regions thereof.

GATE ARRAY

A repeating geometric arrangement of groups of active solid-state devices, each group being connectable into a logic circuit, in one integrated, monolithic semiconductor chip.

GATE CONTROLLED DIODE

A three terminal semiconductor diode with the ability to be turned on or off by a pulse applied to its gate electrode.

GETTERING

The elimination or reduction of unwanted constituents (i.e., impurities) or defects from a substrate.

GRAPHOEPITAXY

The growth of a single crystalline layer across the surface of a nonsingle crystalline substrate by commencing growth at a seeding portion/region thereof.

GUNN DIODE

A diode in which electrons under the influence of sufficiently high electric fields are transferred between energy valleys of different momentum in the conduction band of the active semiconductor device material or holes under the influence of sufficiently high electric fields are transferred between energy valleys of different momentum in the valence band of the active semiconductor device material. A Gunn diode does not normally have a pn junction and cannot be used as a rectifier.

GUNN EFFECT

An intervalley transfer effect wherein electrons under the influence of sufficiently high electric fields are transferred between energy valleys of different momentum in the conduction band of the active semiconductor device material, or holes under the influence of sufficiently high electric fields are transferred between energy valleys of different momentum in the valence band of the active semiconductor device material.

HALL EFFECT DEVICE

An active solid-state device in which a current is flowing and is in a magnetic field perpendicular to the current, and in which a voltage is produced that is perpendicular to both the current flow direction and the magnetic field direction.

HETEROJUNCTION/HETEROINTERFACE

An interface between two dissimilar semiconductor materials. For example, one material may by InAs and the other may be InAlAs, or one material may be GaAs and the other material may be GaAlAs.

HIGH ELECTRON MOBILITY TRANSISTOR (HEMT)

A heterojunction field effect transistor with impurity ions located on the side of the heterojunction with lower affinity for the charge carriers (holes or electrons) injected at the source that pass to the drain via a channel adjacent the heterojunction.

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HOLE

An empty energy level in the valence band of a semiconductor crystal which exhibits properties of a real particle and can act as a mobile positive-charge carrier.

HOMOJUNCTION

An interface between regions of opposite polarity in the same semiconductor material.

HOT CARRIER DIODE

A diode in which electrons (or holes) have energies greater than those that are in thermal equilibrium with the material of at least one of the regions forming the diode. Schottky barrier diodes typically have “hot carriers” (hot electrons) injected into the metal from the semiconductor.

HYBRID CIRCUIT

A small printed circuit having miniature components which may include passive components (resistors, capacitors, and inductors) deposited on a printed circuit board.

IMPURITY

A foreign material present in a semiconductor crystal, such as boron or arsenic in silicon, which is added to the semiconductor to produce either p-type or n-type semiconductor material, or to otherwise result in material whose electrical characteristics depend on the impurity dopant atoms.

INDIRECT BAND GAP SEMICONDUCTOR

A semiconductor material in which a change in semiconductor crystal momentum for an electron is required when it moves from the conduction band to the valence band and vice versa. Silicon and aluminum arsenide are examples of indirect band gap semiconductors.

INSULATED-GATE FIELD EFFECT TRANSISTOR (IGFET)

A unipolar transistor with source, gate, and drain regions and electrodes, in which conduction takes place in a channel controlled by action of the voltage applied to the gate electrode of the device, in which the gate electrode is separated from the channel by an insulator layer.

INSULATOR

A material which has a high resistance to the flow of electric current. It has such low electrical conductivity that the flow of current therethrough can usually be neglected.

INTRINSIC CONCENTRATION

The number of minority carriers in a semiconductor due to thermal generation of electron-hole pairs.

INVERSION

A condition in a semiconductor material in which the concentration of minority carriers exceeds the concentration of majority carriers.

INVERSION LAYER/CHANNEL

A region in a semiconductor material in which the concentration of minority carriers exceeds the concentration of majority carriers.

ISOELECTRONIC

A condition in which two constituents have the same number of valence electrons.

ISOLATION

The separation or surrounding of active semiconductor regions or components with electrically insulative regions to prevent the flow of electrical current between the active semiconductor regions or between electronic component parts of a solid-state electronic device.

ISOPLANAR CMOS

A semiconductor device in which relatively thick regions of silicon dioxide, recessed into the semiconductor surface, are used to electrically isolate device areas and prevent parasitic device formation. More commonly called LOCOS CMOS.

ISOPLANAR ISOLATION

A type of electric isolation in which relatively thick regions of silicon dioxide, recessed into the semiconductor surface, are used to electrically isolate device areas and prevent parasitic device formation. More commonly called LOCOS ISOLATION.

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JUNCTION BARRIER

The opposition to the diffusion of majority carriers across a pn junction due to the charge of the fixed donor and acceptor ions.

JUNCTION CAPACITANCE

The capacitance across a pn junction. It depends on the width of the depletion layer, which increases with increased reverse bias voltage across the junction.

JUNCTION ISOLATION

Electrical isolation of devices on a monolithic integrated circuit chip using a reverse biased junction diode to establish a depletion layer that forms the electrical isolation between devices.

JUNCTION RESISTANCE

The electrical resistance across a semiconductor PN junction.

LAND

The conductive areas, normally metal patterns, on a semiconductor integrated circuit, which form part of the contacts and interconnections between components on the integrated circuit. See bonding pad, die bond.

LIFT-OFF

Process for the removal of unwanted deposited material from a substrate (and thus patterning the same) by the dissolution of an intermediate layer and the commitant physical separation of the overlying deposited material.

LUMINESCENCE

The emission of visible or invisible radiation unaccompanied by high temperature by any substance as a result of absorption of exciting energy in the form of photons, charged particles, or chemical change. It is a general term which includes fluorescence and phosphorescence. Types include hemiluminescence, bioluminescence, photoluminescence, electroluminescence, photoluminescence, and triboluminescence. Active solid-state luminescent devices are semiconductors which operate via injection luminescence. Active devices include pn junctions (including heterojunctions), Schottky barrier junctions, metal-insulator-semiconductor (MIS) structures, and high speed traveling domains (e.g., Gunn domain and acoustoelectric wave generated domains). Passive solid-state electroluminescent devices (phosphors) are insulators which operate in an intrinsic luminescence phenomena (i.e., where an applied electric field generates free carriers) to initiate the light emission mechanism, there being no free carriers in an insulator to be accelerated by an applied field unless the field also generates them.

MAJORITY CARRIER

The predominant charge carrier in a semiconductor. Electrons are majority carriers in n-type semiconductors. Holes are majority carriers in p-type semiconductors.

MASTERSLICE ARRAY/MASTERCHIP

A substrate that contains active and passive electronic components in a predetermined pattern which may be connected into different logic or analog circuits.

MBM JUNCTION

Active solid-state devices having metal-barrier-metal layer junctions.

METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFET)

See Insulated-gate Field Effect Transistor.

METALLIZATION

Process of coating (a) metal or (b) other material which is identified as having the conductive characteristic of a metal onto a semiconductor or a substrate containing semiconductor regions to form electrodes, contacts, interconnects, bonding pads, or heat sinks and also including formation of conductive material by doping of nonconductive material.

MIM DIODE

A junction diode with a thin insulating layer of material sandwiched between two metallic surface layers which operates as a tunneling (direct or Fowler-Nordheim type) diode.

MINORITY CARRIER

The less predominant charge carrier in a semiconductor. In a p-type semiconductor, minority carriers are elec-

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trons, whereas in n-type semiconductor material, minority carriers are holes.

MIS

Acronym for metal-insulator-semiconductor. Typically active solid-state devices with MIS technology have a silicon dioxide layer formed on a single crystal silicon substrate. A polysilicon conductor layer is formed on the oxide.

MOBILITY

The facility with which carriers move through a semiconductor when subjected to an applied electric field. Electrons and holes typically have different mobilities in the same semiconductor.

MODFET

Acronym for a modulation doped field effect transistor. A high speed semiconductor FET in which dopant atoms containing semiconductor layers alternate with nondoped semiconductor layers, so that the carriers (electrons or holes) resulting from the dopant atoms can travel in the undoped material, so that there is little scattering of carriers from dopant atoms. Typically, the dopant atoms are in semiconductor material having a lower carrier affinity than the undoped layers to facilitate carrier spill over into the undoped layers. Such a structure may typically constitute a superlattice. See also High Electron Mobility Transistor.

MONOLITHIC DEVICE (E.G., IC, ETC.)

A device in which all components are fabricated on a single chip of silicon. Interconnections among components are provided by means of metallization patterns on the surface of the chip structure, and the individual parts are not separable from the complete circuit. External connecting wires are taken out to terminal pins or leads.

MSM

Acronym for metal-semiconductor-metal semiconductor device. Active solid-state semiconductor devices having a semiconductor layer sandwiched between two layers of metal and forming back-to-back Schottky diodes.

NEGATIVE RESISTANCE REGION

An operating region of an active solid-state electronic device in which an increase in applied voltage results in a decrease in output current.

NEGATIVE TEMPERATURE COEFFICIENT

The amount of reduction in a device parameter, such as capacitance or resistance, for each degree of device operating temperature.

NMOS

N-channel metal oxide semiconductor devices which use electrons as majority carriers.

NONDOPANT

An impurity added from an external source which does not modify the electrical properties of a semiconductor.

NPN TRANSISTOR

A bipolar transistor with n-type emitter and collector regions separated by a p-type base.

N-CHANNEL FET

A field effect transistor that has an n-type conduction channel.

N-TYPE SEMICONDUCTOR

An extrinsic semiconductor having n-type dopant atoms (e.g., atoms with one or more valence electron than the host atoms). Electron density exceeds hole density.

ORDERED

Crystalline arrangement in which different constituent atoms of a compound semiconductor occupy specific lattice sites resulting in long range regularity of the resultant structure.

OUTDIFFUSION

The solid-state diffusion of impurities from the underlying substrate into a deposited layer during the growth thereof.

PACKAGE

A container, case, or enclosure utilized in the context of semiconductor art for protecting a solid-state electronic device from the environment and which is considered a part of a manufacture product (i.e., as opposed to a package utilized for passage of a product through the

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channels of trade in a safe, convenient, and attractive condition).

PAD

A. The portion of a conductive pattern on a solid-state electronic device for making external connection thereto. B. The portion of a conductive pattern on a chip or a printed circuit board designed for mounting or attaching a substrate or solid-state active electronic device. See also bonding pad, die bond, etc.

PARASITIC DEVICES/CHANNELS

A. Junctions forming unintended interconnection of intended active solid-state devices. B. Devices which were not designed to carry current flow and which result from unintended interconnection of intended active solid-state devices.

PASSIVE DEVICE

A solid-state electronic device or component in which charge carriers do not change their energy levels and that does not provide rectification, amplification, or switching, but which does react to voltage and current. Examples are pure resistors, capacitors, and inductors.

P-CHANNEL

A conduction path, made of p-type semiconductor material, located between source and drain of a field effect device.

PHOTODIODE

A diode in which charge carriers are created by light which illuminates the diode junction. It is a photovoltaic as well as a photoconductive device.

PINCH-EFFECT RESISTOR

A monolithic integrated circuit resistor having a layer of one conductivity type, typically a P-layer formed at the same time as integrated circuit bipolar transistor base regions, which is thinned by an inset region of opposite conductivity type, typically an N-layer formed at the same time as integrated circuit bipolar transistor emitter regions.

PIN DIODE/DEVICE

A diode having an intrinsic semiconductor (i.e., one with no dopants) sandwiched between a p-type layer and an n-type layer. The depletion region (the intrinsic semiconductor layer) thickness can be tailored to optimize quantum efficiency for use as a photo diode or frequency response for use as a microwave diode.

PIN-GRID ARRAY

A semiconductor chip package having leads in the form of pins arranged in columns and rows.

PLANAR TRANSISTOR

A bipolar transistor in which the emitter base and collector regions terminate at the same plane surface without indentations in or protrusions from the surface. Hence, the emitter and base regions form dish-shaped portions extending into the semiconductor from the common surface.

PN-JUNCTION

The interface and region of transition between p-type and n-type semiconductors. See also barrier layer.

PN-JUNCTION DIODE

A semiconductor device having two terminals connected to opposite-type semiconductor materials with a junction therebetween and exhibiting a nonlinear voltage-current characteristic, usually used for switching or rectification.

PNP TRANSISTOR

A bipolar transistor with p-type emitter and collector regions separated by an n-type base.

POINT DEFECT

A crystal defect occurring at a point in a crystal. Examples include (a) a foreign atom incorporated into the crystal lattice at either a substitutional (regular lattice) site or interstitial (between regular lattice sites) site, (b) a missing atom in the lattice, or (c) a host atom located between regular lattice sites and adjacent to a vacancy (called a Frenkel defect). See CRYSTAL DEFECT for other examples of crystalline defects.

POLYSILICON

A polycrystalline form of silicon.

POTENTIAL BARRIER

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The difference in electrical potential across a pn junction in a semiconductor. See also barrier layer.

POTTING

An embedding process in which an electronic component is placed in a can, shell, or other container and buried in a fluid dielectric which subsequently is hardened material. Even though the container is not removed from the finished part, this is considered a molding operation since the fluid is confined to a definite shape during hardening.

PRINTED CIRCUIT BOARD

A structure formed on one or more layers of electrically insulating material having electrical terminals and conductive material deposited thereon, in continuous paths, from terminal to terminal, to form circuits for electronic apparatus such as chips or substrates.

P-TYPE

An extrinsic semiconductor in which the hole density exceeds the conduction electron density.

PUNCHTHROUGH

Expansion of a depletion region* from one junction to another junction in an active solid-state device.

QUANTUM TRANSISTOR

Transistors whose operation is based on the properties of electrons confined in quantum wells - semiconductor films only a hundred or so angstroms thick sandwiched between high confining walls made of a second semiconductor material.

QUANTUM WELL

Semiconductor films only a hundred or so angstroms thick sandwiched between high confining walls made of a second material.

RECOMBINATION

The process by which excess holes and electrons in a semiconductor crystal recombine and no longer function as charge carriers in the semiconductor. Basic recombination processes are band-to-band recombination which occurs when an electron in the conduction band recombines with a hole in the valence band, and trapping recombination which occurs when an electron or hole is captured by a deep energy level, such as produced by a deep level dopant, before recombining with an opposite conductivity-type carrier.

RESISTIVITY

A measure of the resistance of a material to electric current. Resistivity is a bulk material property measured in ohm-cm.

RESONANT TUNNELLING DEVICE

A device that works on the principle of resonant electron (or hole) tunneling through a pair of matched potential barriers. This occurs when the energy of the electrons (or holes) matches that of a quantum energy level in the quantum well formed between the barriers.

SEMICONDUCTOR

A. A generic term for (1) a substance or material whose electronic conductivity at ordinary temperature is intermediate between that of a metal and an insulator and whose conductivity is capable of being modified by the addition of a dopant or (2) an electronic device the main functioning parts are made from semiconductor materials.

B. For the purposes of Class 438, a semiconductor material (1) must have resistivity between that of an insulator and a conductor and (2) be intended for use in a solid state device for at least one of the following purposes: (a) conducting or modifying an electrical current, (b) storing electrical energy for subsequent discharge,or (c) converting electromagnetic wave energy to electrical energy or electrical energy to electromagnetic energy. The resistivity is commonly changed by light, heat, or electric or magnetic fields incident on the material.

SEMICONDUCTOR JUNCTION

The region of transition, which usually exhibits asymmetric conductivity, between two joined semiconductors of different electrical properties or of joined semiconductor and conductor (e.g., metal, etc.) and which is also referred to in the art as a barrier layer. Types of junctions include heterojunctions, Schottky barrier junctions, and PN junctions.

SILICON ON INSULATOR (SOI)

A semiconductor structure using an insulating substrate, instead of silicon as a substrate material, with an overly-

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ing active layer of single crystal silicon containing active solid state devices. The substrate may typically be of the form of an insulating layer which is itself formed on a single crystal substrate.

SILICON ON SAPPHIRE (SOS) CMOS

A complementary metal oxide semiconductor device (e.g., a transistor) wherein single crystal silicon is grown on a passive insulating base of sapphire (single crystal alpha phase aluminum oxide) with complementary MOS transistors formed in the silicon in one or more island portions.

SINGLE CRYSTAL

A body of material having atoms regularly located at periodic lattice sites throughout.

SINKER

A buried electrically conductive, low resistance path in an integrated circuit which connects an electrical contact to a conductive region buried in the integrated circuit. It may be made up of a heavily doped impurity region.

SOLID-STATE DEVICE

An electronic device or component that uses current flow through solid (as opposed to liquid), gas, or vacuum materials. Solid-state devices may be active or passive.

SOURCE

In a field effect transistor, the active region/electrode to which the source of charge carriers is connected.

SPACE CHARGE REGION

The region around a pn junction in which holes and electrons recombine to leave no mobile charge carriers and a net charge density due to the residual dopant ions.

SPIKING

Phenomena associated with electromigration wherein a fingerlike protrusion of a metallization layer is allowed to grow through a dielectric layer and eventually contact a further layer.

SUBSTRATE

A. A base upon which a coating is formed. See the class definition for the requirements for coating, per se, or etching, per se, when a base of semiconductor or containing a semiconductive region is the substrate. B. The supporting material on or in which the components of an integrated circuit are fabricated or attached.

SUPERLATTICE

A periodic sequence of variations in carrier potential energy in a semiconductor, of such magnitude and spacing that the current carrier wave function is spread out over many periods, so that carrier energy and other properties are determined in part by the periodic variations. The variation may be in chemical composition of the material, as in a sequence of heterojunctions, or in impurity concentration, forming a doping superlattice, or both.

SURFACE MOUNT DEVICES

Active or passive solid-state devices which are structured and configured to be mounted directly to a printed circuit board surface. This type of mounting is distinguished from “through-hole” mounting which involves the electrical and physical connection of devices to a printed circuit board using drilled and plated holes through the conductive pattern of the board.

SURFACE RESISTIVITY

The resistance of a material between two opposite sides of a unit square of its surface. Also called Sheet Resistance. Measured in ohms, often written as “ohms per square” in this case.

THERMISTOR

A thermoelectric device whose electrical resistance varies with temperature. Its temperature coefficient of resistance is high, nonlinear, and usually negative.

THIN-FILM

A material on a substrate with a thickness not greater than 10 microns and uniformity within 20% of it"s average value (Grant and Hackh"s Chemical Dictionary, 5th Edition, edited by Roger & Claire Grant, McGraw-Hill, Inc., 1987, page 235).

THICK-FILM DEVICES

Printed thin-film circuits. Silk screen printing tech-

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niques are used to make the desired circuit patterns on a ceramic substrate. Active devices may be added thereto as separate devices (see HYBRID CIRCUIT).

THIN-FILM DEVICES

Solid-state electronic devices which are constructed by depositing films of conducting material on the surface of electrically insulating bases.

THYRISTOR

A four layer p-n-p-n bistable switching device that changes from an off or blocking state to an on or conducting state which uses both electron and hole-type carrier transport.

TRANSFERRED ELECTRON DEVICE

See GUNN EFFECT. In such devices, advantage is taken of the negative differential mobility of electrons or holes in certain semiconducting compounds, particularly GaAs or InP.

TRANSISTOR

An active solid-state semiconductor device having three or more electrodes in which the current flowing between two specified electrodes is modulated by the voltage or current applied to one or more specified electrodes, and is capable of performing switching or amplification. May be of unipolar type (i.e., field effect transistor) or bipolar type.

TRAPATT DEVICE

An acronym for trapped plasma avalanche triggered transit diodes, which are biased into avalanche condition. As the diode breaks down, a highly conducting electron-hole plasma quickly fills the entire n-type region, and the voltage across the diode drops to a low value. The plasma is then extracted from the diode by the low residual electric field, thus causing a large current flow even though the voltage is low. Once extraction of the plasma is completed, the current drops and the voltage rises.

TRENCH ISOLATION

Electrical isolation of electronic components in a monolithic integrated circuit by the use of grooves or other indentations in the surface of the substrate, which may or may not be filled with electrically insulative (i.e., dielectric) material.

TUNNEL DIODE

A semiconductor diode in which the electrons penetrate a quantum barrier that is impenetrable in terms of classical physics, but which is penetrable in terms of quantum physics due to the quantum mechanical uncertainty in position of current carriers.

TWO-DIMENSIONAL ELECTRON GAS

A description of the motion of electrons which are confined in only one direction, such as electrons in the conducting channel of a MOSFET. In an electron gas, the electrons move around without apparent restriction. The behavior of electrons in conducting metals (e.g., copper) is an example of a three-dimensional electron gas. In a two dimensional electron gas, motion is restricted to a single plane (two dimensions). See also MODFET.

UNIPOLAR

An active solid-state electronic device in which only one type of charge carrier (i.e., positive holes or negative electrons) is used to support current flow.

VARACTOR

A semiconductor diode comprising a two terminal active device using the voltage variable capacitance of a pn junction or a Schottky junction that changes capacitance with a change in applied voltage.

VARISTOR

A varistor is a two-electrode active or passive semiconductor device with a voltage dependent nonlinear resistance which falls significantly as the voltage is increased. In an active device, the nonlinear property is due to the presence of one or more potential barriers. In a passive-type varistor, it is due to electrical heating of the material due to current flow therethrough. Varistors are to be contrasted with passive variable resistors such as rheostats or potentiometers.

VIA

A metallized or plated-through hole in an insulating layer, a semiconductor containing substrate or chip, or a printed circuit board which forms a conduction path itself without having a wire or lead inserted therethrough.

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WAFER

A thin slice of semiconductor material with parallel faces used as the substrate for active solid-state devices in discrete or monolithic integrated circuit form.

WIRING CHANNEL

An area on an integrated circuit, such as a gate array, which is left free of active devices and in which interconnection metallization patterns are formed.

WORK FUNCTION

The minimum energy required to remove an electron from the Fermi level of a material and liberate it to free space outside the solid.

ZENER DIODE

A single pn junction, two terminal semiconductor diode reversed biased into breakdown caused by the Zener effect (i.e., by field emission of charge carriers in the device"s depletion layer). NOTE: True Zener breakdown occurs in silicon at values below 6 volts. It is to be distinguished from the avalanche breakdown mechanism that occurs in reverse biased diodes at higher (about 6 volts) voltages.

SUBCLASSES

1 HAVING BIOMATERIAL COMPONENT OR INTEGRATED WITH LIVING ORGANISM:

This subclass is indented under the class definition. Process for making an electrical device utilizing a semiconductor substrate which contains a component identical to material found in a living organism or is integrated with a living organism.

SEE OR SEARCH CLASS:

128, Surgery, for a method of treatment of a living body or organism.

429, Chemistry: Electrical Current Producing Apparatus, Product, and Process, subclass 2 for subject matter under the class definition having living matter (e.g., microorganism, etc.).

2 HAVING SUPERCONDUCTIVE COMPONENT:

This subclass is indented under the class definition. Process for producing an electrical device utilizing a semiconductor substrate having an electrically conductive component which at temperatures of less than or equal to 30K is able to conduct electricity in the absence of resistance.

SEE OR SEARCH CLASS:

29, Metal Working, subclasses 25.01+ for manufacturing a nonsemiconductor-type barrier layer device and subclass 599 for a method of mechanical manufacture of a superconductor electrical device.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 30+ for an active solid-state device in which the active layer through which carrier tunnelling occurs has a lower conductivity than the material adjacent thereto, especially subclasses 31+ for Josephson junction devices, and subclasses 661+ for a superconductive contact or lead.

331, Oscillators, subclass 107 for superconductive element and tunnelling element oscillators.

427, Coating Processes, subclasses 62+ for a process of coating, per se, wherein the product is a superconductive electrical device.

505, Superconductor Technology: Apparatus, Material, Process, particularly subclass 330 for a process of manufacturing a semiconductor electrical device having a superconductive component possessing an operating temperature greater than 30K and subclass 923 for a process of making a semiconductor electrical device having a superconductive component possessing an operating temperature of less than 30K.

3 HAVING MAGNETIC OR FERROELECTRIC COMPONENT:

This subclass is indented under the class definition. Process for making an electrical device wherein the semiconductor substrate has inte-

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gral therewith a component with recited magnetic or ferroelectric properties.

SEE OR SEARCH THIS CLASS, SUBCLASS:

48 for a process of manufacturing an electrical device or circuit utilizing a semiconductor substrate, said device or circuit being responsive to an external magnetic signal.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 295 for an insulated gate field effect transistor having a ferroelectric material layer.

427, Coating Processes, subclasses 127+ for coating a magnetic base or coating a base with a magnetic material.

4 REPAIR OR RESTORATION:

This subclass is indented under the class definition. Process for the renewal, reconstruction, or refurbishment of the previously possessed electrical or mechanical properties of a semiconductor electrical device which have become degraded.

(1) Note. This subclass includes patents to a process of removing and replacing a defective chip from a package as well as a process of repair of defective electrical conduct paths (e.g., wirings).

5 INCLUDING CONTROL RESPONSIVE TO SENSED CONDITION:

This subclass is indented under the class definition. Process including the step of regulating an operation by detecting a characteristic or a change in a characteristic of the process or the semiconductor substrate acted upon and by implementing an action in the process based upon the detected characteristic or change therein.

(1) Note. There must be a positive action carried out in response to the detected characteristic or change therein which furthers the semiconductor substrate toward its subsequent indented utilization. Thus, the removal of defective devices or substrates from a manufacturing process flow (e.g., by sorting, etc.) or the identification of same (e.g., by inking, etc.) is not deemed to be a positive action proper for this subclass.

SEE OR SEARCH CLASS:

209, Classifying, Separating, and Assorting Solids, especially subclasses 552+ for methods sensing a condition of an item and controlling the separation in accordance therewith.

340, Communications: Electrical, for control responsive indicating systems not having structural details, especially subclass 653 for electronic circuit or component and subclasses 657+ for electrical characteristic.

365, Static Information Storage and Retrieval, subclass 201 for testing of memory systems.

377, Electrical Pulse Counters, Pulse Dividers or Shift Registers: Circuits and Systems, subclasses 28+ for error checking of pulse counters.

714, Error Detection/Correction and Fault Detection/Recovery, appropriate subclasses for diagnostic testing, per se, particularly subclasses 100+ for reliability and availability, fault recovery, locating and avoidance, diagnostic testing or monitoring of a digital processing system for reliability purpose.

6 Interconnecting plural devices on semiconductor substrate:

This subclass is indented under subclass 5. Process for electrically connecting multiple electrical devices on a monolithic semiconductive substrate to establish a desired circuit pattern (e.g., wiring, etc.).

SEE OR SEARCH THIS CLASS, SUBCLASS:

128 for a process of forming an array of electrical devices and selectively interconnecting the devices to produce a desired electrical circuit.

7 Optical characteristic sensed:

This subclass is indented under subclass 5. Process wherein the sensed condition is an optical property of the device or an optical property of the process.

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(1) Note. Optical aligning, per se, is not deemed to be a control responsive operation for the purposes of this subclass.

SEE OR SEARCH CLASS:

348, Television, subclasses 86+ for manufacturing wherein a picture signal generator (i.e., television camera) is utilized for monitoring a manufacturing operation.

356, Optics: Measuring and Testing, for optical alignment processes.

382, Image Analysis, for methods for the automated analysis of an image or recognition of a pattern, including measuring significant characteristics of the image or pattern.

8 Chemical etching:

This subclass is indented under subclass 7. Process having a step of chemically etching the semiconductor substrate in conjunction with the sensing of an optical property of the process or of the semiconductor device.

9 Plasma etching:

This subclass is indented under subclass 8. Process wherein the chemical etching step utilizes an ionized chemically reactive gas to etch the semiconductor substrate.

10 Electrical characteristic sensed:

This subclass is indented under subclass 5. Process wherein the sensed condition is an electrical property of the device or an electrical property of the process.

SEE OR SEARCH CLASS:

209, Classifying, Separating, and Assorting Solids, especially subclasses 571+ for methods of electrical testing thereby sensing a property of an item to facilitate subsequent separation.

11 Utilizing integral test element:

This subclass is indented under subclass 10. Process wherein the electrical property is sensed utilizing a specific test structure integral to the semiconductor substrate and which has no other function in the completed device.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 48 for test or calibration structures provided on active solid-state devices to permit or facilitate the measurement, test, or calibration of the characteristics of the devices.

12 And removal of defect:

This subclass is indented under subclass 10. Process wherein a defect detected by the electrical sensing step is thereafter removed.

SEE OR SEARCH THIS CLASS, SUBCLASS:

4 for a process of repairing or restoring the previously possessed electrical or mechanical properties of a semiconductor electrical device which have become degraded.

13 Altering electrical property by material removal:

This subclass is indented under subclass 10. Process whereby following or as a result of the electrical sensing step, an electrical property of the semiconductor substrate is altered by a material removal step (e.g., by etching).

14 WITH MEASURING OR TESTING:

This subclass is indented under the class definition. Process having combined therewith a step of measuring or testing a condition of the process or of the device made thereby.

(1) Note. Processes having at least one step proper for the class and combined therewith a step of electrical aging or burn-in are classified herein.

SEE OR SEARCH CLASS:

209, Classifying, Separating, and Assorting Solids, especially subclasses 571+ for methods of electrical testing thereby sensing a property of an item to facilitate subsequent separation.

250, Radiant Energy, subclasses 306+ for inspection of solids or liquids by charged particles, and subclass 371 for invisible radiant energy responsive methods using semiconductor devices.

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324, Electricity: Measuring and Testing, for per se electrical measuring, especially subclass 71.5 for determining a nonelectrical property of a semiconductor by measuring an electrical property, subclass 451 for determining a material property using thermoelectric phenomenon, subclasses 500+ for fault detecting in electrical circuits and of electrical components, and subclass 719 for semiconductor materials quality determination using conductivity effects.

374, Thermal Measuring and Testing, especially subclass 57 for thermal testing of susceptibility to thermally induced deterioration, flaw, etc., and subclass 178 for thermal measuring utilizing a barrier layer (e.g., semiconductive junction) sensing element.

15 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:

This subclass is indented under subclass 14. Process provided including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

16 Optical characteristic sensed:

This subclass is indented under subclass 14. Process wherein the sensed condition is an optical characteristic of the process or of the device made thereby.

(1) Note. Optical aligning per se is not deemed to be a measurement of an optical characteristic and as such would not bring original classification to this subclass solely based on that claimed feature.

SEE OR SEARCH CLASS:

348, Television, subclasses 86+ for manufacturing wherein a picture signal generator (i.e., television camera) is utilized for monitoring a manufacturing operation.

356, Optics: Measuring and Testing, for optical alignment processes.

382, Image Analysis, especially subclasses 141+, for a manufacturing process using image analysis, aligning images/masks, or pattern recognition.

17 Electrical characteristic sensed:

This subclass is indented under subclass 14. Process wherein the sensed condition is an electrical characteristic of the process or of the device made thereby.

SEE OR SEARCH CLASS:

324, Electricity: Measuring and Testing, for per se electrical measuring, especially subclass 71.5 for determining a nonelectrical property of a semiconductor by measuring an electrical property, subclass 451 for determining a material property using thermoelectric phenomenon, subclasses 500+ for fault detecting in electrical circuits and of electrical components, and subclass 719 for semiconductor materials quality determination using conductivity effects.

18 Utilizing integral test element:

This subclass is indented under subclass 17. Process wherein the electrical property is sensed utilizing a specific test structure integral to the semiconductor substrate and which has no other function in the completed device.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 48 for test or calibration structures provided on active solid-state devices to permit or facilitate the measurement, test, or calibration of the characteristics of the devices.

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19 HAVING INTEGRAL POWER SOURCE (E.G., BATTERY, ETC.):

This subclass is indented under the class definition. Process for making a semiconductor electrical device having therewith an integral structure capable of chemically or radioactively generating electrical power.

SEE OR SEARCH CLASS:

136, Batteries: Thermoelectric and Photoelectric, subclass 202 for apparatus wherein nuclear energy other than that resulting from an induced nuclear reaction is used as a heat source for the generator or comprising a thermoelectric device designed to be employed as an ancillary unit in a nuclear reactor system.

310, Electrical Generator or Motor Structure, subclass 303 for the combination of a semiconductor junction and a radioactive source which radiates the semiconductor material and thus generates a source of current for an external load.

376, Induced Nuclear Reactions: Processes, Systems, and Elements, subclasses 320+ for the direct conversion of the energy produced in a nuclear reaction into an electrical output by a one-step process or apparatus for accomplishing such one-step process.

429, Chemistry: Electrical Current Producing Apparatus, Product, and Process, especially subclass 7 for a combination including a nonbattery electrical component electrically connected within a cell casing other than testing or indicating components.

20 ELECTRON EMITTER MANUFACTURE:

This subclass is indented under the class definition. Process for manufacturing a structure which gives off electrons into free space utilizing a semiconductor substrate.

(1) Note. Some materials may variously be conductive, semiconductive, or insulative. See section A. above for an expansion of what comprises a semiconductor substrate for the purposes of this class.

SEE OR SEARCH CLASS:

136, Batteries: Thermoelectric and Photoelectric, subclass 254 for a photoemissive photoelectric cell.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 10+ for devices having a low workfunction layer for electron emission.

313, Electric Lamp and Discharge Devices, especially subclass 346 for cathodes containing or coated with electron emissive material, subclasses 499+ for subject matter under the class definition having semiconductor depletion layer-type luminescent material, and subclass 546 for photosensitive photocathodes.

427, Coating Processes, subclasses 74+ for coating processes which result in a photoelectric or photovoltaic product (e.g., a photocathode) which is responsive to visible, infrared, or ultraviolet illumination by (a) emitting electrons, (b) generating an electromotive force, or by (c) varying electrical conductivity.

445, Electric Lamp or Space Discharge Component or Device Manufacturing, for a process of manufacturing a nonsemiconductive-type space discharge device.

21 MANUFACTURE OF ELECTRICAL DEVICE CONTROLLED PRINTHEAD:

This subclass is indented under the class definition. Process for manufacturing from a semiconductor substrate an electrical device utilized for the transfer to another surface of an imprint or mark which transfer is regulated by the electrical device.

SEE OR SEARCH CLASS:

29, Metal Working, subclass 890.1 for fluid pattern dispersion device manufacture (e.g., ink jet manufacture).

347, Incremental Printing of Symbolic Information, subclasses 1+ for ink jet marking apparatus, subclasses 159+ for electrical discharge marking apparatus, subclasses 163+ for electrochemical marking apparatus, and

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subclasses 171+ for thermal marking apparatus.

22 MAKING DEVICE OR CIRCUIT EMISSIVE OF NONELECTRICAL SIGNAL:
This subclass is indented under the class definition. Process for making a semiconductor electrical device or circuit which is emissive of a nonelectrical output during operation.

(1) Note. The nonelectrical signal serving as input stimulus to the device or circuit may be described as an information carrying wave.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 13, 79 through 103, and 918 for incoherent light emitting injection luminescent devices.
372, Coherent Light Generators, for coherent light emissive devices, in particular subclasses 43.01+ for a semiconductive laser device and subclass 75 for semiconductor optical laser pump devices.
430, Radiation Imagery Chemistry: Process, Composition, or Product Thereof, subclasses 311+ for electrical device manufacture involving photolithography, and subclass 321 for nonelectro-optic device manufacture involving photolithography.

23 Having diverse electrical device:
This subclass is indented under subclass 22. Process for manufacturing a circuit composed of a plurality of electrical devices integrated on a common substrate or chip of monolithic construction, at least one of the devices being emissive of nonelectrical signal.

24 Including device responsive to nonelectrical signal:
This subclass is indented under subclass 23. Process for making a circuit comprising a combination of a device emissive of nonelectrical signal and a device responsive to nonelectrical signal integrated onto a common substrate or chip of monolithic or hybrid construction.

SEE OR SEARCH CLASS:
65, Glass Manufacturing, especially subclasses 406+ for process of glass bonding an optical fiber to a substrate.
250, Radiant Energy, subclass 551 for signal isolators, including optically coupled light emitters and semiconductor light receivers.
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 80 through 85 for an incoherent light emitter coupled to an active solid-state light responsive device, per se.
372, Coherent Light Generators, for coherent light emissive devices, in particular subclasses 43.01+ for a semiconductive laser device and subclass 75 for semiconductor optical laser pump devices.
385, Optical Waveguides, subclass 14 for a laser in integrated optical circuit, subclasses 129+ for a planar optical waveguide, and subclasses 141+ for a waveguide having a particular optical characteristic modifying chemical composition.

25 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:
This subclass is indented under subclass 24. Process including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

26 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:
This subclass is indented under subclass 22. Process including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elon-

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gated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

SEE OR SEARCH THIS CLASS, SUBCLASS:

64 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device responsive to electromagnetic radiation.

106 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device.

27 Having additional optical element (e.g., optical fiber, etc.):

This subclass is indented under subclass 26. Process for making a semiconductor device wherein the device has combined therewith one or more separate optical elements to transmit or modify electromagnetic radiation incident from the semiconductor device and wherein the optical element is affixed or joined to the semiconductor device.

SEE OR SEARCH CLASS:

65, Glass Manufacturing, especially subclass 406 for processes which involve assembling at least two individually distinct optical fibers, waveguides, or preforms directly to each other (e.g., coupling, etc.)

323, Electricity: Power Supply or Regulation Systems, subclass 902 for optical coupling to a semiconductor.

28 Plural emissive devices:

This subclass is indented under subclass 26. Process for making a collection or grouping of multiple devices emissive of a nonelectrical signal in a single coherent monolith.

29 Including integrally formed optical element (e.g., reflective layer, luminescent material, contoured surface, etc.):

This subclass is indented under subclass 22. Process for making a semiconductor device wherein the device has combined therewith one or more optical elements to transmit or modify electromagnetic radiation incident from the semiconductor device.

30 Liquid crystal component:

This subclass is indented under subclass 29. Process for making a semiconductor device wherein the additional optical element is a substance, usually organic with at least one polarizable group, capable of unidirectional molecular alignment in layers, giving rise to optical bifringement.

(1) Note. Liquid crystals, on variation in pressure, temperature, electric current passing therethrough, etc., change their colors or light transmitting ability, the cholesteric type changing colors while the nematic-type changes between transparency and opacity.

SEE OR SEARCH CLASS:

345, Computer Graphics Processing and Selective Visual Display Systems, subclasses 87+ for a display element control system for liquid crystal display elements arranged in a matrix configuration.

349, Liquid Crystal Cells, Elements and Systems, particularly subclasses 187+ for nominal manufacturing methods or postmanufacturing processing of liquid crystal cells.

31 Optical waveguide structure:

This subclass is indented under subclass 29. Process for making a semiconductor device wherein the additional optical element is an optical conduit for the transmission of light energy.

32 Optical grating structure:

This subclass is indented under subclass 29. Process for making a semiconductor device wherein the additional optical element is a periodic latticework or screen composed of lines

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producing a series of spectra by the dispersion of the radiation emitted from the device.

33 Substrate dicing:
This subclass is indented under subclass 22. Process having a step of dividing the semiconductor substrate into plural separate bodies.

(1) Note. The dicing may be done by any manner, such as abrading, sawing, etching, cleavage, or a combination thereof.

SEE OR SEARCH CLASS:
83, Cutting, for generic processes of cutting a substrate into discrete individual units.
156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 701 through 719 and 930-932 for processes directed to separating an adhered layer with the layer identity retained as semiconductive.
225, Severing by Tearing or Breaking, subclasses 1+ for methods.
451, Abrading, for a process of dicing by abrading.

34 Making emissive array:
This subclass is indented under subclass 22. Process for making a collection or grouping of multiple devices emissive of nonelectrical signal in a single semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
28 for a process of packaging (e.g., with mounting, encapsulating, etc.) plural emissive devices into a coherent monolith.

35 Multiple wavelength emissive:
This subclass is indented under subclass 34. Process wherein the array is emissive of plural electromagnetic wavelengths.

36 Ordered or disordered:
This subclass is indented under subclass 22. Process for making a semiconductor device wherein a compound semiconductor region is ordered or disordered.

37 Graded composition:
This subclass is indented under subclass 22. Process wherein the chemical composition of a semiconductor region of the substrate varies with location within the semiconductive region.

38 Passivating of surface:
This subclass is indented under subclass 22. Process having a step of making the surface of the semiconductor substrate less chemically or optically active.

39 Mesa formation:
This subclass is indented under subclass 22. Process having a step of removing material from the semiconductor substrate to form a raised feature relative to the surrounding regions of the substrate.

40 Tapered etching:
This subclass is indented under subclass 39. Process wherein the material removal step is by etching the substrate to form a mesa with nonparallel sides.

41 With epitaxial deposition of semiconductor adjacent mesa:
This subclass is indented under subclass 39. Process including a step of epitaxial growth of semiconductor material on the portion of the substrate adjacent the mesa.

42 Groove formation:
This subclass is indented under subclass 22. Process having a step of removing material from the semiconductor substrate to form a recessed feature (e.g., trench, notch, etc.) relative to the surrounding regions of the substrate.

43 Tapered etching:
This subclass is indented under subclass 42. Process wherein the material removal step is by etching the substrate to form a groove with nonparallel sides.

44 With epitaxial deposition of semiconductor in groove:
This subclass is indented under subclass 42. Process including a step of epitaxial growth of semiconductor material in the groove.

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45 Dopant introduction into semiconductor region:
This subclass is indented under subclass 22. Process having a step of introducing a dopant into a semiconductive region of the substrate.

46 Compound semiconductor:
This subclass is indented under subclass 22. Process for making a device emissive of electromagnetic radiation having a compound semiconductor.

47 Heterojunction:
This subclass is indented under subclass 46. Process for making a device emissive of electromagnetic radiation having a interface between two dissimilar semiconductor materials, at least one of which is a compound semiconductor, to constitute a junction.

48 MAKING DEVICE OR CIRCUIT RESPONSIVE TO NONELECTRICAL SIGNAL:
This subclass is indented under the class definition. Process for making a semiconductor electrical device or circuit which is responsive to a nonelectrical input or stimuli during operation.

(1) Note. The nonelectrical signal serving as input stimulus of the device or circuit may be described as an information carrying wave.

SEE OR SEARCH CLASS:

136, Batteries: Thermoelectric and Photoelectric, for active solid-state device structures with a specified usage of generating electricity, especially subclasses 200+ for batteries which generate electricity under the action of heat and subclasses 243+ for batteries which generate electricity under the action of light; some of these batteries utilize potential barrier layers.

250, Radiant Energy, subclass 338.4 for infrared responsive semiconductor devices for signaling, subclasses 370.01 through 370.15 for invisible radiant energy responsive semiconductor devices, subclasses 552 through 553 for photocell circuits and apparatus involving solid-state light sources, and subclasses 208.1 through 208.6 for plural photosensitive elements, including arrays.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 53 through 56 , 108, 414, and 467 through 470 for such devices used as temperature responsive devices; subclasses 108, 414, and 421 through 427 for devices responsive to an external magnetic field; subclasses 10, 11, 21, 53 through 56, 72, 113 through 118, 184 through 189, 225 through 234, 257, 258, 290 through 294, 414, and 431 through 466 for light responsive active semiconductor devices.

338, Electrical Resistors, especially subclass 2 for electrical resistors of the strain gage type and subclass 22 for semiconductor thermistors.

427, Coating Processes, subclasses 74+ for coating processes which result in a photoelectric or photovoltaic product (e.g., photocathode) which is responsive to visible, infrared, or ultraviolet illumination by (a) emitting electrons, (b) generating an electromotive force, or (c) varying electrical conductivity.

49 Chemically responsive:
This subclass is indented under subclass 48. Process for making a semiconductor device responsive to a chemical reaction or the presence of a particular chemical or concentration thereof (e.g., pH level, etc.) in close proximity to the device.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 225, 253, and 414+ for an active solid-state device responsive to a nonelectrical signal.

50 Physical stress responsive:
This subclass is indented under subclass 48. Process for making a semiconductor device or circuit responsive to physical deformation (e.g., pressure, strain, etc.).

(1) Note. Processes for making semiconductor electrical device based surface

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acoustic wave devices, accelerometers, and strain gages are proper for this subclass.

SEE OR SEARCH CLASS:

73, Measuring and Testing, particularly subclass 777 for a semiconductor-type stress/strain sensor, subclass 514.16 for a semiconductor-type accelerometer, and subclass 754 for semiconductor-type fluid pressure sensors.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 415+ for a solid-state active device responsive to physical deformation.

333, Wave Transmission Lines and Networks, subclasses 193+ for electromechanical filter using surface acoustic waves.

338, Electrical Resistors, subclass 2 for electrical resistors of the strain gage type.

51 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:

This subclass is indented under subclass 50. Process including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

SEE OR SEARCH THIS CLASS, SUBCLASS:

106 for process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device.

52 Having cantilever element:

This subclass is indented under subclass 50. Process for making a physical stress responsive device or circuit which has a projecting beam or horizontal member supported at only one end.

SEE OR SEARCH CLASS:

216, Etching a Substrate: Processes, subclass 2 for a process of making a cantilever mechanical structure using semiconductive material wherein no electrical function is attributable to the cantilever element produced.

53 Having diaphragm element:

This subclass is indented under subclass 50. Process for making a physical stress responsive device or circuit which has a thin deflectable membrane.

SEE OR SEARCH CLASS:

216, Etching a Substrate: Processes, subclass 2 for a process of making a diaphragm mechanical structure using semiconductive material wherein no electrical function is attributable to the structure produced.

54 Thermally responsive:

This subclass is indented under subclass 48. Process for making a device or circuit responsive to the temperature proximate the device.

(1) Note. Processes of making devices which vary in electrical properties at various temperatures of operation are not deemed to be responsive to thermal stimuli for the purposes of this subclass.

SEE OR SEARCH CLASS:

136, Batteries: Thermoelectric and Photoelectric, subclass 200 for a process of using a thermoelectric device for generating electrical current.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 108, 225, 252, and 467 through 470 for a device responsive to temperature.

55 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:

This subclass is indented under subclass 54. Process provided including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a termi-

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nal, elongated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

SEE OR SEARCH THIS CLASS, SUBCLASS:

106 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device.

56 Responsive to corpuscular radiation (e.g., nuclear particle detector, etc.):

This subclass is indented under subclass 48. Process for making a device or circuit responsive to atomic or subatomic discrete particles (e.g., alpha, neutron, fission fragment or fissionable isotope).

SEE OR SEARCH CLASS:

250, Radiant Energy, subclass 371 for invisible radiant energy responsive methods using semiconductor devices. Also see subclasses 370.01+ for invisible radiant energy responsive electric signaling means of the semiconductor type, particularly subclass 370.02 for an alpha particle detection system, subclass 370.03 for a fission fragmentor fissionable isotope detection system, and subclass 370.05 for a neutron detection system.

57 Responsive to electromagnetic radiation:

This subclass is indented under subclass 48. Process for making a device or circuit responsive to ultraviolet, visible, or infrared light, x-rays, or gamma rays.

(1) Note. Processes of making devices in which (a) stored electrical charges are erased by exposure to electromagnetic radiation or (b) the device is switched from a nonconducting state to a conducting state or vice versa (e.g., optical turn-on type), are not considered to be responsive to a nonelectrical signal for placement in this and its indented subclasses.

SEE OR SEARCH THIS CLASS, SUBCLASS:

257 for a process of manufacturing a field effect transistor which has a floating gate structure capable of having electrical charge stored therein erased upon the application of electromagnetic radiation.

SEE OR SEARCH CLASS:

427, Coating Processes, subclasses 74+ for a process of coating with a photoelectric material to produce an electrical product.

430, Radiation Imagery Chemistry: Process, Composition, or Product Thereof, subclasses 31+ for an electric or magnetic imagery process employing a photoconductive semiconductive component.

58 Gettering of substrate:

This subclass is indented under subclass 57. Process having a step of gettering the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:

471 for a process of gettering a semiconductor substrate per se.

59 Having diverse electrical device:

This subclass is indented under subclass 57. Process for making an electrical device responsive to electromagnetic radiation in combination with an additional electrical device which is not responsive to electromagnetic radiation.

60 Charge transfer device (e.g., CCD, etc.):

This subclass is indented under subclass 59. Process for making a charge transfer device having combined therewith another electrical device or element, either of which being responsive to electromagnetic radiation.

(1) Note. A charge transfer device is a structure in which storage sites for packets of electrical charge are induced at or below the semiconductor surface by an electric field applied by serially arranged gate electrodes formed thereupon and

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wherein carrier potential energy per unit charge minima are established at a given storage site and such minima are transferred in a serial manner via an active channel region to one or more adjacent storage sites.

61 Continuous processing:
This subclass is indented under subclass 57. Process for making a semiconductor device responsive to electromagnetic radiation wherein a series of processing steps are performed in a uninterrupted manner.

62 Using running length substrate:
This subclass is indented under subclass 61. Process whereby the continuous processing is affected using an elongate substrate of indeterminate length having a semiconductive layer thereon.

SEE OR SEARCH THIS CLASS, SUBCLASS:
484 for a process of depositing amorphous active semiconductor onto a substrate of indeterminate length.
490 for a process of depositing polycrystalline active semiconductor onto a substrate of indeterminate length.

63 Particulate semiconductor component:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation wherein the substrate contains particulate semiconductive material.

(1) Note. "Particulate" is defined as a mass of discrete units of matter so small (generally of largest dimension <<1000 microns) that they are not ordinarily handled as individual units, and whose shape and length-to-diameter ratio are such that in the dry state the particles will not hold together as a coherent article without the application of pressure or heat.

SEE OR SEARCH CLASS:
136, Batteries: Thermoelectric or Photoelectric, subclass 250 for a photoelectric device having a particulate or spherical semiconductor component.

64 Packaging (e.g., with mounting, encapsulating, etc.) or treatment of packaged semiconductor:
This subclass is indented under subclass 57. Process provided including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

(1) Note. The term packaging connotes the integration/assembly of the semiconductive substrate/chip/die with a preformed housing, capsule, or support.

SEE OR SEARCH THIS CLASS, SUBCLASS:
106 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device.

65 Having additional optical element (e.g., optical fiber, etc.):
This subclass is indented under subclass 64. Process for packaging a semiconductor device responsive to electromagnetic radiation wherein the device has combined therewith one or more optical elements to transmit or modify electromagnetic radiation incident upon the semiconductor device and the optical element is fixed or attached to the device or the housing or support thereof.

SEE OR SEARCH CLASS:
65, Glass Manufacturing, especially subclass 406 for processes which involve assembling at least two individually distinct optical fibers, waveguides, or preforms directly to each other (e.g., coupling, etc.).
323, Electricity: Power Supply or Regulation Systems, subclass 902 for optical coupling to a semiconductor.

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66 Plural responsive devices (e.g., array, etc.):
This subclass is indented under subclass 64. Process for packaging a multiplicity of devices or elements responsive to electromagnetic radiation into a coherent monolith.

(1) Note. The plural responsive devices may be combined via a hybrid construction or secured onto a common support.

67 Assembly of plural semiconductor substrates:
This subclass is indented under subclass 66. Process having a step of joining multiple semiconductor substrates into a coherent monolith in which plural devices responsive to electromagnetic radiation are formed.

68 Substrate dicing:
This subclass is indented under subclass 57. Process having a step of dividing the semiconductor substrate into multiple separate bodies.

(1) Note. The dicing may be done by any manner, such as abrading, sawing, etching, cleavage, or a combination thereof.

SEE OR SEARCH CLASS:
83, Cutting, for generic processes of cutting a substrate into discrete individual units.
225, Severing by Tearing or Breaking, subclasses 1+ for methods.
451, Abrading, for a process of dicing by abrading.

69 Including integrally formed optical element (e.g., reflective layer, luminescent layer, etc.):
This subclass is indented under subclass 57. Process for making a semiconductor device responsive to electromagnetic radiation wherein the device has combined therewith one or more integrally formed optical elements to transmit or modify electromagnetic radiation incident upon the semiconductor device

70 Color filter:
This subclass is indented under subclass 69. Process for making a semiconductor device responsive to electromagnetic radiation having combined therewith structural means functioning as a color filter element.

71 Specific surface topography (e.g., textured surface, etc.):
This subclass is indented under subclass 69. Process having a surface of specified topography incorporated into an electromagnetic sensitive device or utilized during manufacture thereof.

72 Having reflective or antireflective component:
This subclass is indented under subclass 69. Process for making a semiconductor device responsive to electromagnetic radiation having a component which has reflective or antireflective properties with respect to electromagnetic radiation incident thereupon.

73 Making electromagnetic responsive array:
This subclass is indented under subclass 57. Process for making a collection or grouping of electromagnetically responsive devices on a single, coherent, semiconductor substrate.

(1) Note. Individual detectors of the array may alternatively be referred to as elements, pixels, or cells.

74 Vertically arranged (e.g., tandem, stacked, etc.):
This subclass is indented under subclass 73. Process wherein the array of electromagnetic responsive devices is configured with one responsive device residing at a position over another such device.

75 Charge transfer device (e.g., CCD, etc.):
This subclass is indented under subclass 73. Process for making a structure in which storage sites for packets of electrical charge are induced at or below the semiconductor surface by an electric field applied by serially arranged gate electrodes formed thereupon and wherein carrier potential energy per unit charge minima are established at a given storage site and such minima are transferred in a serial manner via an active channel region to one or more adjacent storage sites.

76 Majority signal carrier (e.g., buried or bulk channel, peristaltic, etc.):
This subclass is indented under subclass 75. Process for making a charge transfer device wherein the transfer of such charge minima is

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by majority carriers of the semiconductive material (i.e., by electrons in n-type material or by holes in p-type semiconductive material) and such transfer is in response to electromagnetic radiation incident to the device.

77 Compound semiconductor:
This subclass is indented under subclass 75. Process for making a charge transfer device in which the storage sites are composed of a compound semiconductor material.

78 Having structure to improve output signal (e.g., exposure control structure, etc.):
This subclass is indented under subclass 75. Process for making a charge transfer device which contains structural means to improve the electrical signal it generates in response to the electromagnetic radiation.

(1) Note. The structural means to improve the output signal may serve to control the amount of light incident on the device which is transferred as output signal charge.

79 Having blooming suppression structure (e.g., antiblooming drain, etc.):
This subclass is indented under subclass 78. Process for making a charge transfer device wherein the structural means to improve the output signal prevents spill over of a large amount of signal charge generated at a storage site which receives an electromagnetic radiation responsive input signal of very high intensity to adjacent storage sites.

(1) Note. The antiblooming suppression structure may include a drain structure for removing charge from storage sites.

(2) Note. The antiblooming drain structure may be located in the device beneath storage sites rather than on its surface.

80 Lateral series connected array:
This subclass is indented under subclass 73. Process wherein the array of electromagnetically responsive devices is laterally arranged and serially electrically connected.

81 Specified shape junction barrier (e.g., V-grooved junction, etc.):
This subclass is indented under subclass 80. Process wherein the junction barrier interface (i.e., between adjoining semiconductor regions of opposite conductivity type) has a specified geometrical configuration.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 465 for a light-responsive active solid-state device having a barrier junction of specified geometrical configuration and subclasses 653+ for an active solid-state device having a specified shape PN junction.

82 Having organic semiconductor component:
This subclass is indented under subclass 57. Process wherein the semiconductor substrate contains a semiconductive compound in which the molecule is characterized by two or more carbon atoms bonded together, one atom of carbon bonded to at least one atom of hydrogen or halogen (i.e., chlorine, fluorine, bromine, iodine) or one atom of carbon bonded to at least one atom of nitrogen by a single or double bond.

(1) Note. Exceptions to this rule include HCN, CN-CN, HNCO, HNCS, cyanogen halides, cyanamide, fulminic acid, and metal carbides. These are not regarded as organic materials. Also, note that graphite and diamond are not regarded as organic semiconductors, since they are not compounds; silicon carbide is not regarded as organic.

83 Forming point contact:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation including forming a potential barrier between an electrode of small contacting or cross-sectional area in touching relationship with a substantially larger area of the semiconductor substrate, thus forming a potential barrier junction at the single point therebetween.

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84 Having selenium or tellurium elemental semiconductor component:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation utilizing a semiconductor substrate containing semiconductive selenium or tellurium in elemental form (i.e., not in a compound) or an alloy (i.e., mixture) thereof.

85 Having metal oxide or copper sulfide compound semiconductive component:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation utilizing a semiconductor substrate containing a metal oxide or copper sulfide compound semiconductor.

86 And cadmium sulfide compound semiconductive component:
This subclass is indented under subclass 85. Process wherein the semiconductor substrate containing a metal oxide or copper sulfide compound semiconductor additionally contains a cadmium sulfide compound semiconductor.

87 Graded composition:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation wherein the chemical composition of a semiconductor region of the substrate varies with location within the semiconductive region.

88 Direct application of electric current:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a step of directly applying electrical current to the semiconductor substrate.

89 Fusion or solidification of semiconductor region:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a step of fusing or solidifying a semiconductive region of the substrate.

90 Including storage of electrical charge in substrate:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a step of storing electrical charge in a region of the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
19 for a process of making a semiconductor electrical device having formed therewith an integral battery or power source.

91 Avalanche diode:
This subclass is indented under subclass 57. Process for making a device which is configured to operate in a manner in which an external voltage applied in the reverse-conducting direction of the device junction with sufficient magnitude causes the potential barrier at the junction to breakdown due to electrons or holes gaining sufficient speed to dislodge valence electrons and thus create more hole-electron current carriers resulting in a sudden change from high dynamic electrical resistance to very low dynamic resistance.

(1) Note. The terms Zener diode and Zener breakdown voltage are used rather loosely in that the breakdown mechanism above about 6 volts is thought to be due to avalanching and that below about 6 volts is thought to be due essentially to tunnelling.

SEE OR SEARCH THIS CLASS, SUBCLASS:
380 for a process of making an avalanche diode which is not responsive to electromagnetic radiation.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 199 for an avalanche diode in a noncharge transfer device having a heterojunction, subclass 438 for a light-responsive avalanche junction device, subclass 481 for an avalanche diode having a Schottky barrier, subclass 551 for an avalanche diode used as a voltage reference element combined with pn junction isolation means in an integrated circuit, and subclasses 603+ for avalanche diodes in general.

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92 Schottky barrier junction:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a Schottky rectifying junction.

93 Compound semiconductor:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a compound semiconductor.

94 Heterojunction:
This subclass is indented under subclass 93. Process for making a device responsive to electromagnetic radiation having a interface between two dissimilar semiconductor materials, at least one of which is a compound semiconductor, to constitute a junction.

95 Chalcogenide (i.e., oxygen (O), sulfur (S), selenium (Se), tellurium (Te)) containing:
This subclass is indented under subclass 93. Process wherein the compound semiconductor contains an element from the group of oxygen, sulfur, selenium, and tellurium.

96 Amorphous semiconductor:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having an amorphous semiconductor component.

97 Polycrystalline semiconductor:
This subclass is indented under subclass 57. Process for making a device responsive to electromagnetic radiation having a polycrystalline semiconductor component.

98 Contact formation (i.e., metallization):
This subclass is indented under subclass 57. Process for making a semiconductor device responsive to electromagnetic radiation having a step of coating the device with electrically conductive material forming an electrical connect or conductor thereto.

(1) Note. The electrically conductive material may additionally be transparent to electromagnetic radiation.

99 HAVING ORGANIC SEMICONDUCTIVE COMPONENT:
This subclass is indented under the class definition. Process for making a semiconductor electrical device wherein the semiconductor substrate contains a semiconductive compound in which the molecule is characterized by two or more carbon atoms bonded together, one atom of carbon bonded to at least one atom of hydrogen or halogen (i.e., chlorine, fluorine, bromine, iodine) or one atom of carbon bonded to at least one atom of nitrogen by a single or double bond.

(1) Note. Exceptions to this rule include HCN, CN-CN, HNCO, HNCS, cyanogen halides, cyanamide, fulminic acid, and metal carbides. These are not regarded as organic materials. Also, note that graphite and diamond are not regarded as organic semiconductors, since they are not compounds; silicon carbide is not regarded as organic.

SEE OR SEARCH THIS CLASS, SUBCLASS:
82 for a process of making a device having an organic semiconductive component which is responsive to electromagnetic radiation.

SEE OR SEARCH CLASS:
29, Metal Working, subclass 25.03 for a process of making an electrolytic capacitor using a solid organic semiconductor.
136, Batteries: Thermoelectric and Photoelectric, subclass 263 for photoelectric cells containing organic active material.
252, Compositions, subclass 62.3 for organic barrier layer device compositions.
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 40 for an active solid-state device having an organic semiconductor.

100 MAKING POINT CONTACT DEVICE:
This subclass is indented under the class definition. Process for making a semiconductor electrical device having a potential barrier

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between an electrode of small contacting or cross-sectional area in touching relationship with a substantially larger area of the semiconductor substrate, thus forming a potential barrier junction at the single point of contact therebetween.

SEE OR SEARCH THIS CLASS, SUBCLASS:

83 for a process of making a point contact device which is responsive to electromagnetic radiation.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 41 for a point contact device.

101 Direct application of electrical current:

This subclass is indented under subclass 100. Process including a step of directly applying electrical current to the point contact semiconductor electrical device.

102 HAVING SELENIUM OR TELLURIUM ELEMENTAL SEMICONDUCTOR COMPONENT:

This subclass is indented under the class definition. Process for making a semiconductor electrical device wherein the semiconductor substrate is comprised of semiconductive selenium or tellurium in elemental form (i.e., not in a compound) or an alloy (i.e., mixture) thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:

84 for a process of making a device responsive to electromagnetic radiation comprised of semiconductive selenium or tellurium in elemental form or an alloy thereof.

SEE OR SEARCH CLASS:

252, Compositions, subclass 62.3 for barrier layer device compositions containing free elemental selenium or tellurium.

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 42 for a device having elemental selenium or tellurium semiconductor.

420, Alloys or Metallic Compositions, subclass 579 for selenium or tellurium base alloy containing metal.

103 Direct application of electrical current:

This subclass is indented under subclass 102. Process having a step of directly applying electrical current to the selenium or tellurium elemental semiconductor component substrate.

104 HAVING METAL OXIDE OR COPPER SULFIDE COMPOUND SEMICONDUCTOR COMPONENT:

This subclass is indented under the class definition. Process for making a semiconductor electrical device wherein the semiconductor substrate contains a metal oxide or copper sulfide compound semiconductor.

SEE OR SEARCH THIS CLASS, SUBCLASS:

85 for a process of making a device responsive to electromagnetic radiation having a metal oxide or copper sulfide compound semiconductor component.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 43 for a semiconductor solid-state device having a metal oxide or copper sulfide compound semiconductor component.

264, Plastic and Nonmetallic Article Shaping or Treating: Processes, subclass 61 for methods of vitrifying or sintering an inorganic preform to make a discrete passive device (e.g., multilayer ceramic capacitor, etc.).

105 HAVING DIAMOND SEMICONDUCTOR COMPONENT:

This subclass is indented under the class definition. Process for making a semiconductor electrical device wherein the semiconductor substrate contains a diamond semiconductor component.

(1) Note. The utilization of a diamond component for other than its semiconductor properties (e.g., as a thermal heat sink) is not proper for this subclass.

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SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 77, for a solid-state device having a diamond semiconductor component.

106 PACKAGING (E.G., WITH MOUNTING, ENCAPSULATING, ETC.) OR TREATMENT OF PACKAGED SEMICONDUCTOR:

This subclass is indented under the class definition. Process provided including (a) multiple operations having a step of permanently attaching or securing a semiconductive substrate to a terminal, elongated conductor, or support (e.g., a mounting, housing, lead frame, discrete heat sink, etc.), (b) multiple operations having a step of shaping flowable plastic or flowable insulative material about a semiconductive substrate, or (c) a step of treating an already mounted or packaged semiconductor substrate (e.g., coating of flowable plastic or flowable insulative material about a semiconductor substrate by dipping, etc.).

(1) Note. Packaging is a semiconductor art manufacturing term for integration, assembly, or surrounding of a semiconductor substrate (e.g., chip, die, etc.) with a permanent encasement, housing, capsule, or support. This is distinguished from package making found in Class 53 which is directed to preparing a manufactured product for passage through the channels of trade in a safe, convenient, and attractive condition, usually wrapped in a cover or in a container which is intended to be removed when the manufactured product is used.

(2) Note. See References to Other Classes in the class definition, for a listing of various related classes providing for unit or combined operations.

(3) Note. See References to Other Classes in the class definition, for a listing of various related classes providing for electrical connectors, electrical device housing or packaging, etc.

SEE OR SEARCH THIS CLASS, SUBCLASS:

26 for a process of packaging (e.g., with mounting, encapsulating, etc.)or treating a packaged semiconductor device or circuit emissive of a nonelectrical signal.

51 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device responsive to physical stress.

55 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a thermally responsive semiconductor electrical device.

64 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a semiconductor device or circuit responsive to electromagnetic radiation.

100 for a process of manufacturing a point-contact-type semiconductor device.

616 for a process of transcribing bump electrodes which substantially do not retain their contour following transfer from a carrier substrate (e.g., template, etc.) to a semiconductor substrate.

SEE OR SEARCH CLASS:

29, Metal Working, especially subclass 827 for lead frame or beam lead device manufacture, subclasses 829+ for the assembly of an electrical component to an insulative base having a conductive path applied thereto, or formed thereon or therein (e.g., a printed circuit board), subclasses 854+ for the assembly of an electrical component directly to terminal or elongated conductor, and subclasses 729+ for an electrical device manufacturing apparatus.

53, Package Making, subclasses 396+ for methods of encompassing, encasing, or completely surrounding goods or materials with a cover made from sheet material stock, and for methods of assembling or securing a separate closure (hood, cap, capsule, crown, seal, etc.) to the aperture of a pre-

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formed receptacle so as to complete the encasement of contents.

65, Glass Manufacturing, especially subclasses 36+ for a process of fusion bonding of glass to a formed part, and subclass 155 for electronic device making means involving fusion bonding.

148, Metal Treatment, for a process of treating metal to modify or maintain the internal physical structure (i.e., microstructure) or chemical properties of metal.

156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 60+ for a single step process of adhesively bonding and for certain multistep processes having a step of adhesively bonding a nominal semiconductive chip or wafer.

216, Etching a Substrate: Processes, especially subclasses 13+ for processes of manufacturing a printed circuit board or thick film circuit board involving an etching step.

219, Electric Heating, subclasses 78.01+ for process and apparatus for bonding by electrical current and pressure.

228, Metal Fusion Bonding, appropriate subclasses, for a process of fusion bonding and additional operations which are considered to be ancillary to the bonding (preheating, positioning, pretinning, etc.) of a semiconductive substrate, especially subclass 123.1 and 179.1+.

264, Plastic and Nonmetallic Article Shaping or Treating: Processes, for a process (and steps perfecting same) of shaping plastic or nonmetallic material and uniting it to a preform (e.g., encapsulating), said preform being a semiconductive substrate.

324, Electricity: Measuring and Testing, for a process of temporarily affixing a semiconductor substrate to a support during the electrical testing thereof.

427, Coating Processes, subclasses 96.1 through 99.5 for a process of coating a <u>nonsemiconductive</u> substrate to produce an integrated or printed circuit or circuit board (e.g., coating an insulative substrate to form a printed or thick film circuit board, etc.).

107 Assembly of plural semiconductive substrates each possessing electrical device:
This subclass is indented under subclass 106. Process wherein plural semiconductive substrates are combined into a hybrid construction or secured onto a common support.

SEE OR SEARCH THIS CLASS, SUBCLASS:

455 for a nonpackaging process of joining or bonding plural semiconductive substrates wherein none of the semiconductive substrates are intended to function as a terminal, elongated conductor, or support.

108 Flip-chip-type assembly:
This subclass is indented under subclass 107. Process wherein a semiconductive substrate which has electric contacts on the top side thereof is flipped to juxtapose the contacts in face-to-face orientation with a substrate which has matching electrical contacts prior to bonding.

109 Stacked array (e.g., rectifier, etc.):
This subclass is indented under subclass 107. Process for making a semiconductor device wherein a multiplicity of semiconductive substrates are juxtaposed in face-to-face orientation.

110 Making plural separate devices:
This subclass is indented under subclass 106. Process for making a semiconductor device wherein a multiplicity of separate semiconductive devices are obtained.

111 Using strip lead frame:
This subclass is indented under subclass 110. Process for making plural separate semiconductor devices utilizing a plurality of support structures or positions arranged on an elongated continuum prior to separation.

(1) Note. The continuum may either be the material of the lead frame (e.g., metal strip) or the lead frame may be mounted serially on another continuum (e.g., plastic strip).

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112 And encapsulating:
This subclass is indented under subclass 111. Process including a step of surrounding the semiconductor substrate with an electrically insulating material which forms a sealed encasement therefor.

113 Substrate dicing:
This subclass is indented under subclass 110. Process wherein a semiconductive substrate is divided into discrete individual units.

(1) Note. The dicing may be done by any manner, such as abrading, sawing, etching, cleavage, or a combination thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
460 for a process under the class definition of dicing a semiconductor substrate into multiple separate bodies.

SEE OR SEARCH CLASS:
83, Cutting, for generic processes of cutting a substrate into discrete individual units.
225, Severing by Tearing or Breaking, subclasses 1+ for methods.
451, Abrading, for a process of dicing by abrading.

114 Utilizing a coating to perfect the dicing:
This subclass is indented under subclass 113. Process including a step of coating the semiconductive substrate to enhance the dicing operation.

115 Including contaminant removal or mitigation:
This subclass is indented under subclass 106. Process including the step of removing undesirable material through the use of a getter, desiccant, etc.

116 Having light transmissive window:
This subclass is indented under subclass 106. Process wherein the housing contains light transmissive means allowing light to reach the enclosed semiconductive device.

SEE OR SEARCH THIS CLASS, SUBCLASS:
64 for a process of packaging (e.g., with mounting, encapsulating, etc.) or treating a packaged semiconductor device responsive to electromagnetic radiation.

117 Incorporating resilient component (e.g., spring, etc.):
This subclass is indented under subclass 106. Process for packaging a semiconductor substrate wherein the resulting structure includes an elastically compressible component.

118 Including adhesive bonding step:
This subclass is indented under subclass 106. Process for packaging a semiconductor substrate including a step of joining the semiconductor substrate to a another body by nonmetallic bonding.

(1) Note. See Lines With Other Classes, “Packaging (e.g., With Mounting, Encapsulating, etc.) or Treatment of Packaged Semiconductor” above. Also see the search notes below.

SEE OR SEARCH CLASS:
156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 60+ for a step of surface bonding or assembly therefor, and the Class 156 definition for special lines to Class 29, Metal Working.

119 Electrically conductive adhesive:
This subclass is indented under subclass 118. Process wherein the nonmetallic bonding material is electrically conductive.

(1) Note. The nonmetallic bonding material may possess particulate metal dispersed in the nonmetallic adhesive binder to render the composition electrically conductive.

120 With vibration step:
This subclass is indented under subclass 106. Process for packaging a semiconductor substrate including a step of applying vibratory energy.

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121 Metallic housing or support:
This subclass is indented under subclass 106. Process for mounting, packaging, or encapsulating a semiconductor device wherein a semiconductive substrate is supported or enclosed by joining the substrate to a metallic body.

122 Possessing thermal dissipation structure (i.e., heat sink):
This subclass is indented under subclass 121. Process wherein the metallic body joined to the semiconductor substrate possesses structure for the dissipation of thermal energy generated during operation of the electrical device.

SEE OR SEARCH THIS CLASS, SUBCLASS:
584 for a process of coating a semiconductor substrate with a thermally conductive material (e.g., plated heat sink, etc.)

123 Lead frame:
This subclass is indented under subclass 121. Process wherein the metallic body joined to the semiconductor device is in the form of a metallic support with electrically conductive leads depending therefrom.

124 And encapsulating:
This subclass is indented under subclass 121. Process including a step of surrounding the semiconductor substrate or the metallic housing or support with an electrically insulating material which forms a sealed encasement therefor.

125 Insulative housing or support:
This subclass is indented under subclass 106. Process for making a structure wherein the semiconductive device is supported or enclosed by preformed insulative body.

(1) Note. An encapsulant, per se, is not considered to be a supporting structure proper for this and indented subclasses.

126 And encapsulating:
This subclass is indented under subclass 125. Process including a step of surrounding the semiconductor substrate or insulative housing or support with an electrically insulating material which forms a sealed encasement therefor.

127 Encapsulating:
This subclass is indented under subclass 106. Process including a step of surrounding the semiconductor substrate with an electrically insulating material which forms a sealed encasement therefor.

SEE OR SEARCH CLASS:
65, Glass Manufacturing, for a per se process of shaping glass material about an electrical device to encapsulate same.
264, Plastic and Nonmetallic Article Shaping or Treating: Processes, especially subclasses 272.11+ for per se electrical component encapsulating by molding of insulative material about the electrical component.

128 MAKING DEVICE ARRAY AND SELECTIVELY INTERCONNECTING:
This subclass is indented under the class definition. Process for forming an array of active devices on a semiconductor substrate and electrically interconnecting the devices into a designated circuit arrangement.

(1) Note. The processes found in this and its indented subclasses result in circuits which are alter-natively referred to as personalized, customized, or application specific.

(2) Note. This and its indented subclasses do not take processes of producing a shorted or shunted structure as an integral part of a single device.

SEE OR SEARCH THIS CLASS, SUBCLASS:
6 for processes of interconnecting plural devices wherein at least one operation is responsive to a sensed condition.
587 for process of forming an array of gate electrodes upon a semiconductor substrate.
598+, for a process of metallizing a semiconductor substrate wherein the electrically conductive metallization contains a portion which is alterable from the conductive to nonconductive condition or vice-versa (e.g., a fuse or antifuse).

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SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), particularly subclasses 202+ for gate arrays.

129 With electrical circuit layout:

This subclass is indented under subclass 128. Process including a step of designing the topological arrangement of arrayed device components or electrical conductors therebetween in combination with making the semiconductor device array.

SEE OR SEARCH CLASS:

369, Dynamic Information Storage or Retrieval, for processes of storing or retrieving dynamic information, subclasses 99+ for a particular detail of the information handling portion of a system, especially subclasses 100+ for radiation beam modification of or by a storage medium and subclass 126 for electrical modification or sensing of a storage medium (e.g., capacitive, resistive, or electrostatic discharge)

130 Rendering selected devices operable or inoperable:

This subclass is indented under subclass 128. Process wherein selected devices located on a semiconductive substrate are electrically completed or electrically shorted so as to be rendered operable or inoperable.

(1) Note. Adjusting an operating characteristic (e.g., threshold voltage) of selected devices so as to render them operational yet nonresponsive to the intended operating voltage is specifically excluded from herein.

SEE OR SEARCH THIS CLASS, SUBCLASS:

276 for processes of programming or encoding a grouping of insulated gate field effect transistors by altering the operative mode (enhancement type or depletion type) of selected transistors.

131 Using structure alterable to conductive state (i.e., antifuse):

This subclass is indented under subclass 128. Process for making an array of electrical devices and selectively interconnecting the devices via a structure which is alterable from a nonconductive state to a conductive state.

SEE OR SEARCH THIS CLASS, SUBCLASS:

467 for altering the conductivity of an antifuse element through the direct application of an electrical current.

600 for metallization processes forming a structure alterable to a conductive state.

132 Using structure alterable to nonconductive state (i.e., fuse):

This subclass is indented under subclass 128. Process for making an array of electrical devices and selectively interconnecting the devices via a structure which is alterable from a conductive state to a nonconductive state.

SEE OR SEARCH THIS CLASS, SUBCLASS:

467 for altering the conductivity of a fuse element through the direct application of electrical current.

601 for metallization processes forming a structure alterable to a nonconductive state.

SEE OR SEARCH CLASS:

327, Miscellaneous Active Electrical Nonlinear Devices, Circuits, and Systems, especially subclass 525 for a specific identifiable device, circuit, or system having as a part of it"s construction or arrangement a fusible link element.

365, Static Information Storage and Retrieval, subclass 96 for fusible links relating to programmable read-only memory and subclass 200 for eliminating “bad bit” information associated with read/write circuits.

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133 MAKING REGENERATIVE-TYPE SWITCHING DEVICE (E.G., SCR, IGBT, THYRISTOR, ETC.):

This subclass is indented under the class definition. Process for making a switching device structure acting as if it has two or more active emitter junctions each of which is associated with a separate, equivalent transistor having an individual gain and which, when initiated by a base region current, causes the equivalent transistors to mutually drive each other in a regenerative manner to lower the voltage drop between emitter regions.

(1) Note. If the current is above a level I_h, called the "holding current", then the device will remain ON when the triggering signal is removed by the regenerative feedback therebetween, and is then said to be "latched.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 107+ for a regenerative-type switching device.

361, Electricity: Electrical Systems and Devices, subclasses 100+ and 205 for circuits employing thyristors (e.g., silicon controlled rectifiers (SCRs))

363, Electric Power Conversion Systems, subclasses 27+, 54, 57+, 68, 85+, 96+, 128+, 135+, and 160+ for circuits employing thyristors (e.g., silicon controlled rectifiers (SCRs))

134 Bidirectional rectifier with control electrode (e.g., triac, diac, etc.):

This subclass is indented under subclass 133. Process for making a regenerative switching device having a control electrode which device can conduct in both the forward and reverse directions, being triggered into conduction by a pulse applied to the control electrode.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 119+ for a bidirectional rectifier with control electrode.

135 Having field effect structure:

This subclass is indented under subclass 133. Process wherein the regenerative switching device includes or is combined with a field effect structure (i.e., wherein the current through a active channel region is controlled by an electric field coming from a voltage which is applied between the gate and source terminals thereof).

(1) Note. Includes amplifying gate-type and optical turn-on-type structures.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 133+ for a regenerative device combined with a field effect transistor.

136 Junction gate:

This subclass is indented under subclass 135. Process for making a regenerative switching device which possesses a gate electrode which forms a PN (rectifying) junction with the semiconductor substrate.

137 Vertical channel:

This subclass is indented under subclass 136. Process for making a junction gate regenerative-type switching device wherein the active channel is configured to provide, in whole or in part, a vertically conductive pathway between source and drain regions.

138 Vertical channel:

This subclass is indented under subclass 135. Process for making a regenerative-type switching device wherein the active channel is configured to provide, in whole or in part, a vertically conductive pathway between source and drain regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:

268 for a process of making a vertical channel insulated gate field effect transistor.

139 Altering electrical characteristic:

This subclass is indented under subclass 133. Process having a step of altering an electrical characteristic of the regenerative-type switching device.

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140 Having structure increasing breakdown voltage (e.g., guard ring, field plate, etc.):
This subclass is indented under subclass 133. Process for making a regenerative switching device having a structure for increasing the breakdown voltage of the device (e.g., beveled junction, contoured edge, etc.).

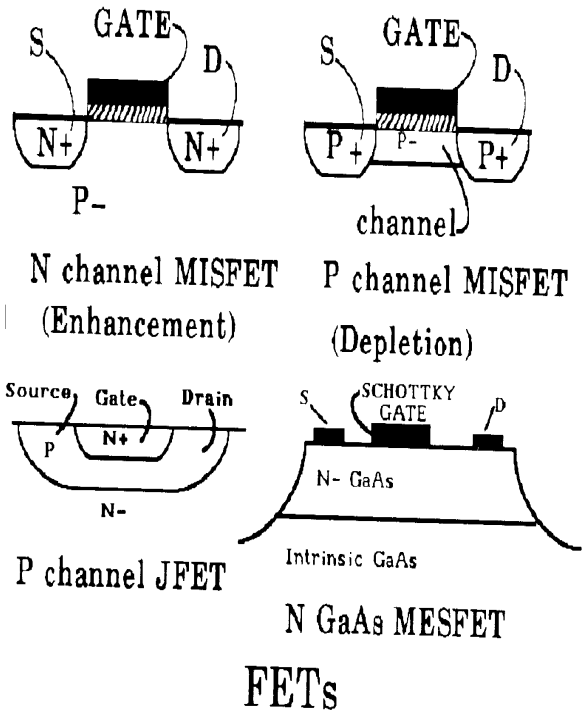
SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 168+ for a regenerative-type switching device having means to increase breakdown voltage.

141 MAKING CONDUCTIVITY MODULATION DEVICE (E.G., UNIJUNCTION TRANSISTOR, DOUBLE BASE DIODE, CONDUCTIVITY-MODULATED TRANSISTOR, ETC.):
This subclass is indented under the class definition. Process for making a conductivity modulation device structure which has a high resistivity semiconductor region of one conductivity-type having a region of opposite conductivity-type forming a pn junction with a central portion of the high resistivity region, with structural means provided to forward bias the pn junction to inject minority carriers into the high resistivity region to vary its conductivity producing modulated wave response (i.e., conductivity modulation).

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 212 for a conductivity modulation device.
388, Electricity: Motor Control Systems, subclass 919 for unijunction transistor circuit trigger control means.

142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS:
This subclass is indented under the class definition. Process for forming or altering a pair of device active regions (i.e., source or drain) separated by a gate structure intended to permit or block the flow of electrical current therebetween.

(1) Note. To be proper hereunder, the claim must include a positive recitation of (a) formation of semiconductive active regions or (b) altering the electrical properties of active semiconductive regions of the substrate.



SEE OR SEARCH THIS CLASS, SUBCLASS:
49 for a process of making a chemically sensitive field effect transistor (i.e., CHEMFET.)

143 Gettering of semiconductor substrate:
This subclass is indented under subclass 142. Process including a step of gettering the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
471 for process of gettering a semiconductor substrate, per se.

144 Charge transfer device (e.g., CCD, etc.):
This subclass is indented under subclass 142. Process for making a structure in which storage sites for packets of electrical charge are induced at or below the semiconductor surface

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by an electric field applied by serially arranged gate electrodes formed thereupon and wherein carrier potential energy per unit charge minima are established at a given storage site and such minima are transferred in a serial manner via an active channel region to one or more adjacent storage sites.

(1) Note. Included herein are devices commonly referred to as charge coupled devices as well as bucket brigade devices.

(2) Note. A field effect device of the charge injection-type (i.e., CID) that transfers the charge in a nonserial manner to the device substrate or the data bus is not proper hereunder.

SEE OR SEARCH THIS CLASS, SUBCLASS:

75 for a process of making a charge transfer device which is responsive to electromagnetic radiation.

587 for a process of making an array of gate electrodes upon a semiconductor substrate.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 215+ for a charge transfer device structure.

365, Static Information Storage and Retrieval, subclass 183 for a charge coupled memory.

377, Electrical Pulse Counters, Pulse Dividers, or Shift Registers: Circuits and Systems, subclasses 57+ for charge transfer device systems.

145 Having additional electrical device:
This subclass is indented under subclass 144. Process for making a charge transfer device structure in combination with an additional electrical device.

146 Majority signal carrier (e.g., buried or bulk channel, peristaltic, etc.):
This subclass is indented under subclass 144. Process for making a charge transfer device structure wherein the transfer of such charge minima is by majority carriers of the semiconductive material (i.e., by electrons in n-type material, and is by holes in p-type semiconductive material).

147 Changing width or direction of channel (e.g., meandering channel, etc.):
This subclass is indented under subclass 144. Process for making a charge transfer device structure wherein the active channel region changes its width or direction throughout all or part of the distance between adjacent storage sites.

148 Substantially incomplete signal charge transfer (e.g., bucket brigade, etc.):
This subclass is indented under subclass 144. Process for making a charge transfer device structure wherein the charge transferred is less than the entire charge stored in the storage site from which it originates.

149 On insulating substrate or layer (e.g., TFT, etc.):
This subclass is indented under subclass 142. Process for making a field effect transistor from a semiconductive layer formed upon an insulating substrate (for example, glass or sapphire) or an insulating layer.

SEE OR SEARCH THIS CLASS, SUBCLASS:

30 for process of making a device or circuit emissive of nonelectrical signal comprising an array of field effect transistors on an insulating substrate combined with a liquid crystal optical material.

150 Specified crystallographic orientation:
This subclass is indented under subclass 149. Process wherein a given feature of the field effect device on an insulating substrate or layer is formed in a definite crystallographic relationship relative to the insulating substrate or layer or the semiconductor layer thereupon.

151 Having insulated gate:
This subclass is indented under subclass 149. Process for making an insulated gate field effect transistor from a semiconductive layer formed upon an insulating substrate (for example, glass or sapphire) or an insulating layer.

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152 Combined with electrical device not on insulating substrate or layer:
This subclass is indented under subclass 151. Process for making a field effect transistor formed on an insulating substrate or layer combined with an additional electrical device which is not formed upon an insulating substrate or layer.

(1) Note. The electrical device not on an insulating substrate or layer is often referred to as a bulk device while the electrical device on the insulating substrate or layer is often referred to as a thin film device with the combined structure either horizontally disposed or vertically stacked (i.e., 3-dimensional).

SEE OR SEARCH THIS CLASS, SUBCLASS:
155 for a process of making a field effect transistor on an insulating substrate or layer and an additional electrical device on an insulating substrate or layer.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 350+ for an insulated gate field effect device formed on a single crystal semiconductor layer on an insulating substrate combined with a diverse-type device structure.

153 Complementary field effect transistors:
This subclass is indented under subclass 152. Process for making plural field effect transistors of opposite conductivity type (i.e., wherein source and drain regions of a first field effect transistor are of opposite conductivity type to source and drain regions of a second field effect transistor).

154 Complementary field effect transistors:
This subclass is indented under subclass 151. Process for making plural field effect transistors of opposite conductivity type (i.e., wherein source and drain regions of a first field effect transistor are of opposite conductivity type to source and drain regions of a second field effect transistor).

155 And additional electrical device on insulating substrate or layer:
This subclass is indented under subclass 151. Process for making a field effect transistor formed on an insulating layer or substrate combined with an additional electrical device which is also formed on an insulating substrate or layer.

(1) Note. The additional electrical device must be other than an insulated gate field effect transistor if formed utilizing the same semiconductive layer or may be any type of electrical device if formed utilizing a different semiconductive layer with the structure formed referred to as a vertically stacked or 3-dimensional structure.

SEE OR SEARCH THIS CLASS, SUBCLASS:
152 for a process of making a field effect transistor on an insulating substrate or layer and an additional electrical device not on an insulating substrate or layer.

156 Vertical channel:
This subclass is indented under subclass 151. Process for making a junction gate field effect transistor wherein the active channel is configured to provide, in whole or in part, a vertically conductive pathway between source and drain regions.

157 Plural gate electrodes (e.g., dual gate, etc.):
This subclass is indented under subclass 151. Process for making a field effect transistor formed on an insulating layer or substrate wherein plural insulated gate electrodes on either the same or opposite sides of the active channel region serve to control the electrical conduction characteristics of the semiconductive active channel region.

SEE OR SEARCH THIS CLASS, SUBCLASS:
283 for a process of making an insulated gate field effect transistor having either dual gate or opposed gate structure.

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158 Inverted transistor structure:
This subclass is indented under subclass 151. Process for making a field effect transistor formed on an insulating substrate or layer wherein the gate electrode of the field effect transistor is formed so as to be in direct contact with the insulating substrate or layer.

159 Source-to-gate or drain-to-gate overlap:
This subclass is indented under subclass 158. Process wherein the source or drain regions or layers of the inverted field effect transistor are formed so as to extend over a portion of the gate electrode formed on the insulating substrate or layer.

160 Utilizing backside irradiation:
This subclass is indented under subclass 158. Process wherein single or multiple layers formed over the gate are patterned by irradiating a photoresist layer with a radiation source located on the opposite side of the substrate from which the gate is formed.

161 Including source or drain electrode formation prior to semiconductor layer formation (i.e., staggered electrodes):
This subclass is indented under subclass 151. Process wherein the source or drain electrodes of the field effect transistor are formed on the insulating substrate or layer prior to the deposition of a semiconductive layer.

162 Introduction of nondopant into semiconductor layer:
This subclass is indented under subclass 151. Process wherein a nonelectrically active impurity (i.e., one that does not change the electrically properties) is introduced into the semiconductive layer.

163 Adjusting channel dimension (e.g., providing lightly doped source or drain region, etc.):
This subclass is indented under subclass 151. Process wherein a particular dimension of the active channel region of the field effect transistor (e.g., thickness, length, etc.) is adjusted.

164 Semiconductor islands formed upon insulating substrate or layer (e.g., mesa formation, etc.):
This subclass is indented under subclass 151. Process wherein the semiconductor layer selectively deposited or deposited and subsequently patterned to form a semiconductive region electrically isolated from laterally adjoining semiconductor regions.

(1) Note. The separate laterally adjacent semiconductor layers are each intended to possess a single field effect transistor and be electrically isolated with respect to one another prior to electrically interconnecting.

165 Including differential oxidation:
This subclass is indented under subclass 164. Process in which the patterning of the semiconductive layer includes a step of oxidizing the semiconductive layer to form regions of differing oxide thickness.

166 Including recrystallization step:
This subclass is indented under subclass 151. Process wherein the crystalline structure of the semiconductive layer is altered or modified (e.g., from amorphous to polycrystalline or single crystalline).

SEE OR SEARCH THIS CLASS, SUBCLASS:
150 for a process of making a field effect transistor on an insulating substrate or layer having a specified crystallographic orientation.

167 Having Schottky gate (e.g., MESFET, HEMT, etc.):
This subclass is indented under subclass 142. Process for making a field effect transistor which possesses a gate which forms a metal-semiconductor rectifying junction with the underlying semiconductive active channel region.

168 Specified crystallographic orientation:
This subclass is indented under subclass 167. Process wherein a given feature of the Schottky gate field effect device is formed in a definite crystallographic orientation relative to the substrate.

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(1) Note. Processes of making a transistor in a semiconductor substrate of given orientation are not sufficient for placement in this subclass.

169 Complementary Schottky gate field effect transistors:
This subclass is indented under subclass 167. Process for making plural Schottky gate field effect transistors of opposite conductivity type (i.e., wherein source and drain regions of a first field effect transistor are of opposite conductivity type to source and drain regions of a second field effect transistor).

170 And bipolar device:
This subclass is indented under subclass 167. Process for making a bipolar transistor in addition to the Schottky gate field effect transistor.

171 And passive electrical device (e.g., resistor, capacitor, etc.):
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor having combined therewith an electrical device or element in which charge carriers do not change their energy levels and do not provide electrical rectification, amplification, or switching, but which does react to voltage and current input.

172 Having heterojunction (e.g., HEMT, MODFET, etc.):
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein the Schottky gate field effect transistor possesses an interface between two dissimilar semiconductor materials which constitute a junction.

173 Vertical channel:
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein the active channel is configured to provide, in whole or in part, a vertically conductive pathway between source and drain regions.

174 Doping of semiconductive channel region beneath gate (e.g., threshold voltage adjustment, etc.):
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor having a step of introducing an electrically active dopant species into the semiconductor channel region beneath the gate electrode.

(1) Note. To be proper herein, the transistor channel region must possess semiconductive characteristics prior to the introduction of the dopant.

175 Buried channel:
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein the channel formed between the source and drain regions is configured so as to be buried beneath the semiconductor substrate surface.

176 Plural gate electrodes (e.g., dual gate, etc.):
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein plural gate electrodes on either the same or opposite side of the active channel region serve to control the electrical conduction characteristics of the semiconductive active channel region.

177 Closed or loop gate:
This subclass is indented under subclass 167. Process for making a Schottky field effect transistor wherein the gate electrode is configured such that it closes upon itself to thereby totally surround one of the device active regions.

178 Elemental semiconductor:
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein the gate electrode is formed upon an elemental semiconductor active channel region.

179 Asymmetric:
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein the pair of active regions are off-set or nonsymmetrical with respect to the centerline of the Schottky gate electrode.

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180 Self-aligned:
This subclass is indented under subclass 167. Process for making a Schottky gate field effect transistor wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

(1) Note. A self-aligned gate is one which is aligned between the source and drain via a masking process which uses the gate material itself to achieve the registration of the related device regions.

181 Doping of semiconductive region:
This subclass is indented under subclass 180. Process wherein a semiconductive region of the substrate is changed in electrical properties by introduction of an electrically active impurity.

182 T-gate:
This subclass is indented under subclass 181. Process wherein a T-shaped gate structure is formed or utilized at any stage in the process.

183 Dummy gate:
This subclass is indented under subclass 181. Process wherein a temporary gate is formed or utilized at any stage in the process and is intended to be removed or have no function in the final device.

184 Utilizing gate sidewall structure:
This subclass is indented under subclass 181. Process wherein a gate sidewall structure is utilized during the doping of semiconductive regions adjacent the gate structure.

(1) Note. The sidewall structure may function as a masking layer or dopant source during the self-aligned doping step.

185 Multiple doping steps:
This subclass is indented under subclass 184. Process including plural steps of doping the semiconductive regions of the substrate.

186 Having junction gate (e.g., JFET, SIT, etc.):
This subclass is indented under subclass 142. Process for making a field effect transistor which possesses a gate electrode which forms a PN (rectifying) junction with the semiconductor active channel region.

187 Specified crystallographic orientation:
This subclass is indented under subclass 186. Process wherein a given feature of the junction gate field effect device is formed in a definite crystallographic orientation relative to the substrate.

(1) Note. Processes of making a transistor in a semiconductor substrate of given orientation are not sufficient for placement in this subclass.

188 Complementary junction gate field effect transistors:
This subclass is indented under subclass 186. Process for making plural junction gate field effect transistors of opposite conductivity type (i.e., wherein source and drain regions of a first field effect transistor are of opposite conductivity type to source and drain regions of a second field effect transistor).

189 And bipolar transistor:
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor which additionally contains a bipolar transistor.

190 And passive device (e.g., resistor, capacitor, etc.):
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor having combined therewith an electrical device or component in which charge carriers do not change their energy levels and do not provide electrical rectification, amplification, or switching, but which does react to voltage and current input.

191 Having heterojunction:
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor which possesses an interface between two dissimilar semiconductor materials which constitute a junction.

192 Vertical channel:
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor wherein the active channel is configured to provide, in whole or in part, a vertically

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conductive pathway between source and drain regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
347 for a process of making a permeable base bipolar transistor.

193 Multiple parallel current paths (e.g., grid gate, etc.):
This subclass is indented under subclass 192. Process for making a junction gate field effect transistor wherein the junction gate which controls the vertical channel consists of a plurality of parallel current paths.

194 Doping of semiconductive channel region beneath gate (e.g., threshold voltage adjustment, etc.):
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor having a step of introducing an electrically active dopant species into the semiconductor channel region beneath the gate electrode.

(1) Note. To be proper herein, the transistor channel region must possess semiconductive characteristics prior to the introduction of the dopant.

195 Plural gate electrodes:
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor having plural gate electrodes on either the same or opposite side of the active channel region which serve to control the electrical conduction characteristics of the semiconductive active channel region.

196 Including isolation structure:
This subclass is indented under subclass 186. Process for making a junction gate field effect transistor having a structure which serves to at least partially electrically isolate the semiconductor region in which the device is formed from laterally adjacent semiconductive regions.

197 Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.):
This subclass is indented under subclass 142. Process for making a field effect transistor wherein the gate electrode is electrically insulated from the semiconductive substrate, that portion of the semiconductive substrate therebeneath being the active channel region separating source and drain.

SEE OR SEARCH THIS CLASS, SUBCLASS:
151 for a process of making an insulated gate field effect transistor on an insulating substrate or layer
585 for insulated gate metallization processes, per se.

198 Specified crystallographic orientation:
This subclass is indented under subclass 197. Process wherein a given feature of the junction gate field effect device is formed in a definite crystallographic orientation relative to the substrate.

(1) Note. Processes of making a transistor in a semiconductor substrate of given orientation are not sufficient for placement in this subclass.

199 Complementary insulated gate field effect transistors (i.e., CMOS):
This subclass is indented under subclass 197. Process for making plural insulated gate field effect transistors of opposite conductivity type (i.e., wherein source and drain regions of a first field effect transistor are of opposite conductivity type to source and drain regions of a second field effect transistor).

200 And additional electrical device:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors having combined therewith an additional electrical device.

201 Including insulated gate field effect transistor having gate surrounded by dielectric (i.e., floating gate):
This subclass is indented under subclass 200. Process for making complementary insulated gate field effect transistors having combined therewith an additional insulated gate field effect transistor possessing a gate electrode enclosed by dielectric.

(1) Note. Usually, the floating gate electrode is located (a) above and insulated from the channel region and (b) below

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and insulated from a controlling gate electrode. A floating gate electrode, due to accumulated electrical influence derived from the controlling gate electrode, provides on-off operation of the channel region. Floating gate arrangements are prevalent in ultraviolet erasable programmable read-only memory devices (i.e., EPROMs)

202 Including bipolar transistor (i.e., BiCMOS):
This subclass is indented under subclass 200. Process for making complementary insulated gate field effect transistors combined with a bipolar transistor.

203 Complementary bipolar transistors:
This subclass is indented under subclass 202. Process for making complementary insulated gate field effect transistors combined with a first bipolar transistor which additionally contains a second bipolar transistor which is of opposite conductivity type to the first bipolar transistor.

204 Lateral bipolar transistor:
This subclass is indented under subclass 202. Process for making complementary insulated gate field effect transistors additionally having a bipolar transistor possessing a horizontal-type structure so that current flow between its emitter and collector regions is parallel to a major surface of the semiconductor substrate.

205 Plural bipolar transistors of differing electrical characteristics:
This subclass is indented under subclass 202. Process for making complementary insulated gate field effect transistors combined with multiple bipolar transistors of differing electrical properties.

206 Vertical channel insulated gate field effect transistor:
This subclass is indented under subclass 202. Process for making complementary insulated gate field effect transistors combined with a bipolar transistor and wherein at least one insulated gate field effect transistor possesses an active channel region which is configured to provide, at least in part, a vertically conductive pathway between source and drain regions.

207 Including isolation structure:
This subclass is indented under subclass 202. Process for making complementary insulated gate field effect transistors combined with a bipolar transistor having a structure serving to at least partially electrically isolate the semiconductive region in which one transistor is formed from laterally adjacent semiconductive regions.

208 Isolation by PN junction only:
This subclass is indented under subclass 207. Process for making complementary insulated gate field effect transistors combined with a bipolar transistor in which the transistors are electrically isolated solely through the use of properly biased PN junctions.

209 Including additional vertical channel insulated gate field effect transistor:
This subclass is indented under subclass 200. Process for making complementary insulated gate field effect transistors having combined therewith an additional field effect transistor having an active channel region configured to provide, at least in part, a vertically conductive pathway between source and drain regions.

210 Including passive device (e.g., resistor, capacitor, etc.):
This subclass is indented under subclass 200. Process for making complementary insulated gate field effect transistors having combined therewith a passive electrical device or element (i.e., an electrical device or component in which charge carriers do not change their energy levels and do not provide electrical rectification, amplification, or switching, but which does react to voltage and current input).

211 Having gate surrounded by dielectric (i.e., floating gate):
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors wherein at least one field effect transistor has an additional insulated gate electrode completely separated by dielectric from its first insulated gate electrode.

(1) Note. Usually, the floating gate electrode is located (a) above and insulated from the channel region and (b) below and insulated from a controlling gate elec-

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trode. A floating gate electrode, due to accumulated electrical influence derived from the controlling gate electrode, provides on-off operation of the channel region. Floating gate arrangements are prevalent in ultraviolet erasable programmable read-only memory devices (i.e., EPROMs)

212 Vertical channel:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors wherein the active channel region of at least one of the transistors is configured to provide, at least in part, a vertically conductive pathway between source and drain regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
268 for a process of making a vertical channel insulated gate field effect transistor.

213 Common active region:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors wherein the transistors share a device active region.

214 Having underpass or crossunder:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors having an electrically conductive structure located within the semiconductor substrate which functions to electrically connect the transistors.

215 Having fuse or integral short:
This subclass is indented under subclass 199. Process for making complementary field effect transistors having a structure which is alterable from the conductive to nonconductive state or functions to electrically short the transistor structure.

216 Gate insulator structure constructed of diverse dielectrics (e.g., MNOS, etc.) or of nonsilicon compound:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors wherein the gate dielectric insulator of at least one of the transistors is constructed of plural diverse dielectrics (e.g., nitride and oxide layers, etc.) or of a nonsilicon containing dielectric compound.

217 Doping of semiconductor channel region beneath gate insulator (e.g., threshold voltage adjustment, etc.):
This subclass is indented under subclass 199. Process having a step of introducing an electrically active dopant species into the semiconductor active channel region beneath the gate insulator of at least one of the complementary insulated gate field effect transistors.

218 Including isolation structure:
This subclass is indented under subclass 199. Process for making complementary field effect transistors having a structure serving to at least partially electrically isolate the semiconductive region in which one transistor is formed from laterally adjacent semiconductive regions.

219 Total dielectric isolation:
This subclass is indented under subclass 218. Process for making complementary insulated gate field effect transistors in which at least one of the insulated gate complementary field effect transistors is fully electrically isolated by dielectric insulative material from laterally adjacent semiconductive regions.

220 Isolation by PN junction only:
This subclass is indented under subclass 218. Process for making complementary insulated gate field effect transistors in which the transistors are electrically isolated solely through the use of properly biased PN junctions.

221 Dielectric isolation formed by grooving and refilling with dielectric material:
This subclass is indented under subclass 218. Process for making complementary insulated gate field effect transistors wherein lateral isolation means is provided by forming a recess into the semiconductor substrate and refilling the recess at least in part with electrically insulative material.

222 With epitaxial semiconductor layer formation:
This subclass is indented under subclass 221. Process for making complementary insulated gate field effect transistors with dielectric isolation formed by grooving and refilling with

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dielectric material including a step of forming an epitaxial semiconductor layer.

223 Having well structure of opposite conductivity type:
This subclass is indented under subclass 221. Process for making complementary insulated gate field effect transistors including a step of forming a well of opposite conductivity to the adjoining semiconductor region in which well is formed an insulated gate field effect transistor of opposite conductivity type to an insulated gate field effect transistor located in the adjoining semiconductor region.

224 Plural wells:
This subclass is indented under subclass 223. Process for making complementary insulated gate field effect transistors wherein plural wells of the same or opposite conductivity type are formed in the semiconductive substrate, each well utilized for formation therein of an insulated gate field effect transistor.

225 Recessed oxide formed by localized oxidation (i.e., LOCOS):
This subclass is indented under subclass 218. Process for making complementary insulated gate field effect transistors wherein lateral isolation means is provided by a step of selectively oxidizing semiconductive regions of the substrate.

226 With epitaxial semiconductor layer formation:
This subclass is indented under subclass 225. Process for making complementary insulated gate field effect transistors with dielectric isolation formed by selectively oxidizing semiconductive regions of the substrate combined with a step of forming an epitaxial semiconductor layer.

227 Having well structure of opposite conductivity type:
This subclass is indented under subclass 225. Process for making complementary insulated gate field effect transistors including a step of forming a well of opposite conductivity to the adjoining semiconductor regions in which well is formed an insulated gate field effect transistor of opposite conductivity type to an insulated gate field effect transistor located in the adjoining semiconductor region.

228 Plural wells:
This subclass is indented under subclass 227. Process for making complementary insulated gate field effect transistors wherein plural wells of the same or opposite conductivity type are formed in the semiconductive substrate, each well utilized for formation therein of an insulated gate field effect transistor.

229 Self-aligned:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

(1) Note. A self-aligned gate is one which is aligned between the source and drain via a masking process which uses the gate material itself to achieve the registration of related device regions.

230 Utilizing gate sidewall structure:
This subclass is indented under subclass 229. Process with a step of utilizing a structure located on the sidewall of the gate electrode as the previously formed device feature.

231 Plural doping steps:
This subclass is indented under subclass 230. Process including multiple steps of introducing electrically active dopant species into semiconductor regions of the substrate.

232 Plural doping steps:
This subclass is indented under subclass 229. Process including multiple steps of introducing electrically active dopant species into semiconductor regions of the substrate.

233 And contact formation:
This subclass is indented under subclass 199. Process for making complementary insulated gate field effect transistors including a step of forming electrical connections to the transistors.

234 Including bipolar transistor (i.e., BiMOS):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having combined therewith a bipolar transistor.

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235 Heterojunction bipolar transistor:
This subclass is indented under subclass 234. Process for making an insulated gate field effect transistor combined with a bipolar transistor wherein the emitter-base junction or the collector-base junction of the bipolar transistor possesses an interface between two dissimilar semiconductor materials.

236 Lateral bipolar transistor:
This subclass is indented under subclass 234. Process for making an insulated gate field effect transistor combined with a bipolar transistor which has a horizontal-type structure resulting in current flow between its emitter and collector regions parallel to a major surface of the semiconductor substrate.

237 Including diode:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having combined therewith a diode device or element.

238 Including passive device (e.g., resistor, capacitor, etc.):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having combined therewith an electrical device or component in which charge carriers do not change their energy levels and do not provide electrical rectification, amplification, or switching, but which does react to voltage and current input.

SEE OR SEARCH THIS CLASS, SUBCLASS:
273 for a process of making an insulated gate field effect transistor which possesses an integral short of the active regions of a single transistor.

239 Capacitor:
This subclass is indented under subclass 238. Process for making an insulated gate field effect transistor having combined therewith a capacitor as the passive device.

240 Having high dielectric constant insulator (e.g., Ta_2O_5, etc.):
This subclass is indented under subclass 239. Process wherein the capacitor dielectric is constructed of a material having a dielectric constant of greater than 7.5, the dielectric constant of Si_3N_4.

241 And additional field effect transistor (e.g., sense or access transistor, etc.):
This subclass is indented under subclass 239. Process for making an insulated gate field effect transistor having combined therewith a capacitor and an additional field effect transistor.

SEE OR SEARCH THIS CLASS, SUBCLASS:
258 for process of making a floating gate-type insulated gate field effect transistor having combined therewith an additional insulated gate field effect transistor.

242 Including transistor formed on trench side-walls:
This subclass is indented under subclass 241. Process wherein the additional diverse field effect transistor is formed on the side-walls of a groove formed in the semiconductor substrate.

(1) Note. The access transistor serves to sense the storage of electrical charges on the capacitor.

243 Trench capacitor:
This subclass is indented under subclass 239. Process for making an insulated gate field effect transistor combined with a capacitor which is located in a groove in the semiconductor substrate.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 301+ for an insulated gate field effect transistor combined with a trench capacitor.

244 Utilizing stacked capacitor structure (e.g., stacked trench, buried stacked capacitor, etc.):
This subclass is indented under subclass 243. Process wherein the trench capacitor contains a number of capacitor plate regions aligned vertically above each other or wherein the capacitor and the insulated gate field effect transistor are located such that one overlies the other.

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245 With epitaxial layer formed over the trench:
This subclass is indented under subclass 243. Process including a step of forming an epitaxial semiconductive layer over the trench region.

246 Including doping of trench surfaces:
This subclass is indented under subclass 243. Process having a step of introducing electrically active dopant species into the surfaces of the groove in which the capacitor is located.

SEE OR SEARCH THIS CLASS, SUBCLASS:
524 for a process of implanting a dopant into a grooved semiconductive region.

247 Multiple doping steps:
This subclass is indented under subclass 246. Process utilizing plural steps of introducing electrically active dopant species into the trench surfaces.

248 Including isolating means formed in trench:
This subclass is indented under subclass 246. Process including forming a structure functioning as electrical isolation means at the groove bottom.

249 Doping by outdiffusion from a dopant source layer (e.g., doped oxide, etc.):
This subclass is indented under subclass 246. Process wherein doping the trench surfaces is via diffusion from an adjacent dopant source layer formed thereupon.

250 Planar capacitor:
This subclass is indented under subclass 239. Process for making an insulated gate field effect transistor combined with a capacitor wherein a generally planar region of the semiconductive substrate forms a first capacitor plate with the capacitor dielectric and a second capacitor plate formed thereupon.

251 Including doping of semiconductive region:
This subclass is indented under subclass 250. Process having a step of introducing an electrically active dopant species into a semiconductive region of the substrate forming the first capacitor plate.

252 Multiple doping steps:
This subclass is indented under subclass 251. Process having plural steps of introducing electrically active dopant species into a semiconductive region of the substrate forming the first capacitor plate.

253 Stacked capacitor:
This subclass is indented under subclass 239. Process for making an insulated gate field effect transistor in combination with a capacitor containing a number of capacitor plate and dielectric layers deposited successively one atop another and overlying the field effect transistor.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 306+ for an insulated gate field effect transistor combined with a stacked capacitor.

254 Including selectively removing material to undercut and expose storage node layer:
This subclass is indented under subclass 253. Process having a step of selectively removing material (e.g., by etching, etc.) to undercut and expose the capacitor electrode which serves as the storage node layer of the stacked capacitor.

(1) Note. The capacitor electrode on which the electrical charge is stored is referred to as the storage node layer.

255 Including texturizing storage node layer:
This subclass is indented under subclass 253. Process having a step of roughening the surface of the capacitor plate which serves as the storage node layer of the stacked capacitor.

(1) Note. The capacitor electrode on which the electrical charge is stored is referred to as the storage node layer.

256 Contacts formed by selective growth or deposition:
This subclass is indented under subclass 253. Process wherein electrical contacts are formed by selective growth or deposition of conductive material onto the semiconductor substrate.

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257 Having additional gate electrode surrounded by dielectric (i.e., floating gate):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein an additional gate electrode completely separated by dielectric from a first insulated gate electrode is formed.

(1) Note. Usually, the floating gate electrode is located (a) above and insulated from the channel region and (b) below and insulated from a controlling gate electrode that determines operation of the floating gate electrode. A floating gate electrode, due to accumulated electrical influence derived from the controlling gate electrode, provides on-off operation of the channel region. Floating gate arrangements are prevalent in ultraviolet erasable programmable read-only memory devices (i.e., EPROMs).

SEE OR SEARCH THIS CLASS, SUBCLASS:
201 for a process of making complementary insulated gate field effect transistors combined with an additional floating gate-type insulated gate field effect transistor.

258 Including additional field effect transistor (e.g., sense or access transistor, etc.):
This subclass is indented under subclass 257. Process for making a floating gate-type insulated gate field effect transistor having combined therewith an additional field effect transistor.

SEE OR SEARCH THIS CLASS, SUBCLASS:
241 for a process of making an insulated gate field effect transistor combined with a capacitor which structure contains an additional insulated gate field effect transistor.

259 Including forming gate electrode in trench or recess in substrate:
This subclass is indented under subclass 257. Process for making a floating gate type insulated gate field effect transistor including forming a gate electrode in a groove located in the semiconductor substrate.

260 Textured surface of gate insulator or gate electrode:
This subclass is indented under subclass 257. Process for making a floating gate-type insulated gate field effect transistor wherein a roughened surface is utilized for the gate insulator or gate electrode.

261 Multiple interelectrode dielectrics or nonsilicon compound gate insulator:
This subclass is indented under subclass 257. Process for making a floating gate-type insulated gate field effect transistor with plural interelectrode dielectrics or a nonsilicon compound dielectric material.

SEE OR SEARCH THIS CLASS, SUBCLASS:
287 for a process of making an insulated gate field effect transistor having the gate insulator constructed of diverse dielectrics or of a nonsilicon compound dielectric.

262 Including elongated source or drain region disposed under thick oxide regions (e.g., buried or diffused bitline, etc.):
This subclass is indented under subclass 257. Process for making a floating gate-type insulated gate field effect transistor having elongated source or drain region located under thick oxide dielectric regions.

(1) Note. The regions disposed under the thick oxide regions must be active source or drain regions rather than channel stops serving to electrically isolate laterally spaced FETs.

SEE OR SEARCH THIS CLASS, SUBCLASS:
294 for a process of making an insulated gate field effect transistor including dielectric isolation structure.

263 Tunneling insulator:
This subclass is indented under subclass 262. Process for making a floating gate type insulated gate field effect transistor including an insulative layer adjacent the gate electrode which allows passage of charge carriers therethrough.

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264 Tunneling insulator:
This subclass is indented under subclass 257. Process for making a floating gate-type insulated gate field effect transistor including an insulative layer adjacent the gate electrode which allows passage of charge carriers therethrough.

265 Oxidizing sidewall of gate electrode:
This subclass is indented under subclass 257. Process for making a floating gate-type field effect transistor including a step of forming a dielectric sidewall on the gate electrode by reacting the gate electrode material with oxygen.

266 Having additional, nonmemory control electrode or channel portion (e.g., for accessing field effect transistor structure, etc.):
This subclass is indented under subclass 257. Process for making a floating gate-type field effect transistor having an additional, nonmemory control electrode (i.e., having direct electrical contact thereto) or channel portion.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 316 for a floating gate memory device with an additional contacted control electrode.

267 Including forming gate electrode as conductive sidewall spacer to another electrode:
This subclass is indented under subclass 266. Process including a step of forming a conductive electrode on the sidewall of another electrode wherein the conductive sidewall serves as a gate electrode.

268 Vertical channel:
This subclass is indented under subclass 197. Process for making a insulated gate field effect transistor wherein the active channel is configured to provide, in whole or in part, a vertically conductive pathway between source and drain regions.

269 Utilizing epitaxial semiconductor layer grown through an opening in an insulating layer:
This subclass is indented under subclass 268. Process for making an insulated gate field effect transistor wherein a epitaxial semiconductor layer is deposited through an opening in an insulating layer upon a semiconductor substrate.

270 Gate electrode in trench or recess in semiconductor substrate:
This subclass is indented under subclass 268. Process for making an insulated gate field effect transistor wherein the gate electrode is formed in a groove or recess in the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
259 for a process of making a floating gate-type insulated gate field effect transistor having a gate electrode formed in a groove located in the semiconductive substrate.

271 V-gate:
This subclass is indented under subclass 270. Process for making an insulated gate field effect transistor wherein the gate electrode has a V-shape configuration.

272 Totally embedded in semiconductive layers:
This subclass is indented under subclass 270. Process wherein the gate electrode is surrounded on all sides by semiconductive layers.

273 Having integral short of source and base regions:
This subclass is indented under subclass 268. Process for making an insulated gate field effect transistor having an integral electrical connection between the source and base (i.e., substrate) regions.

274 Short formed in recess in substrate:
This subclass is indented under subclass 273. Process wherein the integral short is formed in a groove in the semiconductor substrate

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275 Making plural insulated gate field effect transistors of differing electrical characteristics:
This subclass is indented under subclass 197. Process for making multiple insulated gate field effect transistors of differing electrical characteristics.

SEE OR SEARCH THIS CLASS, SUBCLASS:
128 for processes of selectively wiring an array of electrical devices by completing particular devices of the array or by completion or destruction of conductive pathways between particular devices of the array.

276 Introducing a dopant into the channel region of selected transistors:
This subclass is indented under subclass 275. Process for making plural insulated gate field effect transistors having a step of introducing an electrically active dopant species into the semiconductor channel region beneath the gate insulator of one or more transistors to produce transistors of differing electrical characteristics.

SEE OR SEARCH THIS CLASS, SUBCLASS:
130 for processes of rendering electrical devices in an array operable or inoperable by electrically completing or electrically shorting designated devices thereof to selectively interconnect the array.
289 for a process of doping the semiconductor channel region beneath gate insulator to (a) produce field effect transistors of identical electrical characteristics or (b) alter the electrical characteristics of a single field effect transistor.

277 Including forming overlapping gate electrodes:
This subclass is indented under subclass 276. Process for making plural insulated gate field effect transistors of differing electrical characteristics including a step of forming overlapping gate electrodes.

278 After formation of source or drain regions and gate electrode (e.g., late programming, encoding, etc.):
This subclass is indented under subclass 276. Process for making plural insulated gate field effect transistors of differing electrical characteristics wherein the semiconductor channel region is doped subsequent to the formation of the source and drain regions and the gate electrode.

279 Making plural insulated gate field effect transistors having common active region:
This subclass is indented under subclass 197. Process for making multiple insulated gate field effect transistors in which a transistor active region is shared between two or more field effect transistors.

280 Having underpass or crossunder:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor electrically interconnected to an adjoining electrical device via a conductive structure located within the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
214 for a process of making complementary insulated gate field effect transistors combined with an underpass or crossunder.

281 Having fuse or integral short:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor which possesses a structure alterable to a nonconductive state (i.e., fuse) or an integral electrical connection between source and gate regions or between drain and gate regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
132 for a process of making an array of electrical devices and selectively interconnecting the devices via fusible links.
238 for a process of making an insulated gate field effect transistor combined with a resistor.

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282 Buried channel:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein the channel formed between the source and drain regions is configured so as to be located beneath the semiconductor substrate surface.

283 Plural gate electrodes (e.g., dual gate, etc.):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein plural gate electrodes on either the same or opposite side of the active channel region serve to control the electrical conduction characteristics of the semiconductive active channel region.

SEE OR SEARCH THIS CLASS, SUBCLASS:
157 for a process of making an insulated gate field effect transistor upon an insulating substrate or layer wherein the transistor possesses dual gate or opposed gate structure.

284 Closed or loop gate:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein the gate electrode is configured such that it closes upon itself to thereby totally surround one of the device active regions.

285 Utilizing compound semiconductor:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor utilizing a compound semiconductor active region.

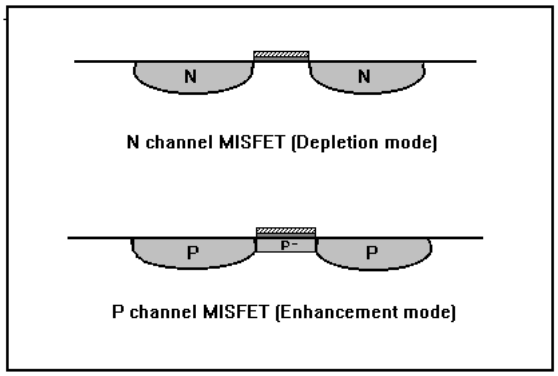
286 Asymmetric:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein the pair of active regions are offset or nonsymmetrical with respect to the centerline of the insulated gate electrode.

287 Gate insulator structure constructed of diverse dielectrics (e.g., MNOS, etc.) or of nonsilicon compound:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein the gate dielectric insulator is constructed of plural diverse dielectrics (e.g., nitride and oxide, etc.) or of a nonsilicon containing dielectric compound.

SEE OR SEARCH THIS CLASS, SUBCLASS:
216 for a process of making complementary insulated gate field effect transistors at least one transistor having a gate insulator structure constructed of diverse dielectrics or of nonsilicon compound.
261 for a process of making a floating gate-type insulated gate field effect transistor having multiple interelectrode dielectrics or nonsilicon containing dielectric.

288 Having step of storing electrical charge in gate dielectric:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having an active step of storing electrical charge in the gate dielectric insulator.

289 Doping of semiconductive channel region beneath gate insulator (e.g., adjusting threshold voltage, etc.):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having a step of introducing electrically active dopant species into the semiconductor active channel region beneath the gate insulator.



SEE OR SEARCH THIS CLASS, SUBCLASS:
276 for a process of doping the semiconductor channel region beneath gate

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insulator of selected transistors to make plural field effect transistors of differing electrical characteristics.

290 After formation of source or drain regions and gate electrode:
This subclass is indented under subclass 289. Process wherein the semiconductor channel region is doped subsequent to the formation of the source and drain regions and the gate electrode.

291 Using channel conductivity dopant of opposite type as that of source and drain:
This subclass is indented under subclass 289. Process wherein the dopant and the semiconductor active channel region beneath the gate insulator are of the same conductivity type.

292 Direct application of electrical current:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having a step of directly applying an electrical current to the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
17 for a step of measuring involving aging electrical devices formed on a semiconductor substrate via the direct application of electrical current.

293 Fusion or solidification of semiconductor region:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having a step of fusing or solidifying a semiconductive region of the substrate.

294 Including isolation structure:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having a structure which serves to at least partially electrically isolate the semiconductor region in which the device is formed from laterally adjacent semiconductive regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
400 for processes of forming an electrically isolated lateral semiconductor structure utilizing dielectric or junction isolation.

295 Total dielectric isolation:
This subclass is indented under subclass 294. Process for making an insulated gate field effect transistor which is fully electrically isolated by dielectric insulative material from laterally adjacent semiconductive regions.

296 Dielectric isolation formed by grooving and refilling with dielectric material:
This subclass is indented under subclass 294. Process for making an insulated gate field effect transistor including the step of forming an isolation structure by making a recess in the semiconductor substrate and refilling the recess with an insulative material.

297 Recessed oxide formed by localized oxidation (i.e., LOCOS):
This subclass is indented under subclass 294. Process for making an insulated gate field effect transistor including the step of oxidizing a selected region of a semiconductive substrate to form an embedded oxide (e.g., field oxide) therein which forms the periphery of a semiconductive region utilized for the formation of the field effect transistor.

298 Doping region beneath recessed oxide (e.g., to form chanstop, etc.):
This subclass is indented under subclass 297. Process including a step of introducing electrically active dopant species into the semiconductor substrate region beneath the recessed oxide (e.g., to form a channel stop thereby preventing electric field inversion beneath the recessed oxide, etc.).

299 Self-aligned:
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

(1) Note. A self-aligned gate is one which is aligned between the source and drain via a masking process which uses the gate material itself to achieve the registration of the related device regions.

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300 Having elevated source or drain (e.g., epitaxially formed source or drain, etc.):
This subclass is indented under subclass 299. Process including a step of forming the source or drain active region at a position above and laterally adjacent to the channel region of the transistor.

301 Source or drain doping:
This subclass is indented under subclass 299. Process having a step for the self-aligned introduction of electrically active dopant species into the semiconductor regions of the substrate to form the transistor source or drain regions or portions thereof.

302 Oblique implantation:
This subclass is indented under subclass 301. Process involving implanting ions other than perpendicularly with respect to the plane of the substrate.

303 Utilizing gate sidewall structure:
This subclass is indented under subclass 301. Process having structure on the sidewall of the gate electrode or gate insulator which is utilized as the previously formed device feature.

304 Conductive sidewall component:
This subclass is indented under subclass 303. Process wherein the gate sidewall structure is composed at least in part of a conductive component.

305 Plural doping steps:
This subclass is indented under subclass 303. Process including multiple steps of introducing dopant species into the semiconductive regions of the substrate.

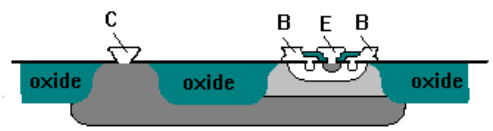
306 Plural doping steps:
This subclass is indented under subclass 301. Process including multiple steps of introducing dopant species into the semiconductive regions of the substrate.

307 Using same conductivity-type dopant:
This subclass is indented under subclass 306. Process wherein the same conductivity-type electrically active dopant is introduced using plural doping steps.

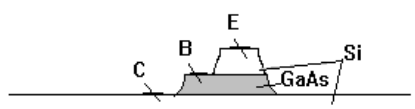
308 Radiation or energy treatment modifying properties of semiconductor regions of substrate (e.g., thermal, corpuscular, electromagnetic, etc.):
This subclass is indented under subclass 197. Process for making an insulated gate field effect transistor having a step of irradiating the semiconductor substrate to alter the electrical properties of semiconductive regions thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
795 for a process of modifying properties of semiconductive regions of the substrate via radiation or energy treatment.

309 FORMING BIPOLAR TRANSISTOR BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS:
This subclass is indented under the class definition. Process for forming a transistor structure which upon completion possesses a base region separating two or more active regions and in which both positive and negative charge carriers are used to support current flow.



Vertical Bipolar transistor



Heterojunction Bipolar transistor

(1) Note. To be proper hereunder, the claim must include a positive recitation of (a) formation of semiconductive active regions or (b) altering the electrical properties of active semiconductive regions of the substrate.

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(2) Note. The regions of a bipolar transistor are commonly referred to as collector, base, and emitter. A bipolar device may alternatively be identified by the semiconductive regions from which the device is formed (i.e., a NPN or PNP device).

SEE OR SEARCH THIS CLASS, SUBCLASS:

170 for a process of making a Schottky gate field effect transistor combined with a bipolar transistor.

189 for a process of making a junction gate field effect transistor combined with a bipolar transistor.

202 for a process of making complementary insulated gate field effect transistors combined with a bipolar transistor.

234 for a process of making an insulated gate field effect transistor combined with a bipolar transistor.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 47, 197, 205, 273, 350, 361, 370, 378, 423, 462, 477+, 511, 512, 517, 518, 525, 526, 539+, and 552+ for a bipolar transistor structure.

310 Gettering of semiconductor substrate:
This subclass is indented under subclass 309. Process having a step of gettering the semiconductor substrate.

311 On insulating substrate or layer (i.e., SOI type):
This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the transistor is formed upon an insulating substrate (e.g., glass, sapphire, etc.) or layer.

312 Having heterojunction:
This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the emitter-base or the collector-base junction is an interface of two dissimilar semiconductor materials resulting in a heterojunction therebetween.

SEE OR SEARCH THIS CLASS, SUBCLASS:

235 for a process of making an insulated gate field effect transistor combined with a heterojunction bipolar transistor.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 197+ for a heterojunction bipolar transistor structure.

313 Complementary bipolar transistors:
This subclass is indented under subclass 312. Process for making a structure which comprises plural bipolar transistors wherein the emitter and collector regions of a first bipolar transistor are of opposite conductivity type to the emitter and collector regions of a second bipolar transistor.(i.e., both pnp and npn bipolar transistor structures), at least one of which possesses a heterojunction.

314 And additional electrical device:
This subclass is indented under subclass 312. Process for making a heterojunction bipolar transistor and an additional electrical device.

315 Forming inverted transistor structure:
This subclass is indented under subclass 312. Process forming a heterojunction bipolar transistor structure in which a semiconductor body such as a semiconductor substrate or a semiconductor layer is used as its emitter region, a first semiconductor region formed in the semiconductor body is used as the base region and a second semiconductor region formed in the first semiconductor region is used as the collector region.

316 Forming lateral transistor structure:
This subclass is indented under subclass 312. Process for making a heterojunction bipolar transistor which has a horizontal structure resulting in current flow between its emitter and collector parallel to a major surface of the semiconductor substrate.

317 Wide bandgap emitter:
This subclass is indented under subclass 312. Process for making a heterojunction bipolar transistor with an active region which involves

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a charge carrier emitter region made of a semiconductor material having an energy gap between its conduction and valence band which is greater than the energy gap of the dissimilar semiconductor material of the base region.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 198 for a wide band-gap emitter heterojunction bipolar transistor structure.

318 Including isolation structure:
This subclass is indented under subclass 312. Process for making a heterojunction bipolar transistor which has structure so as to at least partially electrically isolate the device from laterally adjacent semiconductor regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
353 for an electrical isolation process in a nonheterojunction bipolar device.

319 Air isolation (e.g., mesa, etc.):
This subclass is indented under subclass 318. Process for making a heterojunction bipolar transistor wherein the emitter or collector region of the device is a raised feature with respect to the plane of the substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
343 for a process of making a nonheterojunction bipolar device having a mesa or stacked emitter.

320 Self-aligned:
This subclass is indented under subclass 312. Process for making a heterojunction bipolar transistor wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

321 Utilizing dummy emitter:
This subclass is indented under subclass 320. Process for making a heterojunction bipolar transistor wherein a substitute emitter is formed or removed prior to the forming of the active emitter region of the device.

322 Complementary bipolar transistors:
This subclass is indented under subclass 309. Process for making plural bipolar transistors wherein the emitter and collector regions or a first bipolar transistor are of opposite conductivity type to the emitter and collector regions of a second bipolar transistor.

323 Having common active region (i.e., integrated injection logic (I^2L), etc.):
This subclass is indented under subclass 322. Process for making complementary bipolar transistors which possess a common active region.

324 Including additional electrical device:
This subclass is indented under subclass 323. Process for making complementary bipolar transistors with shared common region having combined therewith an additional electrical device.

325 Having lateral bipolar transistor:
This subclass is indented under subclass 323. Process for making complementary bipolar transistors with shared common region wherein at least one of the bipolar transistors has a horizontal structure resulting in current flow between its emitter and collector parallel to a major surface of the semiconductor substrate.

326 Including additional electrical device:
This subclass is indented under subclass 322. Process for making complementary bipolar transistors having combined therewith an additional electrical device.

327 Having lateral bipolar transistor:
This subclass is indented under subclass 322. Process for making complementary bipolar transistors wherein at least one of the bipolar transistors has a horizontal structure resulting in current flow between its emitter and collector parallel to a major surface of the semiconductor substrate.

328 Including diode:
This subclass is indented under subclass 309. Process for making a bipolar transistor having combined therewith a diode.

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329 Including passive device (e.g., resistor, capacitor, etc.):
This subclass is indented under subclass 309. Process for making a bipolar transistor having combined therewith an electrical device or component in which charge carriers do not change their energy levels and do not provide electrical rectification, amplification, or switching, but which does react to voltage and current input.

330 Resistor:
This subclass is indented under subclass 329. Process for making a bipolar transistor combined with a resistive element or component.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 539+, 577, and 582 for bipolar transistor structure combined with a resistive element.

331 Having same doping as emitter or collector:
This subclass is indented under subclass 330. Process wherein the resistor region has the same doping profile (i.e., is formed in the same step) as either the emitter or collector region of the bipolar transistor with which the resistor is combined.

(1) Note. Most resistors in bipolar integrated circuits are formed with the same doping step as the bipolar transistor base regions. Resistors that are instead formed at the same doping step as the emitter or collector, rather than the base, go in this subclass.

332 Lightly doped junction isolated resistor:
This subclass is indented under subclass 330. Process wherein the resistive element is in the form of a lightly doped layer of one conductivity type located in a region of opposite conductivity type, such that the pn junction between the resistor region and its containing opposite conductivity-type region serves to electrically isolate the resistor.

(1) Note. A resistor region is considered to be lightly doped if it is substantially less heavily doped than the base region of the bipolar transistor combined therewith, or if it has a doping density not greater than 100 times that of the opposite conductivity-type region in which it is contained.

333 Having fuse or integral short:
This subclass is indented under subclass 309. Process for making a bipolar transistor which possesses a structure which is alterable from a conductive to a nonconductive state (i.e., fuse) or an integral electrical short between the collector and emitter active regions or between the base and emitter active regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
132 for a process of making an array of electrical devices and selectively interconnecting the devices via fusible links.

334 Forming inverted transistor structure:
This subclass is indented under subclass 309. Process forming a bipolar transistor structure in which a semiconductor body such as a semiconductor substrate or a semiconductor layer is used as its emitter region, a first semiconductor region formed in the semiconductor body is used as the base region and a second semiconductor region formed in the first semiconductor region is used as the collector region.

SEE OR SEARCH THIS CLASS, SUBCLASS:
315 for a process of making a heterojunction bipolar transistor having an inverted structure.

335 Forming lateral transistor structure:
This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the transistor has a horizontal structure resulting in current flow between its emitter and collector parallel to a major surface of the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
204 for a process of making complementary insulated gate field effect transistors combined with a lateral bipolar transistor.
236 for a process of making an insulated gate field effect transistor combined with a lateral bipolar transistor.

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327 for a process of making a structure comprising complementary bipolar transistors one of which possesses a lateral transistor structure.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 557+ for a lateral bipolar transistor structure.

336 Combined with vertical bipolar transistor:
This subclass is indented under subclass 335. Process for making a lateral bipolar transistor combined with a vertical bipolar transistor having current flow between its emitter and collector perpendicular to a major surface of the semiconductor substrate.

337 Active region formed along groove or exposed edge in semiconductor:
This subclass is indented under subclass 335. Process for making a lateral bipolar transistor wherein the transistor has a recess or exposed edge and an active region of the transistor is formed along the recess or exposed edge.

338 Having multiple emitter or collector structure:
This subclass is indented under subclass 335. Process for making a lateral bipolar transistor having plural emitter active regions or plural collector active regions.

339 Self-aligned:
This subclass is indented under subclass 335. Process for making a lateral bipolar transistor wherein a previously formed device feature is utilized to make device active regions in the desired registration to the previously formed feature.

340 Making plural bipolar transistors of differing electrical characteristics:
This subclass is indented under subclass 309. Process for making multiple bipolar transistors possessing differing electrical properties.

341 Using epitaxial lateral overgrowth:
This subclass is indented under subclass 309. Process for making a bipolar transistor including forming a single crystalline semiconductor layer epitaxially on the semiconductor substrate and laterally over an insulative layer thereupon.

SEE OR SEARCH THIS CLASS, SUBCLASS:
481 for a process utilizing fluid growth or deposition of semiconductor active material onto an insulating layer by epitaxial lateral overgrowth.

342 Having multiple emitter or collector structure:
This subclass is indented under subclass 309. Process for making a bipolar transistor having plural emitter active regions or plural collector active regions.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 563+ for multiple separately connected emitter, collector, or base regions in the same transistor structure.

343 Mesa or stacked emitter:
This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the emitter is a raised feature relative to the adjoining semiconductive regions.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 586 for a bipolar transistor structure with a nonplanar semiconductor surface (e.g., groove, mesa, bevel, etc.).

344 Washed emitter:
This subclass is indented under subclass 309. Process wherein the surface of the semiconductive substrate is etched to remove oxide layers formed on the emitter region during emitter diffusion thus allowing an aperature used for diffusing the emitter impurity to be directly utilized as the aperature for electrical contact formation.

345 Walled emitter:
This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the emitter-base junction terminates against a dielectric isolation sidewall.

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SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), especially subclasses 514 and 515 for walled emitter bipolar transistor structure.

346 Emitter dip prevention or utilization:

This subclass is indented under subclass 309. Process involving special diffusion techniques to eliminate or utilize the tendency of the base-collector junction to "bulge" downward during the emitter diffusion.

347 Permeable or metal base:

This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the base region incompletely separates the collector and emitter regions, or is constructed of a metallic material.

SEE OR SEARCH THIS CLASS, SUBCLASS:

192 for a method of making a vertical junction gate field effect transistor.

348 Sidewall base contact:

This subclass is indented under subclass 309. Process for making a bipolar transistor wherein a conductive layer serving as the base electrode makes contact to the sidewall of the base region.

349 Pedestal base:

This subclass is indented under subclass 309. Process for making a bipolar transistor wherein the base region is provided with a projecting portion.

350 Forming base region of specified dopant concentration profile (e.g., inactive base region more heavily doped than active base region, etc.):

This subclass is indented under subclass 309. Process for making a bipolar transistor with a semiconductor base region possessing a specified concentration profile of an electrically active dopant species contained therein.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 592 for a bipolar transistor device having a base region possessing specified doping concentration profile.

351 Direct application of electrical current:

This subclass is indented under subclass 309. Process for making a bipolar transistor involving having a step of directly applying an electric current to the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:

17 for a step of measuring involving aging electrical devices formed on a semiconductor substrate via the direct application of electrical current.

352 Fusion or solidification of semiconductor region:

This subclass is indented under subclass 309. Process for making a bipolar transistor having a step of fusing or solidifying semiconductive regions of the substrate.

353 Including isolation structure:

This subclass is indented under subclass 309. Process for making a bipolar transistor having a structure which serves to at least partially electrically isolate the semiconductive region in which the transistor is formed from laterally adjacent semiconductive regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:

400 for processes of forming an electrically isolated lateral semiconductor structure utilizing dielectric or junction isolation without a step of bipolar transistor manufacture.

354 Having semi-insulative region:

This subclass is indented under subclass 353. Process for making a bipolar transistor wherein the electrical isolation is provided at least in part by a high resistivity semiconductive component.

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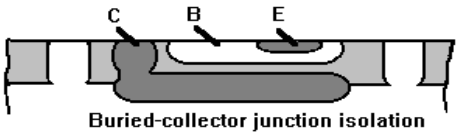
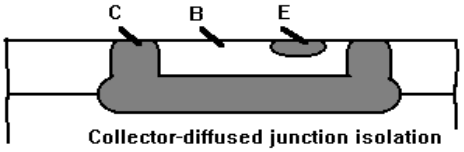
355 Total dielectrical isolation:
This subclass is indented under subclass 353. Process for making a bipolar transistor which is fully electrically isolated by dielectric insulative material from laterally adjacent semiconductive regions.

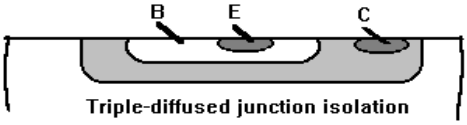
356 Isolation by PN junction only:
This subclass is indented under subclass 353. Process for making a bipolar transistor in a semiconductive region which is completely electrically isolated from laterally spaced regions of the semiconductor substrate solely through the use of properly biased PN junctions.



Buried-collector junction isolation



Collector-diffused junction isolation



Triple-diffused junction isolation

357 Including epitaxial semiconductor layer formation:
This subclass is indented under subclass 356. Process for making a junction isolated bipolar transistor utilizing the formation of an epitaxial semiconductor layer.

358 Up diffusion of dopant from substrate into epitaxial layer:
This subclass is indented under subclass 357. Process including a step of diffusing a dopant from the semiconductor substrate into the epitaxial layer form thereupon.

359 Dielectric isolation formed by grooving and refilling with dielectrical material:
This subclass is indented under subclass 353. Process for making a bipolar transistor involving the formation of a recess in the semiconductor followed by the refilling of the recess with an insulative material.

360 With epitaxial semiconductor formation in groove:
This subclass is indented under subclass 359. Process for making a bipolar transistor additionally involving the epitaxial deposition of a semiconductor material in the groove.

361 Including deposition of polysilicon or noninsulative material into groove:
This subclass is indented under subclass 359. Process for making a bipolar transistor wherein a noninsulative material is deposited into the groove in addition to the insulative material.

362 Recessed oxide by localized oxidation (i.e., LOCOS):
This subclass is indented under subclass 353. Process for making a bipolar transistor including the step of oxidizing a portion of a semiconductive material to form an embedded oxide (i.e., field oxide) therein which forms the periphery of a semiconductive region utilized for the formation of the bipolar transistor.

363 With epitaxial semiconductor layer formation:
This subclass is indented under subclass 362. Process for making a bipolar transistor utilizing in addition to the recessed oxide the formation of an epitaxial semiconductor layer.

364 Self-aligned:
This subclass is indented under subclass 309. Process wherein a previously formed device feature is utilized to make device regions in the desired registration to the previously formed feature.

365 Forming active region from adjacent doped polycrystalline or amorphous semiconductor:
This subclass is indented under subclass 364. Process having an active region (e.g., base, emitter, or collector) formed of polycrystalline or amorphous semiconductor.

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366 Having sidewall:
This subclass is indented under subclass 365. Process including forming dielectric isolation on the sidewall of the base region to separate the base and collector regions.

367 Including conductive component:
This subclass is indented under subclass 366. Process wherein the sidewall is a combination of conductive and insulative components.

368 Simultaneously outdiffusing plural dopants from polysilicon or amorphous semiconductor:
This subclass is indented under subclass 365. Process including the simultaneous outdiffusing of electrically active dopants from the polysilicon or amorphous active region.

369 Dopant implantation or diffusion:
This subclass is indented under subclass 364. Process having a step of implanting or diffusing an electrically active dopant species into a semiconductive region of the substrate.

370 Forming buried region (e.g., implanting through insulating layer, etc.):
This subclass is indented under subclass 369. Process wherein the dopant is implanted or diffused through an insulating layer.

371 Simultaneous introduction of plural dopants:
This subclass is indented under subclass 369. Process involving the concurrent introduction of multiple dopant species into one or more semiconductive regions of the substrate.

372 Plural doping steps:
This subclass is indented under subclass 369. Process having multiple steps of doping semiconductive regions of the substrate.

373 Multiple ion implantation steps:
This subclass is indented under subclass 372. Process wherein the plural doping steps are affected by implanting electrically active dopant ions into semiconductive regions of the substrate.

374 Using same conductivity-type dopant:
This subclass is indented under subclass 373. Process wherein the same conductivity-type electrically active dopant ion is introduced using plural ion implantation steps.

375 Forming partially overlapping regions:
This subclass is indented under subclass 372. Process wherein the plural doping steps are affected upon localized areas which lap over each other in part.

376 Single dopant forming regions of different depth or concentrations:
This subclass is indented under subclass 372. Process wherein the plural doping steps form regions which differ in amount of impurity or the distance the impurity has to travel inwardly from the surface.

377 Through same mask opening:
This subclass is indented under subclass 372. Process wherein plural doping steps are affected through the same opening in a dopant masking layer.

378 Radiation or energy treatment modifying properties of semiconductor regions of substrate (e.g., thermal, corpuscular, electromagnetic, etc.):
This subclass is indented under subclass 309. Process for making a bipolar transistor having a step of irradiating the semiconductor substrate to alter the electrical properties of semiconductive regions thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
795 for a process of modifying properties of semiconductive regions of the substrate via radiation or energy treatment.

379 VOLTAGE VARIABLE CAPACITANCE DEVICE MANUFACTURE (E.G., VARACTOR, ETC.):
This subclass is indented under the class definition. Process for making an active solid-state device wherein the device changes its capacitance depending on the amount of voltage applied thereto.

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SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 312 for an insulated gate FET combined with a voltage variable capacitor, subclass 480 for a Schottky barrier in a voltage variable capacitance diode, and subclasses 595+ for a voltage variable capacitance device.

332, Modulators, subclass 136 for a modulator combined with a voltage variable capacitor.

361, Electricity: Electrical Systems and Devices, subclasses 277+ for a per se voltage variable capacitor (varactor).

380 AVALANCHE DIODE MANUFACTURE (E.G., IMPATT, TRAPPAT, ETC.):

This subclass is indented under the class definition. Process for making a device which is configured to operate in a manner in which an external voltage is applied in the reverse-conducting direction of the semiconductor device junction with sufficient magnitude to cause the potential barrier at the junction to breakdown due to electrons or holes gaining sufficient speed to dislodge valence electrons and thus create more hole-electron current carriers resulting in a sudden change from high dynamic electrical resistance to very low dynamic resistance.

(1) Note. The terms Zener diode and Zener breakdown voltage are used rather loosely in that the breakdown mechanism above about 6 volts is thought to be due to avalanching and that below about 6 volts is thought to be due essentially to tunnelling.

SEE OR SEARCH THIS CLASS, SUBCLASS:

91 for a process of making a device or circuit which is responsive to a nonelectrical signal and operates in an avalanche breakdown mode.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 199 for an avalanche diode in a noncharge transfer device having a heterojunction, subclass 438 for a light-responsive avalanche junction device, subclass 481 for an avalanche diode having a Schottky barrier, subclass 551 for an avalanche diode used as a voltage reference element combined with pn junction isolation means in an integrated circuit, and subclasses 603+ for avalanche diodes in general.

381 MAKING PASSIVE DEVICE (E.G., RESISTOR, CAPACITOR, ETC.):

This subclass is indented under the class definition. Process for making an electrical device or component utilizing a semiconductor substrate in which charge carriers do not change their energy levels and that does not provide rectification, amplification, or switching, but which does react to voltage and current input.

(1) Note. Formation of a conductive layer of specified resistivity is not sufficient for placement hereunder unless the intent is for the layer to function as a discrete resistor element.

(2) Note. An isolation structure which functions by the application of an electrical bias (e.g., a channel stop, guard ring, or field plate region) is not a passive charge storage element proper here for, nor is the floating gate structure of a field effect device.

SEE OR SEARCH THIS CLASS, SUBCLASS:

21 for making a device controlled ink jet printhead or thermal printhead.

50 for a process of making a pressure sensitive resistive device.

171 for a process of making a Schottky gate field effect transistor combined with a passive electrical device.

190 for a process of making a junction gate field effect transistor combined with a passive electrical device.

210 for a process of making complementary insulated gate field effect transistors combined with a passive electrical device.

238 for a process of making an insulated gate field effect transistor combined with a passive electrical device.

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329 for a process of making a bipolar transistor combined with a passive electrical device.
379 for a process of making a voltage variable capacitance device.

SEE OR SEARCH CLASS:
264, Plastic and Nonmetallic Article Shaping or Treating: Processes, subclass 61 for methods of vitrifying or sintering of inorganic preform to make a discrete passive device (e.g., multilayer ceramic capacitor, etc.).

382 Resistor:
This subclass is indented under subclass 381. Process involving the manufacture of an electrically resistive element utilizing a semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
21 for a process of making an electrical resistor-type thermal printhead.
50 for a process of making a resistor responsive to physical stress.
238 for a process of making an insulated gate field effect transistor combined with a resistor device or element.
330 for making a bipolar transistor combined with a resistor device or element.

383 Lightly doped junction isolated resistor:
This subclass is indented under subclass 382. Process wherein the resistive element is in the form of a lightly doped layer of one conductivity type located in a region of opposite conductivity type, such that the pn junction between the resistor region and its containing opposite conductivity-type region serves to electrically isolate the resistor.

384 Deposited thin film resistor:
This subclass is indented under subclass 382. Process wherein the resistor is formed by the deposition of resistive material upon the semiconductor substrate.

SEE OR SEARCH CLASS:
427, Coating Processes, especially subclasses 96.1 through 99.5 for a process of coating a nonsemiconductive substrate to produce an integrated or printed circuit or circuit board and subclasses 101-103 for a process of coating a nonsemiconductive substrate to produce a resistor for current control (excludes heating element).

385 Altering resistivity of conductor:
This subclass is indented under subclass 384. Process wherein the electrical resistivity of a conductive material (i.e., metallization) is altered subsequent to deposition.

386 Trench capacitor:
This subclass is indented under subclass 381. Process for making a capacitor located in a groove in a semiconductive substrate.

387 Having stacked capacitor structure (e.g., stacked trench, buried stacked capacitor, etc.):
This subclass is indented under subclass 386. Process wherein the trench capacitor contains a number of capacitor plate regions aligned vertically above each other.

388 With epitaxial layer formed over the trench:
This subclass is indented under subclass 386. Process for making a trench capacitor including a step of forming an epitaxial semiconductive layer over the trench region.

389 Including doping of trench surfaces:
This subclass is indented under subclass 386. Process for making a trench capacitor having a step of introducing electrically active dopant species into a surface (i.e., sidewall or bottom) of the trench in which the capacitor is located.

SEE OR SEARCH THIS CLASS, SUBCLASS:
524 for a process of implanting a dopant into a grooved semiconductive region.

390 Multiple doping steps:
This subclass is indented under subclass 389. Process for making a trench capacitor utilizing plural doping steps.

391 Including isolating means formed in trench:
This subclass is indented under subclass 389. Process for making a trench capacitor having structure functioning as electrical isolation formed in the trench bottom.

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392 Doping by outdiffusion from a dopant source layer (e.g., doped oxide):
This subclass is indented under subclass 389. Process for making a trench capacitor wherein the trench surfaces are doped via outdiffusion from a doped source layer.

393 Planar capacitor:
This subclass is indented under subclass 386. Process for making a capacitor wherein a generally planar region of a semiconductive substrate forms a first capacitor plate with a dielectric layer and a second capacitor plate formed thereupon.

394 Including doping of semiconductive region:
This subclass is indented under subclass 393. Process for making a planar capacitor having a step of introducing electrically active dopant species into a semiconductive region of the substrate forming the first capacitor plate.

395 Multiple doping steps:
This subclass is indented under subclass 394. Process for making a planar capacitor utilizing plural steps of incorporating electrically active dopant species into a semiconductive region of the substrate forming the first capacitor plate.

396 Stacked capacitor:
This subclass is indented under subclass 386. Process for making a capacitor containing a number of capacitor plate and dielectric layers deposited successively one atop another.

397 Including selectively removing material to undercut and expose storage node layer:
This subclass is indented under subclass 396. Process for making a stacked capacitor having a step of selectively removing material to undercut and expose the capacitor electrode which serves as the storage node layer.

(1) Note. The capacitor electrode on which the electrical charge is stored is referred to as the storage node layer.

398 Including texturizing storage node layer:
This subclass is indented under subclass 396. Process for making a stacked capacitor having a step of roughening the surface of the capacitor plate which serves as the storage node layer.

(1) Note. The capacitor electrode on which the electrical charge is stored is referred to as the storage node layer.

399 Having contacts formed by selective growth or deposition:
This subclass is indented under subclass 396. Process for making a stacked capacitor wherein electrical contacts are formed by selective growth or deposition of conductive material onto the substrate.

400 FORMATION OF ELECTRICALLY ISOLATED LATERAL SEMICONDUCTIVE STRUCTURE:
This subclass is indented under the class definition. Process for making partial or total electrical isolation means serving to minimize electrical current flow between laterally adjoining semiconductive regions of the substrate.

(1) Note. To be proper hereunder, the proximate function of the formed semiconductor structure must be to electrically isolate laterally adjoining semiconductive regions, wherein each region is adapted for the construction of an electrical device.

SEE OR SEARCH THIS CLASS, SUBCLASS:

49 for a process of manufacturing a regenerative switching device having a guard ring or field plate component.

196 for a process of making a junction gate field effect transistor having an electrical isolation structure.

207 for a process of making a structure combining complementary insulated gate field effect transistors with a bipolar transistor (BiCMOS) additionally having an electrical isolation structure.

218 for a process of making a structure having complementary insulated gate field effect transistors (CMOS) additionally having an electrical isolation structure.

294 for a process of manufacturing an insulated gate field effect transistor having an electrical isolation structure.

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353 for a process of manufacturing a bipolar transistor having an electrical isolation structure.

455 for a process in which plural semiconductive substrates are joined together with insulative material to provide layered semiconductive regions which may be electrically isolated from one another.

479 for a process involving fluid growth of a layer of semiconductive material upon an insulative substrate (i.e., SOI formation).

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 499+ for an integrated circuit structure with electrically isolated components.

401 Having substrate registration feature (e.g., alignment mark):

This subclass is indented under subclass 400. Process wherein the process of forming electrical isolation utilizes an alignment feature formed on the semiconductive substrate or forms an alignment feature for subsequent use.

402 And gettering of substrate:

This subclass is indented under subclass 400. Process for making laterally spaced electrically isolated semiconductor regions having a step of gettering a semiconductor substrate.

403 Having semi-insulating component:

This subclass is indented under subclass 400. Process for making laterally spaced electrically isolated semiconductor regions wherein a high resistivity semiconductive component serves to electrically isolate, at least in part, the laterally spaced regions.

404 Total dielectric isolation:

This subclass is indented under subclass 400. Process for making laterally spaced electrically isolated semiconductor regions wherein the semiconductive regions are fully electrically isolated by dielectric insulative material.

SEE OR SEARCH THIS CLASS, SUBCLASS:

219 for a process of making complementary insulated gate field effect transistors having total dielectric isolation means.

295 for a process of making an insulated gate field effect transistor having total dielectric isolation means.

355 for a process of making a bipolar transistor having total dielectric isolation means.

405 And separate partially isolated semiconductor regions:

This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure additionally having laterally spaced semiconductor regions at least one of which is fully electrically isolated from other laterally spaced semiconductive regions and at least one other region which is partially electrically isolated from another laterally spaced semiconductive region.

406 Bonding of plural semiconductive substrates:

This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure including a step of joining plural semiconductive substrates together into a coherent monolith, such as by thermal treatment.

SEE OR SEARCH THIS CLASS, SUBCLASS:

455 for a process of laminating or bonding of plural semiconductive substrates not resulting in an electrically isolated lateral semiconductor structure.

407 Nondopant implantation:

This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure including a step of ion implantation of a nonelectrically active impurity into a semiconductive region of the substrate.

(1) Note. The nondopant may react with the semiconductor region to produce a dielectric material embedded in the semiconductor region.

408 With electrolytic treatment step:

This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure including a step of

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electrochemical treatment of the semiconductor substrate (i.e., such as to affect etching or coating action thereupon).

409 Porous semiconductor formation:
This subclass is indented under subclass 408. Process wherein the electrolytic treatment results in the formation of a porous semiconductor component.

410 Encroachment of separate locally oxidized regions:
This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure including a step of oxidation of adjacent semiconductive regions whereby the oxidized regions acquire a touching relationship.

411 Air isolation (e.g., beam lead supported semiconductor islands, etc.):
This subclass is indented under subclass 404. Process for making a total dielectric isolation structure wherein the resulting structure has islands of semiconductor material supported by beam leads and separated by air.

SEE OR SEARCH THIS CLASS, SUBCLASS:
461 for a process of depositing electrically conductive material to a semiconductive substrate and subsequently removing portions of the substrate to separate the same into beam leaded semiconductor devices.
619 for process of depositing an electrically conductive structure (i.e., metallization) upon a semiconductive substrate contacting spaced regions thereupon utilizing an air-gap dielectric.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 522 for an air bridge isolated integrated circuit structure.

412 Semiconductor islands formed upon insulating substrate or layer (e.g., mesa isolation, etc.):
This subclass is indented under subclass 411. Process for making a total dielectric isolation semiconductor structure wherein laterally spaced semiconductor islands are formed upon an insulative substrate or layer.

413 With epitaxial semiconductor formation:
This subclass is indented under subclass 404. Process for making a total dielectric isolation semiconductor structure having a step of epitaxially depositing a semiconductive layer onto the substrate.

414 Isolation by PN junction only:
This subclass is indented under subclass 400. Process whereby the laterally spaced regions of the semiconductor substrate are electrically isolated solely through the use of properly biased PN junctions.

415 Thermomigration:
This subclass is indented under subclass 414. Process for making junction isolated laterally spaced semiconductor regions having a step of dopant migration under the influence of a temperature gradient.

416 With epitaxial semiconductor formation:
This subclass is indented under subclass 414. Process for making junction isolated laterally spaced semiconductor regions having a step of epitaxially depositing a semiconductor layer.

417 And simultaneous polycrystalline growth:
This subclass is indented under subclass 416. Process for making junction isolated laterally spaced semiconductor regions in which polycrystalline semiconductive regions are deposited simultaneously with the epitaxial deposition.

418 Dopant addition:
This subclass is indented under subclass 416. Process for making junction isolated laterally spaced semiconductor regions including a step of introducing an electrically active dopant species into semiconductive regions of the substrate.

419 Plural doping steps:
This subclass is indented under subclass 418. Process for making junction isolated laterally spaced semiconductor regions including multiple steps of introducing an electrically active dopant species into semiconductive regions of the substrate.

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420 Plural doping steps:
This subclass is indented under subclass 414. Process for making an junction isolated laterally spaced semiconductor regions including multiple steps of introducing an electrically active dopant species into semiconductive regions of the substrate.

421 Having air-gap dielectric (e.g., groove, etc.):
This subclass is indented under subclass 400. Process for making an electrically isolated laterally spaced semiconductor structure resulting in laterally spaced semiconductive regions separated at least in part by a recessed air-gap feature relative to the surrounding surface (e.g., groove, trench, notch, etc.).

SEE OR SEARCH THIS CLASS, SUBCLASS:
411 for a process of forming a total dielectric isolation structure utilizing air isolation.

422 Enclosed cavity:
This subclass is indented under subclass 421. Process wherein the air-gap dielectric is in the form of an enclosed cavity or void between the laterally spaced semiconductive regions.

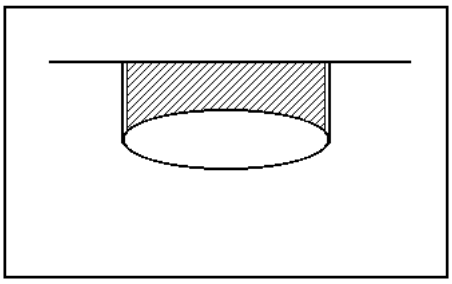
423 Implanting to form insulator:
This subclass is indented under subclass 400. Process for making an electrically isolated laterally spaced semiconductor structure including a step of implanting a nonelectrically active dopant species to form an insulative region which serves to electrically isolate lateral semiconductive regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
407 for a process of forming total dielectric isolation with a step of implanting a nondopant ion.
766 for a process of forming a buried insulative region by ion implantation of a nondopant species.

424 Grooved and refilled with deposited dielectric material:
This subclass is indented under subclass 400. Process for making electrically isolated laterally spaced semiconductor regions including a step of forming a recess or trench in the semiconductive substrate and refilling the same with deposited insulative material.

425 Combined with formation of recessed oxide by localized oxidation:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including the step of forming an embedded oxide by localized oxidation (of semiconductor material).

(1) Note. To be proper herein, the locally oxidized regions must consume semiconductor regions of the substrate (i.e., other than the oxidation solely of deposited layers residing within the groove). Additionally, the uppermost surface of the embedded oxide must be physically below the adjoining semiconductor top surface.



SEE OR SEARCH THIS CLASS, SUBCLASS:
444 for a process of forming a recessed oxide electrical isolation structure by localized oxidation including a preliminary step of forming a groove into the semiconductor substrate.

426 Recessed oxide laterally extending from groove:
This subclass is indented under subclass 425. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material whereby the embedded oxidized region extends laterally from the groove region.

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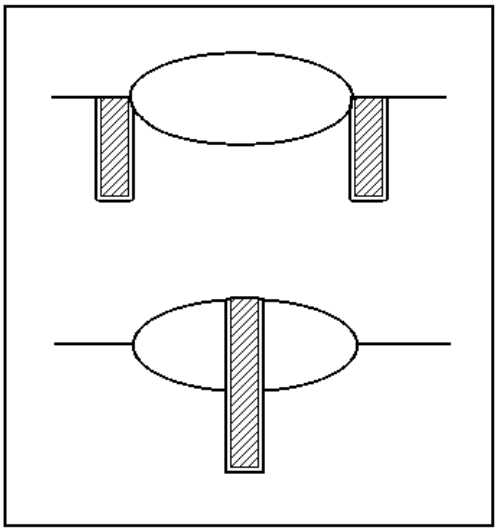

427 Refilling multiple grooves of different widths or depths:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material wherein grooves of differing widths or depths are filled with insulative material.

428 Reflow of insulator:
This subclass is indented under subclass 427. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including a step of redistributing insulative material by the viscous flow of the insulative material when exposed to high temperature.

429 And epitaxial semiconductor formation in groove:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including a step of epitaxially depositing semiconductive material in the groove.

430 And deposition of polysilicon or noninsulative material into groove:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material wherein polysilicon or noninsulative material is deposited into the groove.

431 Oxidation of deposited material:
This subclass is indented under subclass 430. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including a step of oxidizing the polysilicon or noninsulative material deposited into the groove.

432 Nonoxidized portions remaining in groove after oxidation:
This subclass is indented under subclass 431. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material wherein at least a portion of the polysilicon or noninsulative material deposited into the groove remains after the oxidation step.

433 Dopant addition:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material combined with a step of introducing an electrically active dopant species into a semiconductive region of the substrate.

434 From doped insulator in groove:
This subclass is indented under subclass 433. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material wherein the semiconductor regions are doped from a doped insulator residing in the groove.

435 Multiple insulative layers in groove:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with plural insulative layers.

436 Reflow of insulator:
This subclass is indented under subclass 435. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including a step of redistributing insulative material by the viscous flow of the insulative material when exposed to high temperature.

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437 Conformal insulator formation:
This subclass is indented under subclass 435. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including forming an insulative layer which follows the contour of the groove.

438 Reflow of insulator:
This subclass is indented under subclass 424. Process for making electrically isolated laterally spaced semiconductor regions by grooving and refilling with insulative material including a step of redistributing insulative material by the viscous flow of the insulative material when exposed to high temperature.

439 Recessed oxide by localized oxidation (i.e., LOCOS):
This subclass is indented under subclass 400. Process for making electrically isolated laterally spaced semiconductor regions including the step of oxidizing a portion of a semiconductive material to form an embedded oxide (e.g., field oxide) therein which isolates the laterally adjacent semiconductive regions.

440 Including nondopant implantation:
This subclass is indented under subclass 439. Process including a step of ion implanting a nonelectrically active impurity species into <u>any region</u> of the semiconductor substrate.

(1) Note. The nondopant may serve to alter the oxidation rate of the implanted region.

SEE OR SEARCH THIS CLASS, SUBCLASS:
423 for a process of forming a laterally spaced isolation structure involving the implantation of an ion which <u>reacts</u> with the substrate to form an insulative material.

441 With electrolytic treatment step:
This subclass is indented under subclass 439. Process including a step of electrochemical treatment of the semiconductor substrate (e.g., such as to affect etching or coating action thereon).

442 With epitaxial semiconductor layer formation:
This subclass is indented under subclass 439. Process including a step of epitaxially growing a single crystal semiconductor layer on the substrate.

443 Etchback of recessed oxide:
This subclass is indented under subclass 439. Process having a step of thinning the formed recessed oxide by chemical etching action followed by an additional step of oxidizing a semiconductive region of the substrate.

444 Preliminary etching of groove:
This subclass is indented under subclass 439. Process including a preliminary step of etching a trench into the semiconductive substrate followed by locally oxidizing the trench surfaces to form the recessed oxide therein.

SEE OR SEARCH THIS CLASS, SUBCLASS:
421 for a process of forming electrically isolated lateral semiconductive regions utilizing an air-gap separation.
425 for a process of forming a grooved and refilled electrical isolation structure including a step of forming an embedded localized oxidation region of the semiconductor substrate within or adjoining the groove.

445 Masking of groove sidewall:
This subclass is indented under subclass 444. Process utilizing a layer in contact with the groove sidewalls which serves as a protective covering during either an etching or oxidation step.

446 Polysilicon containing sidewall:
This subclass is indented under subclass 445. Process utilizing a polysilicon containing component for masking the groove sidewalls.

447 Dopant addition:
This subclass is indented under subclass 444. Process including a step of introducing an electrically active dopant species into semiconductive regions of the substrate.

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448 Utilizing oxidation mask having polysilicon component:
This subclass is indented under subclass 439. Process utilizing a layer in contact with the substrate having a polysilicon containing component which serves as a protective covering during the localized oxidation step.

449 Dopant addition:
This subclass is indented under subclass 439. Process including a step of introducing an electrically active dopant species into semiconductive regions of the substrate.

450 Implanting through recessed oxide:
This subclass is indented under subclass 449. Process wherein the dopant species is implanted through the recessed oxide into the semiconductive regions therebeneath.

451 Plural doping steps:
This subclass is indented under subclass 449. Process utilizing multiple steps of doping semiconductive regions of the substrate.

452 Plural oxidation steps to form recessed oxide:
This subclass is indented under subclass 439. Process having multiple steps of oxidizing the semiconductor substrate in the region of the recessed oxide.

453 And electrical conductor formation (i.e., metallization):
This subclass is indented under subclass 439. Process including a step of making an electrically conductive member integral to the semiconductive substrate.

(1) Note. The contact may be, for example, directly to semiconductive regions of the substrate or may reside atop the field oxide isolation structure.

SEE OR SEARCH THIS CLASS, SUBCLASS:
584 for a process of depositing electrically or thermally conductive material on a semiconductor substrate.

454 Field plate electrode:
This subclass is indented under subclass 400. Process having a step of forming an electrically conductive structure formed on a major surface of the semiconductor substrate for electrically separating laterally positioned device regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
584 for a process of depositing electrically or thermally conductive material on a semiconductor substrate.

455 BONDING OF PLURAL SEMICONDUCTOR SUBSTRATES:
This subclass is indented under the class definition. Process in which plural semiconductive substrates are joined together into a coherent body, such as by thermal treatment.

(1) Note. Connection of electrical terminals on transposed semiconductive substrates by joining the respective terminals on one substrate to the terminals on a second substrate (e.g., flip-chip bonding, etc.) is a packaging operation and as such cross-referencing hereunder is discouraged.

SEE OR SEARCH THIS CLASS, SUBCLASS:
107 for a process of packaging (e.g., mounting, encapsulating, etc.) involving the assembly of plural semiconductive substrates or the treating of a packaged device containing the same.
406 for a process of making a full electrical isolation structure including a laminating step whereby current flow will be minimized between laterally adjoining semiconductive regions.

SEE OR SEARCH CLASS:
65, Glass Manufacturing, particularly subclasses 36+ for fusion bonding of glass to a formed part. While Class 65 considers silicon and silicon dioxide glass, and hence takes the melting, shaping or fusion bonding of the same (as well as combined operations whether preparatory or subsequent to the melting, shaping, or fusion bonding step), if the structure formed is

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identified as having utility for semiconductor electrical devices, placement is proper in Class 438.

117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefor, subclass 1 for processes of joining independent crystals.

156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 60+, for a per se process of adhesive bonding or assembly therefor of plural preforms.

228, Metal Fusion Bonding, for processes of metal fusion bonding of semiconductive substrates.

456 Having enclosed cavity:
This subclass is indented under subclass 455. Process for joining plural semiconductive substrates into an integral body resulting in a partially or wholly enclosed void structure therein.

SEE OR SEARCH THIS CLASS, SUBCLASS:

422 for a process of forming an electrically isolated lateral semiconductive structure utilizing a partially or wholly enclosed cavity as an air-gap dielectric.

457 Warping of semiconductor substrate:
This subclass is indented under subclass 455. Process for joining plural semiconductive substrates into an integral body including a step of bending one or more of the semiconductor substrates to be joined.

458 Subsequent separation into plural bodies (e.g., delaminating, dicing, etc.):
This subclass is indented under subclass 455. Process for joining plural semiconductive substrates into an integral body having a step of dividing the integral body into plural individual bodies subsequent to the joining operation.

SEE OR SEARCH CLASS:

156, Adhesive Bonding and Miscellaneous Chemical Manufacture, subclasses 701 through 719 and 930-932 for a delaminating process, per se, for separating an adhered layer or portion from another layer at a bonding face with identity retained as semiconductive.

459 Thinning of semiconductor substrate:
This subclass is indented under subclass 455. Process for joining plural semiconductive substrates into an integral body having a step of reducing the thickness of at least one of the semiconductive substrates.

460 SEMICONDUCTOR SUBSTRATE DICING:
This subclass is indented under the class definition. Process including the step of separating the semiconductor substrate into plural individual bodies (e.g., die, etc.) usually by removal of material therefrom or by cleavage thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:

113 for a process of packaging (e.g., mounting, encapsulating, etc.) of treating a packaged semiconductor device having a step of dividing a semiconductor substrate into discrete individual units.

SEE OR SEARCH CLASS:

83, Cutting, for a generic process of cutting a substrate into discrete individual units.

225, Severing by Tearing or Breaking, subclasses 1+ for methods.

451, Abrading, for a process of dicing by abrading.

461 Beam lead formation:
This subclass is indented under subclass 460. Process for separating a semiconductor substrate into plural individual bodies wherein the resultant bodies possess electrical leads which extend beyond the edges of the body (i.e., cantilevered).

SEE OR SEARCH THIS CLASS, SUBCLASS:

411 for a process of making laterally spaced isolated semiconductor structure wherein self-supporting electrodes hold plural semiconductor bodies in spaced relationship to each other.

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SEE OR SEARCH CLASS:

29, Metal Working, subclass 827 for beam lead device manufacture wherein an electrically conductive body is mounted in a cantilever fashion to an electrical device.

462 Having specified scribe region structure (e.g., alignment mark, plural grooves, etc.):

This subclass is indented under subclass 460. Process wherein the region of the semiconductor substrate delineating the separating boundary between adjacent die possesses a specified structure.

(1) Note. The specified structure may serve no function in the separation of the substrate into plural bodies (e.g., alignment marks, etc.) or may facilitate the separation operation (e.g., plural grooves of specified relationship, a trench having significant sidewall structure, etc.).

(2) Note. A scribe groove, per se, or plural scribe lines intersecting in such a way so as to form chips of a certain shape (e.g., trapezoidal, etc.) are not considered proper herein.

463 By electromagnetic irradiation (e.g., electron, laser, etc.):

This subclass is indented under subclass 460. Process utilizing electromagnetic radiation for dividing the semiconductor substrate into plural distinct bodies.

(1) Note. Proper for this subclass are processes wherein the electromagnetic irradiation serves to from a "scribe" line (i.e., a weakened or removed area to facilitate subsequent separation) combined with an additional step of separating the substrate into distinct bodies at such line.

464 With attachment to temporary support or carrier:

This subclass is indented under subclass 460. Process including a step of attaching the semiconductor substrate to a temporary holder to facilitate the handling of the substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:

106 for a process of packaging (e.g., mounting, encapsulating, etc.) a semiconductor substrate by securing the same to a support (i.e., a mounting) or treating a packaged semiconductor device.

465 Having a perfecting coating:

This subclass is indented under subclass 460. Process including a step of coating the semiconductor substrate with a coating which enhances the dicing operation.

466 DIRECT APPLICATION OF ELECTRICAL CURRENT:

This subclass is indented under the class definition. Process including the step having an electric current come in direct contact with the semiconductor substrate (i.e., nonradiatively) to treat the same.

(1) Note. Per se (a) irradiation of ionized atoms or molecules to implant the same into a semiconductor material, (b) exposing a semiconductive substrate to a plasma or electron beam, or (c) electrochemical treatment of a semiconductive substrate, is not considered a direct application electrical treatment for this and indented subclasses.

SEE OR SEARCH THIS CLASS, SUBCLASS:

10 for a semiconductor manufacturing process including a step of measuring or testing of the process or of the substrate for feedback control of the manufacturing process.

17 for a semiconductor manufacturing process including a step of measuring or testing an electrical characteristic of the process or of the substrate.

88 for a process of making a device responsive to electromagnetic radiation having a step of directly applying electrical current.

101 for a process of manufacturing a point contact semiconductive device having a step of directly applying electrical current.

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103 for a process of manufacturing a device having a selenium or tellurium elemental semiconductive device including a step of directly applying electrical current.

292 for a process of making an insulated gate field effect transistor having a step of directly applying electrical current.

351 for a process of making a bipolar transistor having a step of directly applying electrical current.

SEE OR SEARCH CLASS:

204, Chemistry: Electrical and Wave Energy, especially subclasses 192.1+ for processes of coating, forming, or etching by sputtering.

324, Electricity: Measuring and Testing, appropriate subclass for per se electrical testing (i.e., aging).

467 To alter conductivity of fuse or antifuse element:

This subclass is indented under subclass 466. Process involving the direct application of electrical current to a fuse or antifuse portion of the semiconductor substrate to alter the conductivity of same.

SEE OR SEARCH THIS CLASS, SUBCLASS:

132 for a process of making an array of electrical devices and selectively interconnecting the devices via fusible links.

281 for a process of making an insulated gate field effect transistor combined with a fuse or integral short.

333 for a process of making a bipolar transistor combined with a fuse or integral short.

468 Electromigration:

This subclass is indented under subclass 466. Process involving the movement of atoms (usually dopant atoms) under the influence of an electric field.

469 Utilizing pulsed current:

This subclass is indented under subclass 466. Process wherein the electrical current is presented in periodic surges.

470 Fusion of semiconductor region:

This subclass is indented under subclass 466. Process wherein semiconductor regions of the substrate are melted upon application of the electrical current.

SEE OR SEARCH THIS CLASS, SUBCLASS:

89 for a process of making a semiconductive device responsive to electromagnetic radiation having a step of fusing or solidifying a semiconductive region of the substrate.

293 for a process of making an insulated gate field effect transistor having a step of fusing or solidifying a semiconductive region of the substrate.

352 for a process of making a bipolar transistor having a step of fusing or solidifying a semiconductive region of the substrate

471 GETTERING OF SUBSTRATE:

This subclass is indented under the class definition. Process having a step of treating a semiconductor substrate to reduce or remove deleterious defects (impurities, vacancies, dislocations, etc.) therefrom.

(1) Note. Examples of gettering techniques include segregation (e.g., coalescence) of defects to a defined region, implanting internal defect localizing regions, removal of superfluous electrical charges other than mere static electricity or those accumulated during manufacture (e.g., passivation of dangling bonds on the substrate surface by covalently bonding to hydrogen), and removal of mobile ion contamination such as by volatilization.

(2) Note. The introduction of recombination centers (i.e., deep level dopants) into the semiconductor substrate, such centers serving to control carrier lifetime, is not considered to be gettering for the purpose of this and indented subclasses. However, the removal of the same from the semiconductor substrate is proper hereunder.

(3) Note. Gettering includes treating the substrate locally (e.g., surface, internal

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regions, etc.). In gettering, impurities within the substrate may be attracted to a region of the substrate where they can be removed or "fixed". In cleaning, foreign matter on the substrate surface is removed. Thus there may be a cleaning step within an overall process of gettering. Processes of apparatus gettering (i.e., apparatus cleaning) are not considered proper hereunder unless combined with the gettering of a semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:

115 for a step of contaminant removal or mitigation in a process of mounting, packaging, or encapsulating a semiconductor device.

510 for a process of doping semiconductive regions with an electrically active element.

795 for a process of radiation or energy treating a semiconductive substrate to modify the properties thereof of semiconductive regions thereof.

SEE OR SEARCH CLASS:

134, Cleaning and Liquid Contact With Solids, subclasses 1 through 42 for a process of cleaning.

472 By vibrating or impacting:

This subclass is indented under subclass 471. Process wherein a step of vibrating the semiconductive substrate or striking the semiconductive substrate with solid material is utilized to produce a gettering effect.

SEE OR SEARCH CLASS:

134, Cleaning and Liquid Contact With Solids, especially subclasses 6+ for a process of cleaning a semiconductor wafer by impacting the wafer with solid matter.

473 By implanting or irradiating:

This subclass is indented under subclass 471. Process wherein a step of implanting or irradiating the semiconductive substrate is utilized to produce a gettering effect.

474 Ionized radiation (e.g., corpuscular or plasma treatment, etc.):

This subclass is indented under subclass 473. Process wherein ionized radiation is applied to the semiconductor substrate to produce a gettering effect.

475 Hydrogen plasma (i.e., hydrogenization):

This subclass is indented under subclass 474. Process wherein the radiation is a plasma containing ionized hydrogen (i.e., proton irradiation).

476 By layers which are coated, contacted, or diffused:

This subclass is indented under subclass 471. Process wherein the substrate is exposed to a specified material by (a) depositing a layer of the material on the substrate, (b) physically contacting the substrate with the material, or (c) diffusing into the substrate a gettering species to form a gettering region in the substrate.

477 By vapor phase surface reaction:

This subclass is indented under subclass 471. Process in which the substrate is treated with a reactive gas mixture which preferentially forms volatile compounds with the undesired impurities.

478 FORMATION OF SEMICONDUCTIVE ACTIVE REGION ON ANY SUBSTRATE (E.G., FLUID GROWTH, DEPOSITION, ETC.):

This subclass is indented under the class definition. Process for depositing onto any substrate single or multiple layers of semiconductor material adapted to serve as an active device region, the semiconductive material being deposited as amorphous, polycrystalline, or single crystalline material.

(1) Note. Included herein are those processes for the fluid growth of semiconductive material having a sufficiently high resistivity so as to be termed semi-insulative. However, if the proximate function of the semiconductive material is as a electrical conductor (e.g., a multilayer inter-connect having a polysilicon layer), classification is excluded fro m this and indented subclasses.

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SEE OR SEARCH THIS CLASS, SUBCLASS:

102 for selenium or tellurium elemental semiconductor deposition,

104 for transition metal oxide or copper sulfide compound semiconductor deposition,

105 for diamond semiconductor deposition,

412 for a process of forming laterally spaced isolated semiconductive islands/mesas upon an insulating substrate or layer.

414 for a process of forming laterally spaced junction isolated semiconductive regions.

423 Chemistry of Inorganic Compounds, particularly subclasses 348+ for methods of producing elemental silicon intended as a feedstock for later fabrication into active layers/regions.

584 for a process of coating conductive material onto a semiconductive substrate, or intermediate layers thereupon.

SEE OR SEARCH CLASS:

117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefor, for processes of single crystal growth of semiconductor material upon a seed or substrate and perfecting steps combined therewith.

479 On insulating substrate or layer:

This subclass is indented under subclass 478. Process wherein the semiconductor layer is deposited onto an electrically insulating substrate or layer.

(1) Note. The formation of a semiconductive active region on an insulative substrate by the chemical reduction of a portion of the insulative substrate thereby altering the reduced portion of the insulative substrate into a semiconductive region is proper herein.

480 Including implantation of ion which reacts with semiconductor substrate to form insulating layer:

This subclass is indented under subclass 479. Process for the deposition of a semiconductor layer onto an electrically insulating layer including implanting an ion which reacts with the semiconductive regions of the substrate to form an electrically insulating layer.

SEE OR SEARCH THIS CLASS, SUBCLASS:

766 for a per se process of implanting an ion which reacts with semiconductive regions of the substrate to form an electrical insulator.

481 Utilizing epitaxial lateral overgrowth:

This subclass is indented under subclass 479. Process wherein the semiconductor material is deposited so as to overlay electrically insulative material and such that epitaxial growth occurs laterally from a crystal seeding region.

482 Amorphous semiconductor:

This subclass is indented under subclass 478. Process wherein the deposited semiconductive material possesses no regular crystalline lattice.

483 Compound semiconductor:

This subclass is indented under subclass 482. Process wherein the deposited amorphous semiconductor is a compound semiconductor.

484 Running length (e.g., sheet, strip, etc.):

This subclass is indented under subclass 482. Process involving the fluid growth of an amorphous semiconductor onto a substrate presented as a continuum of indeterminate length.

SEE OR SEARCH THIS CLASS, SUBCLASS:

62 for a process of making a device responsive to electromagnetic radiation utilizing the deposition of a semiconductive active layer onto a substrate of indeterminate length.

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485 Deposition utilizing plasma (e.g., glow discharge, etc.):
This subclass is indented under subclass 482. Process utilizing a plasma or glow discharge during the deposition of the semiconductive material.

486 And subsequent crystallization:
This subclass is indented under subclass 482. Process having a step of depositing an amorphous semiconductor layer combined with the subsequent crystallization of the amorphous semiconductor layer.

SEE OR SEARCH CLASS:
117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefor, appropriate subclasses for the process of single crystallization and perfecting steps therewith.

487 Utilizing wave energy (e.g., laser, electron beam, etc.):
This subclass is indented under subclass 486. Process whereby the crystallization is affected by the application of a source of wave energy to the amorphous semiconductor.

488 Polycrystalline semiconductor:
This subclass is indented under subclass 478. Process wherein the deposited semiconductive material is polycrystalline (i.e., possesses multiple crystalline regions having grain boundaries therebetween).

SEE OR SEARCH THIS CLASS, SUBCLASS:
764 for processes of depositing semi-insulative polycrystalline silicon upon a semiconductive substrate.

489 Simultaneous single crystal formation:
This subclass is indented under subclass 488. Process wherein both single and polycrystalline regions are simultaneously formed on the same substrate.

490 Running length (e.g., sheet, strip, etc.):
This subclass is indented under subclass 488. Process involving the fluid growth of an indeterminate length of amorphous semiconductor.

SEE OR SEARCH THIS CLASS, SUBCLASS:
62 for a process of making a device responsive to electromagnetic radiation utilizing the deposition of a semiconductive active layer onto a substrate of indeterminate length.

491 And subsequent doping of polycrystalline semiconductor:
This subclass is indented under subclass 488. Process having a subsequent step of incorporating an electrically active dopant species into the polycrystalline semiconductive material.

492 Fluid growth step with preceding and subsequent diverse operation:
This subclass is indented under subclass 478. Process having a step of the fluid growth of a semiconductor active region combined with a preceding nonfluid growth step and a subsequent nonfluid growth step.

493 Plural fluid growth steps with intervening diverse operation:
This subclass is indented under subclass 478. Process wherein multiple fluid growth steps having combined therewith at least one step not perfecting to either prior or subsequent growth steps and which step is preformed intermediate to the multiple fluid growth steps.

SEE OR SEARCH CLASS:
117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefor, appropriate subclasses for the process of single crystallization and perfecting steps therewith.

494 Differential etching:
This subclass is indented under subclass 493. Process where the differential etching of the substrate intermediate to the steps of fluid growth of semiconductive material is the diverse step.

495 Doping of semiconductor:
This subclass is indented under subclass 493. Process wherein the incorporation of an electrically active dopant species into a semiconductive region of the substrate intermediate to the

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steps of fluid growth of semiconductive material is the diverse step.

496 Coating of semiconductive substrate with nonsemiconductive material:
This subclass is indented under subclass 493. Process wherein the coating of a nonsemiconductive material intermediate to the steps of fluid growth of semiconductive material is the diverse operation.

497 Fluid growth from liquid combined with preceding diverse operation:
This subclass is indented under subclass 478. Process having a nonfluid growth operation which precedes the fluid growth of semiconductive material from the liquid state and is not merely perfecting thereto.

(1) Note. See Class 117, class definition section I, C, (4) Note, for a detailed description of the types of perfecting prior operations which in combination with a step of single crystal growth are proper therein.

498 Differential etching:
This subclass is indented under subclass 497. Process wherein the differential etching of the substrate prior to the fluid growth of semiconductive material from the liquid state is the diverse step.

499 Doping of semiconductor:
This subclass is indented under subclass 497. Process wherein a semiconductive region of the substrate is incorporated with an electrically active dopant species prior to a step of fluid growth of semiconductive material from the liquid state.

500 Fluid growth from liquid combined with subsequent diverse operation:
This subclass is indented under subclass 478. Process having a nonfluid growth operation which is subsequent to the fluid growth of semiconductive active region from the liquid state and is not merely perfecting thereto.

(1) Note. See Class 117, class definition (4) Note, for a detailed description of the types of perfecting subsequent operations which in combination with a step of single crystal growth are proper therein.

501 Doping of semiconductor:
This subclass is indented under subclass 500. Process wherein a semiconductive region of the substrate is incorporated with an electrically active dopant species subsequent to a step of fluid growth of semiconductive material from the liquid state.

502 Heat treatment:
This subclass is indented under subclass 500. Process wherein the substrate having the deposited semiconductor active region thereon is heat treated following a step of fluid growth of semiconductive material from the liquid state.

503 Fluid growth from gaseous state combined with preceding diverse operation:
This subclass is indented under subclass 478. Process having a nonfluid growth operation which precedes the fluid growth of semiconductive material from the vapor state and is not merely perfecting thereto.

(1) Note. See Class 117, class definition section I, C, (4) Note, for a detailed description of the types of perfecting prior operations which in combination with a step of single crystal growth are proper therein.

504 Differential etching:
This subclass is indented under subclass 503. Process wherein the differential etching of the substrate prior to the fluid growth of semiconductive material from the gaseous state is the diverse step.

505 Doping of semiconductor:
This subclass is indented under subclass 503. Process wherein a semiconductive region of the substrate is incorporated with an electrically active dopant species prior to a step of fluid growth of semiconductive material from the vapor or gaseous state.

506 Ion implantation:
This subclass is indented under subclass 505. Process wherein the doping is by implantation of dopant ions into the semiconductor regions of the substrate.

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507 Fluid growth from gaseous state combined with subsequent diverse operation:
This subclass is indented under subclass 478. Process having a nonfluid growth operation which is subsequent to the fluid growth of semiconductive active region from the gaseous state and is not merely perfecting thereto.

(1) Note. See Class 117, class definition section I, C, (4) Note, for a detailed description of the types of perfecting subsequent operations which in combination with a step of single crystal growth are proper therein.

508 Doping of semiconductor:
This subclass is indented under subclass 507. Process wherein a semiconductive region of the substrate is incorporated with an electrically active dopant species subsequent to a step of fluid growth of semiconductive material from the gaseous state.

509 Heat treatment:
This subclass is indented under subclass 507. Process wherein the substrate having the deposited semiconductor active region thereon is heat treated following a step of fluid growth of semiconductive material from the gaseous state.

510 INTRODUCTION OF CONDUCTIVITY MODIFYING DOPANT INTO SEMICONDUCTIVE MATERIAL:
This subclass is indented under the class definition. Process involving the incorporation within a semiconductive substrate of material referred to as dopants or dopant modifiers or impurity functioning to alter the electrical characteristics of semiconductive regions thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
301 for a process of making an insulated gate field effect transistor having a step for the self-aligned doping of source or drain regions.
414 for the formation of laterally spaced isolation regions within a semiconductive substrate by the use of differently doped semiconductive regions.
471 for incorporation within a semiconductive substrate of sites (e.g., precipitates, strained layers, etc.) functioning as gettering sites.
658 for processes of incorporating an alloying constituent into a conductive layer deposited upon a semiconductive substrate.
783 for processes of incorporating an additional constituent into a insulative region deposited upon a semiconductive substrate.

SEE OR SEARCH CLASS:
250, Radiant Energy, subclasses 492.1+ for generic irradiation of a semiconductor substrate, per se, wherein no doping of the semiconductor substrate occurs.

511 Ordering or disordering
This subclass is indented under subclass 510. Process for making semiconductor regions of the substrate ordered or disordered prior to, simultaneous with, or subsequent to a step of doping semiconductor regions of the substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
36 for a process of making a device emissive of a nonelectrical signal having a step of affecting ordering or disordering of semiconductor regions of the substrate.
797 for processes of radiation or energy treatment of a compound semiconductor substrate to affect ordering or disordering.

512 Involving nuclear transmutation doping:
This subclass is indented under subclass 510. Process for introducing a dopant into semiconductor regions of the substrate having a combination of diverse steps in which one step involves the conversion of an element into a dopant by nuclear transmutation.

SEE OR SEARCH CLASS:
376, Induced Nuclear Reactions, Systems, and Elements, subclass 183 for per se nuclear transmutation doping of semiconductors.

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513 Plasma (e.g., glow discharge, etc.):
This subclass is indented under subclass 510. Process involving the use of a gaseous vapor of ions in equilibrium or a vapor of ions in vacuum in nonequilibrium state (i.e., a "cold plasma") to introduce a dopant into the semiconductive material.

SEE OR SEARCH THIS CLASS, SUBCLASS:
485 for a process of utilizing a plasma or glow discharge during the deposition of an amorphous semiconductive layer upon a substrate wherein the proximate function of the amorphous semiconductor material is as an active semiconductor region.

SEE OR SEARCH CLASS:
204, Chemistry: Electrical and Wave Energy, especially subclass 192.12 for glow discharge sputter deposition (e.g., cathode sputtering).

514 Ion implantation of dopant into semiconductor region:
This subclass is indented under subclass 510. Process involving penetration of the surface of the semiconductive regions of the substrate with electrically active dopant species possessing sufficient kinetic energy therefor, usually resulting in the formation of a barrier layer rectifying junction within the semiconductive regions.

(1) Note. Ion implantation involves the introduction of a desired dopant species into a semiconductive region of a substrate by ionizing the dopant material and accelerating the resulting ions through a carefully controlled voltage to impinge on the semiconductive region so that the depth of the resulting dopant atoms is determined by the accelerating voltage and the doping density is determined by the flux of the ion beam.

SEE OR SEARCH THIS CLASS, SUBCLASS:
535 for the implantation of dopant ions into nonsemiconductive regions of the substrate and subsequent diffusion into semiconductive regions.
659 for the implantation of an ion into a metallic or conductive region of the substrate.
798 for the ionized irradiation of a semiconductor substrate to modify the properties of semiconductor regions contained therein.

SEE OR SEARCH CLASS:
250, Radiant Energy, subclasses 492.1+ for generic processes of irradiating objects or material wherein no function is attributed to the implanted species.
427, Coating Processes, subclasses 523+ for a coating process involving ion plating or implantation (see especially subclass 527 when silicon is present in the substrate, plating, or implanted layer).

(1) Note. Processes utilizing ion bombardment or ion treating, that specifies neither implanting, etching, plating, etc., but merely recites some change as in the materials characteristic properties of the semiconductor substrate go as original to Class 438.

515 Ionized molecules
This subclass is indented under subclass 514. Process involving the use of ionized molecules possessing sufficient kinetic energy to penetrate the semiconductive substrate with one or more of the elements of the molecule remaining in the semiconductive regions functioning as an electrically active dopant.

516 Including charge neutralization:
This subclass is indented under subclass 514. Process including discharging electrical charges which would otherwise accumulate in the semiconductor substrate due to the implantation of electrically active dopant ions therein.

517 Of semiconductor layer on insulating substrate or layer:
This subclass is indented under subclass 514. Process wherein the electrically active dopant ions are implanted into a semiconductor layer or portion thereof, the semiconductor layer residing on an insulating substrate or layer.

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518 Of compound semiconductor:
This subclass is indented under subclass 514. Process wherein the semiconductive region into which the electrically active dopant is implanted is a compound semiconductor.

519 Including multiple implantation steps:
This subclass is indented under subclass 518. Process having plural steps of implanting ions, at least one step of which introduces an electrically active dopant ion, into a compound semiconductive substrate.

520 Providing nondopant ion (e.g., proton, etc.):
This subclass is indented under subclass 519. Process wherein a nonelectrically active impurity species is implanted into a compound semiconductor region of the substrate in conjunction with the prior, simultaneous, or subsequent implantation of an electrically active dopant ion.

(1) Note. Process for the implantation of positively charged hydrogen ions (i.e., protons) in conjunction with the implantation of a dopant is proper herein.

521 Using same conductivity-type dopant:
This subclass is indented under subclass 519. Process wherein the multiple implantation steps introduce electrically active dopant ions of the same conductivity type into one or more regions of the compound semiconductor substrate.

522 Including heat treatment:
This subclass is indented under subclass 518. Process including a step of heat treating the substrate having compound semiconductive regions.

SEE OR SEARCH THIS CLASS, SUBCLASS:
542 for a per se process of diffusing (i.e., driving-in) a dopant into semiconductive regions of the substrate via a heat treatment step.

523 And contact formation (i.e., metallization):
This subclass is indented under subclass 518. Process including a step of making an electrical contact to a compound semiconductor region of the substrate.

524 Into grooved semiconductor substrate region:
This subclass is indented under subclass 514. Process wherein the electrically active dopant is implanted into a trench or recess formed in a semiconductor region of the substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
389 for a process of making a trench capacitor including doping of the surfaces of the trench.
433 for a process of forming electrically isolated lateral semiconductor structure by forming a groove and refilling the same with dielectric material combined with a step of doping a semiconductor region of the substrate.
447 for a process of forming electrically isolated lateral semiconductor structure by forming a recessed oxide via localized oxidation combined with the preliminary etching of a groove and doping a semiconductor region of the substrate.

525 Using oblique beam:
This subclass is indented under subclass 514. Process wherein the angle of the ion beam relative to the major surface of the semiconductor substrate is other than 90 degrees.

SEE OR SEARCH THIS CLASS, SUBCLASS:
302 for a process of making an insulated gate field effect transistor having a step of self-aligned doping of source and/or drain regions via oblique ion implantation.

526 Forming buried region:
This subclass is indented under subclass 514. Process involving a step of producing a region implanted with an electrically active dopant which is not in contact with the free surface of the semiconductor substrate through which it was implanted.

(1) Note. The mere indication that the projected range (i.e., the average depth of the implanted ions) is of a particular value is insufficient for placement herein.

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527 Including multiple implantation steps:
This subclass is indented under subclass 514. Process having plural steps of implanting ions, at least one step of which introduces an electrically active dopant ion, into a semiconductive substrate.

528 Providing nondopant ion (e.g., proton, etc.):
This subclass is indented under subclass 527. Process wherein a nonelectrically active impurity species is implanted into a semiconductor region of the substrate in conjunction with the prior, simultaneous, or subsequent implantation of an electrically active dopant species.

(1) Note. Process for the implantation of positively charged hydrogen ions (i.e., protons) in conjunction with the implantation of a dopant is included herein.

529 Using same conductivity-type dopant:
This subclass is indented under subclass 527. Process wherein the multiple implantation steps introduce electrically active dopant ions of the same conductivity type into one or more regions of the semiconductor substrate.

530 Including heat treatment:
This subclass is indented under subclass 514. Process including a step of heat treating the semiconductive substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
795 for a process of heat treatment of a semiconductive substrate to modify the properties thereof.

531 Using shadow mask:
This subclass is indented under subclass 514. Process involving the use of a spaced templet positioned with respect to the ion source and the semiconductor substrate in such a manner as to allow the electrically active dopant ions to impinge only a portion of the semiconductor substrate.

532 Into polycrystalline region:
This subclass is indented under subclass 514. Process involving implanting electrically active dopant ions into polycrystalline semiconductive regions.

533 And contact formation (i.e., metallization):
This subclass is indented under subclass 514. Process including a step of forming an electrical contact to a semiconductor region of the substrate.

534 Rectifying contact (i.e., Schottky contact):
This subclass is indented under subclass 533. Process wherein the electrical contact is a rectifying contact.

535 By application of corpuscular or electromagnetic radiation (e.g., electron, laser, etc.):
This subclass is indented under subclass 510. Process having a step of applying corpuscular or electromagnetic radiation to the semiconductor substrate to affect the incorporation of an electrically active dopant therein.

(1) Note. See herein for a process of implantation of dopant ions into nonsemiconductive regions of the substrate and subsequent diffusion into semiconductive regions thereof.

536 Recoil implantation:
This subclass is indented under subclass 535. Process involving the use of kinetic energy via the use of applied corpuscular or electromagnetic radiation for introduction of an electrically active dopant species to a semiconductive region of the substrate whereby at least a portion of the kinetic energy travels in other than a straight path (e.g., bounces back and forth).

SEE OR SEARCH CLASS:
204, Chemistry: Electrical and Wave Energy, especially subclass 192.11 for ion beam sputter deposition.

537 Fusing dopant with substrate (i.e., alloy junction):
This subclass is indented under subclass 510. Processes for incorporating an electrically active impurity into a semiconductor material during an operation affecting the partial melting of the substrate.

(1) Note. The impurity contact alloys with a semiconductor material to form a p-type or n-type region, depending on the impurity used.

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SEE OR SEARCH THIS CLASS, SUBCLASS:

470 for a process of fusing a dopant with a semiconductive region by the direct application of electrical current.

538 Using additional material to improve wettability or flow characteristics (e.g., flux, etc.):
This subclass is indented under subclass 537. Processes including the incorporation of an agent to alter the melting and crystallization of the alloying operation.

539 Application of pressure to material during fusion:
This subclass is indented under subclass 537. Processes wherein pressure is applied during the alloying operation.

540 Including plural controlled heating or cooling steps or nonuniform heating:
This subclass is indented under subclass 537. Processes including regulated multiple cooling or heating operations, or nonuniform application of thermal energy to the semiconductor substrate during the alloying operation.

541 Including diffusion after fusing step:
This subclass is indented under subclass 540. Processes including a step of solid-state diffusion subsequent to the alloying operation.

542 Diffusing a dopant:
This subclass is indented under subclass 510. Processes for permeating an electrically active impurity in a semiconductive region of the substrate.

543 To control carrier lifetime (i.e., deep level dopant):
This subclass is indented under subclass 542. Processes involving the introduction by diffusion of an impurity serving to form energy levels in the forbidden band of a semiconductor material that can act as traps for charge carriers (e.g., gold (Au), chromium (Cr), iron (Fe), nickel (Ni), etc.).

544 To solid-state solubility concentration:
This subclass is indented under subclass 542. Processes involving the introduction by diffusion at a concentration level up to the limit at which precipitation out of solid solution begins to occur for the particular electrically active impurity in the semiconductive material.

545 Forming partially overlapping regions:
This subclass is indented under subclass 542. Processes for permeating one or more electrically active impurities in localized areas which lap over each other only in part.

546 Plural dopants in same region (e.g., through same mask opening, etc.):
This subclass is indented under subclass 542. Processes for applying multiply electrically active impurities in the same area.

547 Simultaneously:
This subclass is indented under subclass 546. Processes wherein the multiple electrically active impurities are applied at the same time.

548 Plural dopants simultaneously in plural regions:
This subclass is indented under subclass 542. Processes for permeating multiple electrically active impurities in multiple localized areas.

549 Single dopant forming plural diverse regions (e.g., forming regions of different concentrations or of different depths, etc.):
This subclass is indented under subclass 542. Processes for permeating an electrically active impurity into multiple different localized areas which differ in the amount of impurity, the distance the impurity has to travel inwardly from the surface, or the like.

550 Nonuniform heating:
This subclass is indented under subclass 542. Processes including the nonuniform application of thermal energy to the semiconductor substrate (e.g., heating distinct areas as opposed to heating the entire substrate, etc.).

551 Using multiple layered mask:
This subclass is indented under subclass 542. Processes involving use of a mask composed of plural layers to retard the diffusion of an electrically active impurity.

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552 Having plural predetermined openings in master mask:
This subclass is indented under subclass 551. Processes wherein the multiple layered diffusion mask contains a multitude of desired openings.

(1) Note. The multiple openings need not all be open at any one given step (i.e., sequential diffusion steps may utilize various openings selected from among the predetermined openings).

553 Using metal mask:
This subclass is indented under subclass 542. Processes involving use of a mask made from metal to retard the diffusion of an electrically active impurity.

554 Outwardly:
This subclass is indented under subclass 542. Processes wherein the electrically active impurity moves from an internal location toward the major surface of the semiconductor substrate.

555 Laterally under mask opening:
This subclass is indented under subclass 542. Processes wherein the direction of diffusion for the electrically active impurity includes a component parallel to the major surface of the masking layer.

556 Edge diffusion by using edge portion of structure other than masking layer to mask:
This subclass is indented under subclass 542. Processes using an edge feature of the substrate other than a masking layer to retard the diffusion of the electrically active impurity.

557 From melt:
This subclass is indented under subclass 542. Processes wherein the source of the electrically active impurity is molten material.

558 From solid dopant source in contact with semiconductor region:
This subclass is indented under subclass 542. Processes wherein the electrically active impurity is produced by a solid substance which is in physical contact with the semiconductor region to be doped.

559 Using capping layer over dopant source to prevent out-diffusion of dopant:
This subclass is indented under subclass 558. Processes including use of an overlying layer of material to prevent the diffusion of the electrically active impurity in the dopant source from moving therethrough.

560 Plural diffusion stages:
This subclass is indented under subclass 558. Processes wherein the diffusion is carried out in multiple stages.

561 Dopant source within trench or groove:
This subclass is indented under subclass 558. Processes wherein the solid dopant source material resides within the confines of a recessed region in the semiconductor substrate.

562 Organic source:
This subclass is indented under subclass 558. Processes wherein the solid dopant source material is composed of other than inorganic matter.

563 Glassy source or doped oxide:
This subclass is indented under subclass 558. Processes wherein the solid dopant source material is composed of a glass-type material or an oxide which has been doped.

564 Polycrystalline semiconductor source:
This subclass is indented under subclass 558. Processes wherein the solid dopant source material is composed of a multicrystalline semiconductor (i.e., polysilicon).

565 From vapor phase:
This subclass is indented under subclass 542. Processes wherein an electrically active impurity is produced using a gaseous substance as the dopant source material.

566 Plural diffusion stages:
This subclass is indented under subclass 565. Processes wherein the diffusion is carried out in multiple stages.

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567 Solid source in operative relation with semiconductor region:
This subclass is indented under subclass 565. Processes wherein the dopant source material originates from a solid source in close proximity to the semiconductor region to be doped.

568 In capsule-type enclosure:
This subclass is indented under subclass 567. Processes carried out in a small containerlike apparatus.

569 Into compound semiconductor region:
This subclass is indented under subclass 565. Process wherein an electrically active dopant is diffused into a compound semiconductor.

570 FORMING SCHOTTKY JUNCTION (I.E., SEMICONDUCTOR-CONDUCTOR RECTIFYING JUNCTION CONTACT):
This subclass is indented under the class definition. Processes for making a metal-to-semiconductor interface that exhibits a nonlinear impedance.

SEE OR SEARCH THIS CLASS, SUBCLASS:
92 for a process of making a Schottky junction which is responsive to electromagnetic radiation.
167 for a process of making a field effect transistor device incorporating a Schottky gate electrode.
534 for a process of implanting a conductivity modifying dopant into semiconductive regions of the substrate combined with the formation of a Schottky electrode.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), appropriate subclasses, including subclasses 54, 73, 260, 280 through 284, 449 through 457, 471 through 486, and 928 for Schottky barrier devices.

571 Combined with formation of ohmic contact to semiconductor region:
This subclass is indented under subclass 570. Processes additionally having a method for the formation of an ohmic contact to a semiconductor region.

572 Compound semiconductor:
This subclass is indented under subclass 570. Processes wherein the rectifying contact is formed on a compound semiconductor.

573 Multilayer electrode:
This subclass is indented under subclass 572. Processes wherein the contact is composed of plural layers.

SEE OR SEARCH THIS CLASS, SUBCLASS:
605 for a process for making plural layer ohmic electrode to a III-V compound semiconductor.

574 T-shaped electrode:
This subclass is indented under subclass 573. Processes wherein the contact is configured so as to possess a central conductive portion with adjacent conductive portions laterally extending therefrom.

575 Using platinum group metal (i.e., platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof):
This subclass is indented under subclass 573. Processes for forming a contact using a platinum group metals (i.e., platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Rh), iridium (Ir), osmium (Os), or alloy thereof).

576 Into grooved or recessed semiconductor region:
This subclass is indented under subclass 572. Processes wherein the contact is formed in a recess in the semiconductor substrate.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 284 for a field effect device having a Schottky gate residing in a groove.

577 Utilizing lift-off:
This subclass is indented under subclass 576. Processes including a step of material removal via a lift-off technique.

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578 Forming electrode of specified shape (e.g., slanted, etc.):
This subclass is indented under subclass 576. Processes wherein the contact possesses a specified shape.

579 T-shaped electrode:
This subclass is indented under subclass 578. Processes wherein the contact is configured so as to possess a central conductive portion with adjacent conductive portions laterally extending therefrom.

580 Using platinum group metal (i.e., platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof):
This subclass is indented under subclass 570. Processes for forming a contact using a platinum group metals (i.e., platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof).

581 Silicide:
This subclass is indented under subclass 580. Processes for forming a contact using the chemical combination of silicon (Si) with one of the platinum group metals (i.e., platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof).

582 Using refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 570. Processes for forming the contact using a refractory metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

583 Silicide:
This subclass is indented under subclass 582. Processes for forming a contact using the chemical combination of silicon (Si) with one of the refractory group elements (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

584 COATING WITH ELECTRICALLY OR THERMALLY CONDUCTIVE MATERIAL:
This subclass is indented under the class definition. Processes having a step of depositing electrically or thermally conductive material upon a semiconductive substrate.

(1) Note. Deposition may occur on any portion of the semiconductor substrate, including nonsemiconductor regions associated therewith.

SEE OR SEARCH THIS CLASS, SUBCLASS:

98 for a process of making an electrical contact to a radiation responsive device.

381 for a process of making a passive device (e.g., resistor, capacitor, etc.).

453 for a process of forming an electrically isolated lateral isolation structure having combined therewith an electrical contact structure.

454 for a process of forming a field plate electrode structure utilized in electrically isolating laterally spaced semiconductor regions.

585 Insulated gate formation:
This subclass is indented under subclass 584. Processes for forming an electrode which is electrically insulated from the adjoining semiconductor regions and which upon application of a voltage thereto exerts a change in electrical behavior in the adjoining semiconductor region.

586 Combined with formation of ohmic contact to semiconductor region:
This subclass is indented under subclass 585. Processes having combined therewith the formation of an ohmic contact to a semiconductor region.

587 Forming array of gate electrodes:
This subclass is indented under subclass 585. Process involving the deposition of electrically conductive material resulting in the formation of a repeating geometrical arrangement (e.g., multiple, adjacent electrically conductive elements) of coplanar gate electrodes.

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(1) Note. The array of coplanar gate electrodes may be partially overlapping (i.e., for applicability in multiphase CCDs).

(2) Note. Included herein are processes directed to formation of an arrayed gate electrode structure for various field effect device applications ranging from "gate arrays" to charge transfer devices to other arrays of active solid-state devices possessing gate electrodes (e.g., programmable logic arrays (PLAs) configured for connection of the individual structural units into a specific circuit, etc.)

SEE OR SEARCH THIS CLASS, SUBCLASS:

75 for a process of making an image sensor-type charge transfer device having an array of gate electrodes.

128 for a process of forming an array of electrical devices and selectively interconnecting the devices to produce a desired electrical circuit.

144 for a process of making a charge transfer device by altering the electrical properties of semiconductive regions of the substrate.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), especially subclasses 202+ for a gate array structure and subclasses 245+ for a charge transfer device having a structure for applying an electric field into the device.

588 Plural gate levels:
This subclass is indented under subclass 587. Processes wherein the array of insulated gate electrodes reside on more than one level relative to the main surface of the semiconductor substrate.

SEE OR SEARCH CLASS:

257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclass 250 for a charge transfer device having plural gate levels.

589 Recessed into semiconductor substrate:
This subclass is indented under subclass 585. Processes wherein the insulated gate electrode is recessed below the main surface of the semiconductor substrate.

590 Compound semiconductor:
This subclass is indented under subclass 585. Processes wherein the insulated gate is formed on a compound which is a semiconductor.

591 Gate insulator structure constructed of plural layers or nonsilicon containing compound:
This subclass is indented under subclass 585. Processes wherein the gate insulator is a laminate of multiple dielectric layers or is a nonsilicon containing dielectric compound.

592 Possessing plural conductive layers (e.g., polycide):
This subclass is indented under subclass 585. Processes wherein the electrode is a laminate of multiple conductive layers.

593 Separated by insulator (i.e., floating gate):
This subclass is indented under subclass 592. Processes wherein an intervening dielectric layer separates the plural conductive layers.

594 Tunnelling dielectric layer:
This subclass is indented under subclass 593. Processes wherein the intervening dielectric allows for the migration of charge carriers therethrough.

595 Having sidewall structure:
This subclass is indented under subclass 585. Processes wherein the insulated gate electrode has material features formed along the electrode sidewall.

596 Portion of sidewall structure is conductive:
This subclass is indented under subclass 595. Processes wherein a least a portion of the material features formed along the electrode sidewalls is electrically conductive.

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597 To form ohmic contact to semiconductive material:
This subclass is indented under subclass 584. Processes for depositing electrically conductive material which forms an indirect or direct ohmic contact to a semiconductive region.

598 Selectively interconnecting (e.g., customization, wafer scale integration, etc.):
This subclass is indented under subclass 597. Processes wherein an array of devices is electrically interconnected into a designated circuit arrangement.

SEE OR SEARCH THIS CLASS, SUBCLASS:
128 for processes of making a device array combined with selectively interconnecting the devices in a particular circuit configuration.

599 With electrical circuit layout:
This subclass is indented under subclass 598. Processes including a step of designing the topological arrangement of electrical conductors between arrayed device components.

600 Using structure alterable to conductive state (i.e., antifuse):
This subclass is indented under subclass 598. Processes for making an electrical interconnect structure which is alterable to a conductive state.

601 Using structure alterable to nonconductive state (i.e., fuse):
This subclass is indented under subclass 598. Processes for making an electrical interconnect structure which is alterable to a nonconductive state.

602 To compound semiconductor:
This subclass is indented under subclass 597. Processes wherein an ohmic contact is formed to a compound which is a semiconductor.

603 II-VI compound semiconductor:
This subclass is indented under subclass 602. Processes wherein the compound semiconductor is composed of elements of Group II (i.e., zinc (Zn), cadmium (Cd), and mercury (Hg)) and Group VI (i.e., oxygen (O), sulfur (S), selenium (Se), and tellurium (Te)).

604 III-V compound semiconductor:
This subclass is indented under subclass 602. Processes wherein the compound semiconductor is composed of elements of Group III (i.e., boron (B), aluminum (Al), gallium (Ga), and indium (In)) and Group V (i.e., nitrogen (N), phosphorus (P), arsenic (As), antimony (Sb), and bismuth (Bi)).

605 Multilayer electrode:
This subclass is indented under subclass 604. Processes wherein the ohmic contact is composed of plural layers.

606 Ga and As containing semiconductor:
This subclass is indented under subclass 604. Processes wherein the III-V compound semiconductor contains gallium (Ga) and arsenic (As).

607 With epitaxial conductor formation:
This subclass is indented under subclass 597. Processes involving the formation of an epitaxial conductive layer in ohmic electrical contact to a semiconductor region.

SEE OR SEARCH CLASS:
117, Single-Crystal, Oriented Crystal, and Epitaxy Growth Processes: Non-Coating Apparatus Therefor, appropriate subclasses for a process of forming an epitaxial layer upon a substrate.

608 Oxidic conductor (e.g., indium tin oxide, etc.):
This subclass is indented under subclass 597. Processes wherein the ohmic contact is formed of an electrically conductive oxide.

609 Transparent conductor:
This subclass is indented under subclass 608. Processes wherein the oxidic conductor is transparent to electromagnetic radiation incident thereupon.

610 Conductive macromolecular conductor (including metal powder filled composition):
This subclass is indented under subclass 597. Processes wherein the ohmic contact is formed of an electrically conductive macromolecular composition.

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611 Beam lead formation:
This subclass is indented under subclass 597. Processes wherein the electrical contact leads extend beyond the edge of the semiconductor substrate.

SEE OR SEARCH THIS CLASS, SUBCLASS:
411 for processes of making an electrically isolated lateral semiconductor structure wherein spaced semiconductor bodies are held in place via beam leads.
461 for processes of dicing a semiconductor substrate which coincidently form beam lead conductors.

612 Forming solder contact or bonding pad:
This subclass is indented under subclass 597. Processes for making an ohmic electrical contact to a semiconductor region which contact also serves as a solder contact or bonding pad.

613 Bump electrode:
This subclass is indented under subclass 612. Processes wherein the electrical contact is in the shape of an abrupt protuberance elevated relative to the main surface of the substrate.

614 Plural conductive layers:
This subclass is indented under subclass 613. Processes wherein the bump electrode is composed of multiple conductive layers.

615 Including fusion of conductor:
This subclass is indented under subclass 613. Processes wherein at least a portion of the conductive material forming the bump electrode is molten during formation of the bump.

616 By transcription from auxiliary substrate:
This subclass is indented under subclass 615. Processes wherein the bump electrode is formed by transcription of conductive material from an auxiliary substrate to the semiconductor substrate.

617 By wire bonding:
This subclass is indented under subclass 615. Processes wherein the bump electrode is formed by a process which includes a step of utilizing a metallic wire to form the elevated structure.

(1) Note. If a significant portion of the bonding wire remains attached to the semiconductor substrate and is discernable in the final structure, then original classification is proper in that class providing for the welding of same to a substrate.

SEE OR SEARCH CLASS:
219, Electric Heating, appropriate subclasses for a process of joining a bonding wire to a substrate via the application of electric heat.
228, Metal Fusion Bonding, especially subclasses 180.1+ for simultaneous bonding of multiple joints and subclass 180.5 for wire bonding.

618 Contacting multiple semiconductive regions (i.e., interconnects):
This subclass is indented under subclass 597. Processes wherein the electrical contact is formed so as to make electrical contact to plural semiconductive regions

619 Air bridge structure:
This subclass is indented under subclass 618. Processes wherein a portion of the electrical contact is suspended over the semiconductor substrate.

620 Forming contacts of differing depths into semiconductor substrate:
This subclass is indented under subclass 618. Processes wherein at least one electrical contact is formed at a depth into the semiconductive substrate which differs from that of another electrical contact.

621 Contacting diversely doped semiconductive regions (e.g., p-type and n-type regions, etc.):
This subclass is indented under subclass 618. Processes wherein at least one electrical contact is formed to a semiconductive region which is diversely doped (more heavily doped, oppositely doped, etc.) with respect to the semiconductive region contacted by another electrical contact.

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622 Multiple metal levels, separated by insulating layer (i.e., multiple level metallization):
This subclass is indented under subclass 618. Processes wherein there are plural levels of metal forming electrical contact material, the levels being separated by intervening dielectric material except at designated openings therethrough.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, Solid-State Diodes), subclasses 758+ for a solid-state integrated circuit device structure having multiple level metallization.

623 Including organic insulating material between metal levels:
This subclass is indented under subclass 622. Processes wherein the intervening dielectric is at least partly composed of organic insulating material.

(1) Note. An organic compound is one which fulfills the requirements of the Class 260 definitions (i.e., has a molecule characterized by two carbon atoms bonded together, one atom of carbon being bonded to at least one atom of hydrogen of a halogen, or one atom of carbon bonded to at least one atom of nitrogen by a single or double bond, certain compounds such as HCN, CN-CN, HNCO, HNCS, cyanogen halides, cyanamide, fulminic acid and metal carbides, being exceptions to this rule).

624 Separating insulating layer is laminate or composite of plural insulating materials:
This subclass is indented under subclass 622. Processes wherein there is at least one separating insulator layer between different metal levels, which separating insulator layer is itself made up of plural sublayers or which separating layer is a composite such as a mixture of silicon oxide and silicon nitride.

625 At least one metallization level formed of diverse conductive layers:
This subclass is indented under subclass 622. Processes wherein at least one of the metallization levels is composed of plural conductive layers of differing composition or electrical characteristics.

626 Planarization:
This subclass is indented under subclass 625. Processes wherein at least one of the metallization levels or at least one separating insulating layer is leveled into a single plane at any stage in the process.

627 At least one layer forms a diffusion barrier:
This subclass is indented under subclass 625. Processes wherein at least one of the diverse conductive layers forms a barrier to the migration of a contact material into the semiconductor or into another contact layer.

628 Having adhesion promoting layer:
This subclass is indented under subclass 625. Processes wherein a material (e.g., layer, etc.) is utilized to promote adhesion of the electrical contact or lead to an adjacent surface.

629 Diverse conductive layers limited to viahole/plug:
This subclass is indented under subclass 625. Processes wherein the diverse conductive layers of a metallization level are limited in lateral extent to the viahole or plug extending through an insulating layer.

630 Silicide formation:
This subclass is indented under subclass 629. Processes wherein at least one of the diverse conductive layers is a compound of silicon and a metal.

631 Having planarization step:
This subclass is indented under subclass 622. Processes wherein at least one of the metallization levels or at least one separating insulating layer is leveled into a single plane at any stage in the process.

632 Utilizing reflow:
This subclass is indented under subclass 631. Processes wherein the planarization step is conducted by decreasing the viscosity of a layer and causing a leveling of the same by the viscous flow thereof.

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633 Simultaneously by chemical and mechanical means:
This subclass is indented under subclass 631. Processes wherein the planarization step is conducted by the simultaneous chemical and mechanical material removal.

SEE OR SEARCH THIS CLASS, SUBCLASS:
692 for a process of chemical-mechanical polishing of a semiconductor substrate.

634 Utilizing etch-stop layer:
This subclass is indented under subclass 631. Processes wherein the planarization step is conducted utilizing an etch stop layer to limit the extent of a material removal operation.

635 Insulator formed by reaction with conductor (e.g., oxidation, etc.):
This subclass is indented under subclass 622. Processes wherein an insulating layer is formed by the conversion of a conductive layer at least in part to an electrically insulative material.

636 Including use of antireflective layer:
This subclass is indented under subclass 622. Processes including the use of an antireflection layer.

637 With formation of opening (i.e., viahole) in insulative layer:
This subclass is indented under subclass 622. Processes including a step of forming an opening in the separating insulating layer.

638 Having viaholes of diverse width:
This subclass is indented under subclass 637. Processes wherein at least one viahole is formed which is wider than at least one other viahole.

639 Having viahole with sidewall component:
This subclass is indented under subclass 637. Processes wherein the viahole has an additional component formed along the sidewall thereof.

640 Having viahole of tapered shape:
This subclass is indented under subclass 637. Processes wherein the viahole is formed so as to possess nonparallel sidewalls.

641 Selective deposition:
This subclass is indented under subclass 622. Processes wherein a material is deposited selectively upon the semiconductor substrate.

642 Diverse conductors:
This subclass is indented under subclass 618. Processes wherein the electrically conductive pathway contacting multiple semiconductive regions is composed of plural conductive layers of differing composition or electrical characteristics.

643 At least one layer forms a diffusion barrier:
This subclass is indented under subclass 642. Processes wherein at least one of the diverse conductive layers forms a barrier to the diffusional migration of a contact material into the semiconductor or into another contact layer.

644 Having adhesion promoting layer:
This subclass is indented under subclass 642. Processes wherein a material (e.g., layer, etc.) is utilized to promote adhesion of the electrical conductor to an adjacent surface.

645 Having planarization step:
This subclass is indented under subclass 642. Processes wherein a material layer is leveled into a single plane at any stage in the process.

646 Utilizing reflow:
This subclass is indented under subclass 645. Processes wherein the planarization step is conducted by decreasing the viscosity of a layer and causing a leveling of the same by the viscous flow thereof.

647 Having electrically conductive polysilicon component:
This subclass is indented under subclass 642. Processes wherein one of the diverse conductive layers is polycrystalline silicon.

648 Having refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 642. Processes for forming at least one layer of the diverse conductive layers using a refractory metal (i.e., titanium (Ti), zirconium (Zr), haf-

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nium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

649 Silicide:
This subclass is indented under subclass 648. Processes for forming a conductive layer using the chemical combination of silicon (Si) with one of the refractory group elements (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

650 Having noble group metal (i.e., silver (Ag), gold (Au), platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof):
This subclass is indented under subclass 642. Processes for forming at least one of the conductive layers using one of the noble group elements (e.g., silver (Ag), gold (Au), platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof).

651 Silicide:
This subclass is indented under subclass 650. Processes for forming a contact using the chemical combination of silicon (Si) with one of the noble group elements (e.g., silver (Ag), gold (Au), platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof).

652 Plural layered electrode or conductor:
This subclass is indented under subclass 597. Processes for making an ohmic contact to a semiconductor region involving the formation of multiple conductive layers of differing composition or electrical characteristics.

653 At least one layer forms a diffusion barrier:
This subclass is indented under subclass 652. Processes wherein at least one of the diverse conductive layers forms a barrier to the diffusional migration of a contact material into the semiconductor or into another contact layer.

654 Having adhesion promoting layer:
This subclass is indented under subclass 652. Processes wherein a material (e.g., layer, etc.) is utilized to promote adhesion of the electrical contact or lead to an adjacent surface.

655 Silicide:
This subclass is indented under subclass 652. Processes wherein at least one of the diverse conductive layers is formed by the chemical combination of silicon (Si) with a metal atom.

656 Having refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 652. Processes wherein at least one of the diverse conductive layers is formed using a refractory metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), or tungsten (W), or alloy thereof).

657 Having electrically conductive polysilicon component:
This subclass is indented under subclass 652. Processes wherein one of the diverse conductive layers is polycrystalline silicon.

658 Altering composition of conductor:
This subclass is indented under subclass 597. Processes wherein the composition of the conductive material which forms an ohmic contact to an adjacent semiconductive region is altered (e.g., via implantation, diffusion, etc.)

(1) Note. The material serving to alter the composition of the conductive material must by supplied from other than a semiconductive region of the substrate. Formation of a silicide by reaction with a semiconductor substrate region is thus not sufficient for placement in this subclass.

659 Implantation of ion into conductor:
This subclass is indented under subclass 658. Processes wherein an ion is implanted into the electrical conductor (e.g., to alter the composition thereof, etc.).

660 Including heat treatment of conductive layer:
This subclass is indented under subclass 597. Processes wherein a thermal treatment is performed on the electrically conductive layer

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(e.g., for modifying the electrical properties thereof, etc.).

SEE OR SEARCH CLASS:
148, Metal Treatment, appropriate subclasses for processes of altering the physical or electrical characteristics of metallic material.

661 Subsequent fusing conductive layer:
This subclass is indented under subclass 660. Processes wherein the conductive layer is melted subsequent to the deposition thereof.

662 Utilizing laser:
This subclass is indented under subclass 661. Processes wherein the melting of the conductive layer is affected through the application of coherent radiant energy thereupon.

663 Rapid thermal anneal:
This subclass is indented under subclass 660. Processes wherein the heat treatment is of sufficiently short time span so as to limit the thermal affects primarily to the electrically conductive layer.

664 Forming silicide:
This subclass is indented under subclass 663. Processes wherein the rapid thermal anneal results in the formation of a single silicide layer by the reaction of a conductive layer and a silicon substrate region.

665 Utilizing textured surface:
This subclass is indented under subclass 597. Processes wherein a surface is roughened at some stage in the process.

666 Specified configuration of electrode or contact:
This subclass is indented under subclass 597. Processes wherein the ohmic electrode or contact has a specified shape or configuration.

SEE OR SEARCH CLASS:
257, Active Solid-State Devices (e.g., Transistors, solid-state Diodes), subclass 773 for an electrical contact or lead to an active solid-state device having a specified configuration.

667 Conductive feedthrough or through-hole in substrate:
This subclass is indented under subclass 666. Processes wherein the electrically conductive material is formed upon one surface of the semiconductor substrate and is able to make electrical contact with the opposing surface of the semiconductor substrate.

668 Specified aspect ratio of conductor or via-hole:
This subclass is indented under subclass 666. Processes wherein the width-to-depth ratio or width-to-height ratio of the electrical conductor or the viahole in which the same is to reside is given.

669 And patterning of conductive layer:
This subclass is indented under subclass 597. Processes including the selective removal of portions of the conductive layer formed upon the semiconductor substrate.

670 Utilizing lift-off:
This subclass is indented under subclass 669. Processes including a step of material removal via a lift-off technique.

671 Utilizing multilayered mask:
This subclass is indented under subclass 669. Processes involving the use of a mask composed of plural layers.

672 Plug formation (i.e., in viahole):
This subclass is indented under subclass 669. Processes wherein the patterning step results in the remaining conductive material being recessed below the top surface of the substrate.

673 Tapered etching:
This subclass is indented under subclass 669. Processes wherein the patterning step is accomplished through a tapering etching step.

674 Selective deposition of conductive layer:
This subclass is indented under subclass 597. Processes wherein the conductive material is deposited upon selected regions of the substrate.

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675 Plug formation (i.e., in viahole):
This subclass is indented under subclass 674. Processes wherein the selective deposition results in the deposited conductive material being recessed below the top surface of the substrate.

676 Utilizing electromagnetic or wave energy:
This subclass is indented under subclass 674. Processes wherein the selective deposition is accomplished through the irradiation of localized regions of the substrate with electromagnetic or wave energy.

677 Pretreatment of surface to enhance or retard deposition:
This subclass is indented under subclass 674. Processes including a step of treating the substrate surface preparatory to the selective deposition step to increase or decrease the deposition thereon.

678 Electroless deposition of conductive layer:
This subclass is indented under subclass 597. Processes wherein the formation of the conductive layer is accomplished by immersion of the semiconductor substrate in a metallic salt solution and deposition therefrom without the use of electricity.

679 Evaporative coating of conductive layer:
This subclass is indented under subclass 597. Processes wherein the formation of the conductive layer is accomplished through the evaporation of the conductive material from a source and the deposition of the same on the semiconductive substrate.

680 Utilizing chemical vapor deposition (i.e., CVD):
This subclass is indented under subclass 597. Processes wherein the conductive material is deposited utilizing a vapor phase precursor which decomposes or reacts either in the gaseous phase or on a substrate.

681 Of organo-metallic precursor (i.e., MOCVD):
This subclass is indented under subclass 680. Processes where the chemical vapor deposition process utilizes an organo-metallic compound.

682 Silicide:
This subclass is indented under subclass 597. Processes wherein the conductive material is formed by the chemical combination of Silicon (Si) with a metal atom.

683 Of refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 682. Processes for forming a contact using the chemical combination of silicon (Si) with one of the refractory group elements (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

684 Electrically conductive polysilicon:
This subclass is indented under subclass 597. Processes for forming a contact using electrically conductive polycrystalline silicon.

685 Refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 597. Processes for forming the contact using a refractory metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof).

686 Noble group metal (i.e., silver (Ag), gold (Au), platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof):
This subclass is indented under subclass 597. Processes for forming a contact using one of the noble group elements (e.g., silver (Ag), gold(Au), platinum (Pt), palladium (Pd), rhodium (Rh), ruthenium (Ru), iridium (Ir), osmium (Os), or alloy thereof).

687 Copper or copper alloy conductor:
This subclass is indented under subclass 597. Processes for forming a contact using copper (Cu) or an alloy thereof.

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688 Aluminum or aluminum alloy conductor:
This subclass is indented under subclass 597. Processes for forming a contact using aluminum (Al) or an alloy thereof.

689 CHEMICAL ETCHING:
This subclass is indented under the class definition. Processes having a step of removing material from a semiconductor substrate through the action of a chemical agent, wherein the intent is to use the electrical properties of the semiconductor for at least one of the purposes outlined in section I, C, of the class definition for this class (438).

SEE OR SEARCH CLASS:

204, Chemistry: Electrical and Wave Energy, subclasses 192.32+ for a process of sputter etching.

205, Electrolysis: Processes, Compositions Used Therein, and Methods of Preparing the Compositions, subclasses 640+ for methods of electrolytic erosion of a substrate, particularly subclass 656 for erosion of a substrate of nonuniform internal electrical characteristics.

216, Etching a Substrate: Processes, appropriate subclasses for a process of chemical etching a generic substrate.

690 Combined with the removal of material by nonchemical means (e.g., ablating, abrading, etc.):
This subclass is indented under subclass 689. Processes wherein the chemical removal is accompanied by the removal, either concurrently or consecutively, of material by nonchemical means.

691 Combined mechanical and chemical material removal:
This subclass is indented under subclass 690. Processes wherein the nonchemical material removal is a mechanical (e.g., abrading, cutting, etc.) removal method.

692 Simultaneous (e.g., chemical-mechanical polishing, etc.):
This subclass is indented under subclass 691. Processes wherein the chemical and mechanical material removal processes are concurrent.

693 Utilizing particulate abradant:
This subclass is indented under subclass 692. Processes wherein the mechanical material removal is affected through the use of a particulate abrasive material.

694 Combined with coating step:
This subclass is indented under subclass 689. Processes additionally having a step of depositing a material onto the semiconductive substrate.

695 Simultaneous etching and coating:
This subclass is indented under subclass 694. Processes wherein the chemical etching and material deposition occur concurrently.

696 Coating of sidewall:
This subclass is indented under subclass 694. Processes wherein the chemical etching and material deposition is affected so that only vertically disposed surfaces remain coated with the deposited material.

697 Planarization by etching and coating:
This subclass is indented under subclass 694. Processes wherein at least one surface of the semiconductor substrate is leveled through a combination of chemical etching and material deposition.

(1) Note. The material being planarized may or may not be that layer which was deposited.

698 Utilizing reflow:
This subclass is indented under subclass 697. Processes wherein the planarization method requires decreasing the viscosity of a layer residing on the substrate in order to fluidize the same.

699 Plural coating steps:
This subclass is indented under subclass 697. Processes having multiple material deposition steps are utilized in the planarization of the surface.

700 Formation of groove or trench:
This subclass is indented under subclass 694. Processes wherein at least one groove or trench is formed by a combination of chemical etching and material deposition.

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701 Tapered configuration:
This subclass is indented under subclass 700. Processes wherein the viahole or trench is formed so as to possess nonparallel sides.

702 Plural coating steps:
This subclass is indented under subclass 700. Processes wherein the viahole or trench is formed by a process having multiple material deposition steps.

703 Plural coating steps:
This subclass is indented under subclass 694. Processes having multiple material deposition steps.

704 Having liquid and vapor etching steps:
This subclass is indented under subclass 689. Processes having a liquid (i.e., wet) chemical etching step and a gaseous (i.e., dry) chemical etching step.

SEE OR SEARCH CLASS:
216, Etching a Substrate: Processes, subclass 57 for the combination of wet chemical etching with dry chemical etching upon a generic substrate.

705 Altering etchability of substrate region by compositional or crystalline modification:
This subclass is indented under subclass 689. Processes wherein the manner in which a semiconductor substrate is etched by a chemical etchant is altered by contacting the substrate prior to etching (a) with a material which alloys or diffuses into a substrate region or (b) by modifying the crystalline structure of a substrate region (e.g., amorphosizing, introducing dislocations, etc.).

706 Vapor phase etching (i.e., dry etching):
This subclass is indented under subclass 689. Processes wherein the chemical etchant is in a gaseous state when brought into contact with the semiconductive substrate.

(1) Note. A colloidal dispersion having fine droplets of an etchant is not considered to be vapor phase for the purposes of this and its indented subclass.

SEE OR SEARCH THIS CLASS, SUBCLASS:
477 for a gettering process in which the semiconductor substrate is treated with a reactive gas mixture which preferentially forms volatile compounds with certain undesired impurities.

707 Utilizing electromagnetic or wave energy:
This subclass is indented under subclass 706. Processes wherein the vapor phase etching is conducted using irradiation of electromagnetic or wave energy.

708 Photo-induced etching:
This subclass is indented under subclass 707. Processes involving the simultaneous irradiation of the substrate or adjoining space with infrared, visible, or ultraviolet radiation to induce the vapor phase etching of regions thereof.

709 Photo-induced plasma etching:
This subclass is indented under subclass 708. Processes wherein the photo-induced vapor phase etching is accompanied with the excitation of the etchant into a plasma.

(1) Note. A plasma is a gas that is sufficiently ionized for its properties to depend on the ionization. It contains approximately equal numbers of positive ions and electrons, so the mixture is electrically neutral, highly conductive, and affected by magnetic fields. A thermal plasma is produced by temperatures above 20,000 degrees centigrade.

710 By creating electric field (e.g., plasma, glow discharge, etc.):
This subclass is indented under subclass 707. Processes involving the application of an electric field to generate, modify, or control the vaporous reactant(s) used in the chemical etching process.

(1) Note. Chemical etching processes utilizing corona, glow discharge, and plasma are found here, when utilized to cause dissociation of the etching gas precedent to the chemical etching of the semiconductor substrate therewith.

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(2) Note. A plasma is a gas that is sufficiently ionized for its properties to depend on the ionization. It contains approximately equal numbers of positive ions and electrons, so the mixture is electrically neutral, highly conductive, and affected by magnetic fields. A thermal plasma is produced by temperatures above 20,000 degrees centigrade. In a cold plasma, the temperature of the electrons is high whereas the temperature of the ions is relatively low.

SEE OR SEARCH CLASS:

216, Etching a Substrate: Processes, particularly subclasses 67+ for generic plasma etching methods. However, the use of a high temperature thermal plasma which removes of alters material solely by thermal means is proper for Class 219, Electric Heating.

711 Utilizing multiple gas energizing means:
This subclass is indented under subclass 710. Processes wherein plural gas energizing means are utilized either simultaneously or consecutively to ionize the etching gas (e.g., RF discharge and a DC electron source, etc.)

712 Reactive ion beam etching (i.e., RIBE):
This subclass is indented under subclass 710. Processes wherein the semiconductor substrate is mounted on the RF-powered electrode of the etching apparatus.

713 Forming tapered profile (e.g., tapered etching, etc.):
This subclass is indented under subclass 710. Processes wherein the etchant removes material from the substrate resulting in a mesa or trench profile possessing nonparallel sides.

714 Including change in etch influencing parameter (e.g., energizing power, etchant composition, temperature, etc.):
This subclass is indented under subclass 710. Processes wherein a parameter influencing material removal, such as energizing power, gas etchant composition, temperature, etc., is varied during the etching process.

715 With substrate heating or cooling:
This subclass is indented under subclass 710. Processes including the temperature maintenance or modification of the semiconductor substrate during the etching thereof with the energized gas.

716 With substrate handling (e.g., conveying, etc.):
This subclass is indented under subclass 710. Processes including the physical handling or manipulation of the semiconductor substrate in conjunction with the etching thereof.

717 Utilizing multilayered mask:
This subclass is indented under subclass 710. Processes wherein selected regions of the semiconductor substrate are protected from the effects of the energized gas through use of a mask composed of plural layers.

718 Compound semiconductor:
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is a compound semiconductor.

719 Silicon:
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is silicon.

720 Electrically conductive material (e.g., metal, conductive oxide, etc.):
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is an electrically conductive material.

721 Silicide:
This subclass is indented under subclass 720. Processes wherein the material undergoing etching with the energized gas is an electrically conductive compound of silicon and a metal atom.

722 Metal oxide:
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is a compound of a metal and oxygen.

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723 Silicon oxide or glass:
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is a compound of silicon and oxygen or glass.

724 Silicon nitride:
This subclass is indented under subclass 710. Process wherein the material undergoing etching with the energized gas is a compound of silicon and nitrogen.

725 Organic material (e.g., resist, etc.):
This subclass is indented under subclass 710. Processes wherein the material undergoing etching with the energized gas is an organic material.

726 Having microwave gas energizing:
This subclass is indented under subclass 710. Processes wherein the ionized etching gas is produced using a microwave source.

727 Producing energized gas remotely located from substrate:
This subclass is indented under subclass 726. Processes wherein the etching gas is energized in a region spaced apart from the region in which the semiconductor substrate is located.

728 Using magnet (e.g., electron cyclotron resonance, etc.):
This subclass is indented under subclass 727. Processes wherein the a magnet is utilized in producing or confining the energized gas.

729 Using specified electrode/susceptor configuration (e.g., of multiple substrates using barrel-type susceptor, planar reactor configuration, etc.) to generate plasma:
This subclass is indented under subclass 710. Processes having a specified physical arrangement of electrode(s) and/or susceptor.

730 Producing energized gas remotely located from substrate:
This subclass is indented under subclass 729. Processes wherein the etching gas is energized in a region spaced apart from the region in which the semiconductor substrate is located.

731 Using intervening shield structure:
This subclass is indented under subclass 730. Processes wherein a blocking means is interposed between the region generating the energized gas and the region in which the semiconductor substrate resides.

732 Using magnet (e.g., electron cyclotron resonance, etc.):
This subclass is indented under subclass 710. Processes wherein the a magnet is utilized in producing or confining the energized gas.

733 Using orientation dependant etchant (i.e., anisotropic etchant):
This subclass is indented under subclass 706. Processes wherein the vapor phase etching of the semiconductor substrate is produced through the use of an etchant possessing varying etching rates upon varying crystallographic orientations.

734 Sequential etching steps on a single layer:
This subclass is indented under subclass 706. Processes wherein plural etching steps are carried out on a single layer at different times.

(1) Note. Removal of a resist layer which has the sole function of protecting an underlying area from etchant is not considered to be an etching step for this and the indented subclasses.

735 Differential etching of semiconductor substrate:
This subclass is indented under subclass 706. Processes directed to (a) contact only selected surface areas of the substrate with the etchant to remove a constituent part of the substrate at the selected surface areas only or (b) cause the substrate to be treated at different rates in different areas to produce a nonuniform surface.

736 Utilizing multilayered mask:
This subclass is indented under subclass 735. Processes wherein selected regions of the semiconductor substrate are protected from the effects of the etching gas through use of a mask composed of plural layers.

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737 Substrate possessing multiple layers:
This subclass is indented under subclass 735. Processes wherein the semiconductor substrate undergoing etching possesses plural layers.

738 Selectively etching substrate possessing multiple layers of differing etch characteristics:
This subclass is indented under subclass 737. Process involving the etching of a multilayered substrate, using a single etching step, where the process parameters used causes a difference of the etching rate or characteristic in at least two different layers of the substrate.

739 Lateral etching of intermediate layer (i.e., undercutting):
This subclass is indented under subclass 738. Processes wherein an intermediate layer on the substrate is etched laterally to the major surface thereof.

740 Utilizing etch stop layer:
This subclass is indented under subclass 738. Processes wherein the selective etching is effected through the use of a material resistant to the etchant.

741 PN junction functions as etch stop:
This subclass is indented under subclass 740. Processes wherein the etch stop layer is a component of a PN junction.

742 Electrically conductive material (e.g., metal, conductive oxide, etc.):
This subclass is indented under subclass 737. Processes wherein the material undergoing etching with the energized gas is an electrically conductive material.

743 Silicon oxide or glass:
This subclass is indented under subclass 737. Processes wherein the material undergoing etching with the energized gas is a compound of silicon and oxygen or glass.

744 Silicon nitride:
This subclass is indented under subclass 737. Process wherein the material undergoing etching with the energized gas is a compound of silicon and nitrogen.

745 Liquid phase etching:
This subclass is indented under subclass 689. Processes wherein the chemical etchant is in a liquid state when brought into contact with the semiconductive substrate.

746 Utilizing electromagnetic or wave energy:
This subclass is indented under subclass 745. Processes wherein the liquid phase etching is conducted using irradiation of electromagnetic or wave energy.

747 With relative movement between substrate and confined pool of etchant:
This subclass is indented under subclass 745. Processes including the step of causing a relative motion between the semiconductor substrate being etched and the liquid phase etchant which is confined by a container.

748 Projection of etchant against a moving substrate or controlling the angle or pattern of projected etchant:
This subclass is indented under subclass 745. Processes wherein the chemical etchant is sprayed upon the moving semiconductor substrate or sprayed upon the semiconductor substrate in a specific angle or pattern.

749 Sequential application of etchant:
This subclass is indented under subclass 745. Processes wherein plural liquid phase etching steps are carried out on the semiconductor substrate in succession to one another.

750 To same side of substrate:
This subclass is indented under subclass 749. Processes wherein the sequential liquid phase etching steps are carried out on the same major surface of the semiconductor substrate.

751 Each etch step exposes surface of an adjacent layer:
This subclass is indented under subclass 750. Processes wherein a layer on the semiconductor substrate previously covered by a different layer is exposed by each liquid phase etching step.

752 Germanium:
This subclass is indented under subclass 745. Processes wherein the material undergoing wet chemical etching is germanium (Ge).

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753 Silicon:
This subclass is indented under subclass 745. Processes wherein the material undergoing wet chemical etching is silicon (Si).

754 Electrically conductive material (e.g., metal, conductive oxide, etc.):
This subclass is indented under subclass 745. Processes wherein the material undergoing wet chemical etching is an electrically conductive material.

755 Silicide:
This subclass is indented under subclass 754. Processes wherein the material undergoing wet chemical etching is an electrically conductive compound of silicon and a metal atom.

756 Silicon oxide:
This subclass is indented under subclass 745. Processes wherein the material undergoing wet chemical etching is a compound of silicon and oxygen.

757 Silicon nitride:
This subclass is indented under subclass 745. Processes wherein the material undergoing wet chemical etching is a compound of silicon and nitrogen.

758 COATING OF SUBSTRATE CONTAINING SEMICONDUCTOR REGION OR OF SEMICONDUCTOR SUBSTRATE:
This subclass is indented under the class definition. Processes for forming or applying a coating on a semiconductor substrate, and wherein the intent is to use the electrical properties of the semiconductor for at least one of the purposes outlined in section I, B, of the Class 438 definition above.

(1) Note. Coating limited to nonsemiconductive areas of the substrate is acceptable in this and undented subclasses if the substrate also contains, integral therewith, a semiconductive region functioning as per the Class Definition B, above.

(2) Note. The passivation of dangling bonds on the semiconductor substrate surface (such as by covalently bonding hydrogen to the surface) is considered to be proper under gettering above.

SEE OR SEARCH THIS CLASS, SUBCLASS:
33 or 465, for formation of a coating combined with substrate dicing.
476 for coating combined with gettering.
478+, for formation of a semiconductive coating.
493 for formation of a nonconductive coating combined with formation of a semiconductive coating.
689 for coating of metal, metallization, or formation of a heat sink.

SEE OR SEARCH CLASS:
204, Chemistry: Electrical and Wave Energy, subclasses 192.12+ for glow discharge sputter deposition processes.
205, Electrolysis: Processes, Compositions Used Therein, and Methods of Preparing the Compositions, especially subclasses 123+ for forming an electrolytic coating on a selected area of a semiconductor substrate and subclass 157 for electrolytic coating a semiconductor substrate.
427, Coating Processes, for processes of coating where the product of the process is generically disclosed for both semiconductive electrical purpose and nonsemiconductive electrical purpose.

759 Combined with the removal of material by nonchemical means:
This subclass is indented under subclass 758. Processes having an additional step of removing material from the semiconductor substrate by nonchemical means (e.g., ablating, abrading, grinding, etc.)

760 Utilizing reflow (e.g., planarization, etc.):
This subclass is indented under subclass 758. Processes wherein the coating step is combined with a step of decreasing the viscosity of the layer and causing a redistribution of the same by the viscous flow thereof.

761 Multiple layers:
This subclass is indented under subclass 758. Processes wherein plural layers are formed upon the semiconductor substrate.

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762 At least one layer formed by reaction with substrate:
This subclass is indented under subclass 761. Processes wherein at least one of the layers is formed by reacting an external agent with a constituent of the substrate to form a compound thereof.

763 Layers formed of diverse composition or by diverse coating processes:
This subclass is indented under subclass 761. Processes wherein the plural layers are formed utilizing different processes (e.g., thermal insulator with deposited insulator, etc.) or are of differing composition or physical characteristics (e.g., crystallinity, orientation, etc.).

764 Formation of semi-insulative polycrystalline silicon:
This subclass is indented under subclass 758. Processes involving the deposition of polycrystalline silicon which possesses an electrical conductivity less than that typically utilized for the formation of electrical devices.

SEE OR SEARCH THIS CLASS, SUBCLASS:
488 for processes of depositing polycrystalline silicon of semiconductive electrical characteristics.
564 for processes of depositing polycrystalline silicon combined with the subsequent diffusion of conductivity modifying dopants therefrom into adjacent semiconductive regions.

765 By reaction with substrate:
This subclass is indented under subclass 758. Processes wherein a coating layer is formed by reacting an external agent with a constituent of the substrate to form the coating thereupon.

766 Implantation of ion (e.g., to form ion amorphousized region prior to selective oxidation, reacting with substrate to form insulative region, etc.):
This subclass is indented under subclass 765. Processes having a step of implanting an ionized species into a substrate region to form or facilitate formation of a reactive coating layer.

SEE OR SEARCH THIS CLASS, SUBCLASS:
423 for a process of forming an electrically isolated lateral semiconductor structure having a step of implanting to form an electrically insulative region.
798 for a process of exposing a semiconductor substrate to ionized radiation for modification of some property of the same.

767 Compound semiconductor substrate:
This subclass is indented under subclass 765. Processes wherein the substrate region reacting with the external agent is a compound semiconductor.

768 Reaction with conductive region:
This subclass is indented under subclass 765. Processes wherein the substrate region reacting with an external agent is a conductive region or layer residing upon the semiconductor substrate.

SEE OR SEARCH CLASS:
148, Metal Treatment, appropriate subclasses for methods of reactively coating (e.g., carburizing, nitriding, oxidizing, etc.) a metallic substrate.

769 Reaction with silicon semiconductive region (e.g., oxynitride formation, etc.):
This subclass is indented under subclass 765. Processes wherein the substrate region reacting with an external agent is a silicon semiconductor region.

770 Oxidation:
This subclass is indented under subclass 769. Processes wherein the external agent supplies oxygen which reacts with the silicon substrate region to form a compound therewith.

771 Using electromagnetic or wave energy:
This subclass is indented under subclass 770. Processes wherein the oxidation is conducted using irradiation of electromagnetic or wave energy.

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772 Microwave gas energizing:
This subclass is indented under subclass 771. Processes wherein the irradiation is of microwave frequency.

(1) Note. The FCC allowed frequency for microwave energy is 2.45 GHz, with a corresponding wavelength of from 1mm to 1m.

(2) Note. Microwave is a term applied to electromagnetic waves which occupy a region in the electromagnetic spectrum which is bounded by radio waves on the side of longer wavelengths and by infrared waves on the side of shorter wavelengths.

773 In atmosphere containing water vapor (i.e., wet oxidation):
This subclass is indented under subclass 770. Processes wherein the oxidation is carried out in an atmosphere containing water in vaporous form.

774 In atmosphere containing halogen:
This subclass is indented under subclass 770. Processes wherein the oxidation is carried out in an atmosphere containing a halogen.

775 Nitridation:
This subclass is indented under subclass 769. Processes wherein the external agent supplies nitrogen which reacts with the silicon substrate region to form a compound therewith.

776 Using electromagnetic or wave energy:
This subclass is indented under subclass 775. Processes wherein the nitridation is conducted using irradiation of electromagnetic or wave energy.

777 Microwave gas energizing:
This subclass is indented under subclass 776. Processes wherein the irradiation is of microwave frequency.

(1) Note. The FCC allowed frequency for microwave energy is 2.45 GHz, with a corresponding wavelength of from 1mm to 1m.

(2) Note. Microwave is a term applied to electromagnetic waves which occupy a region in the electromagnetic spectrum which is bounded by radio waves on the side of longer wavelengths and by infrared waves on the side of shorter wavelengths.

778 Insulative material deposited upon semiconductive substrate:
This subclass is indented under subclass 758. Processes wherein an insulative coating is formed upon the semiconductor substrate solely by the deposition of externally supplied material.

779 Compound semiconductor substrate:
This subclass is indented under subclass 778. Processes wherein the substrate upon which is deposited the coating is a compound semiconductor.

780 Depositing organic material (e.g., polymer, etc.):
This subclass is indented under subclass 778. Processes wherein the deposited material is at least partly composed of organic material. An organic compound is one which fulfills the requirements of the Class 260 definitions (i.e., has a molecule characterized by two carbon atoms bonded together, one atom of carbon being bonded to at least one atom of hydrogen or a halogen, or one atom of carbon bonded to at least one atom of nitrogen by a single or double bond, certain compounds such as HCN, CN-CN, HNCO, HNCS, cyanogen halides, cyanamide, fulminic acid and metal carbides, being exceptions to this rule).

SEE OR SEARCH THIS CLASS, SUBCLASS:
623 for processes of constructing a multilayer interconnect using an organic insulating material between metal levels.

781 Subsequent heating step modifying organic coating composition:
This subclass is indented under subclass 780. Processes including a subsequent thermal treatment step altering the chemical composition of the organic coating composition.

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782 With substrate handling during coating (e.g., immersion, spinning, etc.):
This subclass is indented under subclass 778. Processes wherein the semiconductor substrate is handled or manipulated in conjunction with the coating operation.

783 Insulative material having impurity (e.g., for altering physical characteristics, etc.):
This subclass is indented under subclass 778. Processes wherein the deposited insulative material contains one or more impurities (e.g., for altering a physical characteristic such as etchability, for serving as a diffusion source for adjacent semiconductive regions of the substrate, etc.).

784 Introduction simultaneous with deposition:
This subclass is indented under subclass 783. Processes wherein the impurity is introduced into the insulative material concurrently with the deposition step.

785 Insulative material is compound of refractory group metal (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), tungsten (W), or alloy thereof):
This subclass is indented under subclass 778. Processes for forming an insulative compound using one of the refractory group elements (i.e., titanium (Ti), zirconium (Zr), hafnium (Hf), vanadium (V), niobium (Nb), tantalum (Ta), chromium (Cr), molybdenum (Mo), or tungsten (W)).

786 Tertiary silicon containing compound formation (e.g., oxynitride formation, etc.):
This subclass is indented under subclass 778. Processes for forming an insulative compound of silicon and two other elements is deposited upon the semiconductor substrate.

787 Silicon oxide formation:
This subclass is indented under subclass 778. Processes wherein the deposited insulative material is a compound of silicon and oxygen.

788 Using electromagnetic or wave energy (e.g., photo-induced deposition, plasma, etc.):
This subclass is indented under subclass 787. Processes wherein the silicon oxide is deposited using irradiation of electromagnetic or wave energy.

789 Organic reactant:
This subclass is indented under subclass 788. Processes wherein a reactant compound utilized during the deposition of silicon oxide is an organic material (e.g., organo-siloxane, etc.).

790 Organic reactant:
This subclass is indented under subclass 787. Processes wherein a reactant compound utilized during the deposition of silicon oxide is an organic material (e.g., organo-siloxane, etc.).

791 Silicon nitride formation:
This subclass is indented under subclass 778. Processes wherein the deposited material is a compound of silicon and nitrogen.

792 Using electromagnetic or wave energy (e.g., photo-induced deposition, plasma, etc.):
This subclass is indented under subclass 791. Processes wherein the silicon nitride is deposited using irradiation of electromagnetic or wave energy.

793 Organic reactant:
This subclass is indented under subclass 792. Processes wherein a reactant compound utilized during the deposition of silicon nitride is an organic material (e.g., organo-siloxane, etc.).

794 Organic reactant:
This subclass is indented under subclass 791. Processes wherein a reactant compound utilized during the deposition of silicon nitride is an organic material (e.g., organo-siloxane, etc.).

795 RADIATION OR ENERGY TREATMENT MODIFYING PROPERTIES OF SEMICONDUCTOR REGION OF SUBSTRATE

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(E.G., THERMAL, CORPUSCULAR, ELECTROMAGNETIC, ETC.):
This subclass is indented under the class definition. Process of radiating a semiconductor substrate with a form of energy to change some characteristic thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
308 for a process of making an insulated gate field effect transistor having a step of modifying semiconductor regions of the substrate via a radiation or energy treatment.
378 for a process of making a bipolar transistor having a step of modifying semiconductor regions of the substrate via a radiation or energy treatment.
471 for a process of gettering a semiconductive substrate (including layers thereon) by a thermal treatment.
466 for a process of directly applying electrical current to a semiconductor substrate.

SEE OR SEARCH CLASS:
117, Single-Crystal, Oriented-Crystal, and Epitaxy Growth Processes; Non-Coating Apparatus Therefor, for processes of heat treating polycrystalline or amorphous semiconductor material to thereby cause single crystal growth.
219, Electric Heating, particularly subclass 638 for inductive heating of a semiconductive rod.
250, Radiant Energy, particularly subclasses 492.2+ for methods of using, generating, or controlling ion bombardment of semiconductive substrates when there is no indication of what occurs to the substrate.

796 Compound semiconductor:
This subclass is indented under subclass 795. Process wherein the substrate being modified is a compound semiconductor.

797 Ordering or disordering:
This subclass is indented under subclass 796. Process wherein a compound semiconductive region is transformed from an ordered state to a disordered state or vice versa.

SEE OR SEARCH THIS CLASS, SUBCLASS:
36 for a process of making a device emissive of nonelectrical signal having a step wherein a compound semiconductor is transformed from an ordered state to a disordered state or vice versa.
511 for a process of introducing an electrically active dopant species into a semiconductor wherein the semiconductor is transformed from an ordered state to a disordered state or vice versa.

798 Ionized irradiation (e.g., corpuscular or plasma treatment, etc.):
This subclass is indented under subclass 795. Process wherein ionized radiation is applied to the semiconductor to modify the properties thereof.

SEE OR SEARCH THIS CLASS, SUBCLASS:
474 for a process of gettering a semiconductor substrate by the application of ionized irradiation thereto.
514 for a process for implanting an electrically active dopant into a semiconductive region of the substrate.

799 By differential heating:
This subclass is indented under subclass 795. Process involving the nonuniform heating of a semiconductive substrate to modify the properties of semiconductor regions thereof.

SEE OR SEARCH CLASS:
250, Radiant Energy, subclass 492.22 for a method of controlling the pattern of irradiation incident upon a semiconductor substrate and subclass 492.23 for method of variably impinging radiation upon a semiconductor substrate.

800 MISCELLANEOUS:
This subclass is indented under the class definition. Process not provided for above.

CROSS-REFERENCE ART COLLECTIONS

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900 BULK EFFECT DEVICE MAKING:
Art collection involving the construction of a semiconductor device whose electrical characteristics and electronic properties are exhibited throughout the entire body of the material, rather than in just a localized region thereof (e.g., the surface).

901 CAPACITIVE JUNCTION:
Art collection involving the construction of a barrier layer junction possessing capacitive properties.

902 CAPPING LAYER:
Art collection involving the use of an overlayer serving to separate and protect an underlying region or layer from the environment.

903 CATALYST AIDED DEPOSITION:
Art collection involving the use of a catalyst to facilitate material deposition.

904 CHARGE CARRIER LIFETIME CONTROL:
Art collection involving the control of the lifetime of charge carriers (i.e., electrons or holes) in the semiconductor.

905 CLEANING OF REACTION CHAMBER:
Art collection involving cleaning an etch chamber.

906 CLEANING OF WAFER AS INTERIM STEP:
Art collection involving cleaning a semiconductive wafer as a step between other processing steps.

907 CONTINUOUS PROCESSING:
Art collection involving carrying out process steps in semiconductor manufacture in a continual manner.

908 Utilizing cluster apparatus:
This subclass is indented under subclass 907. Art collection wherein the continuous processing is conducted in an apparatus having a plurality of processing chambers having associated handling means to move the semiconductor substrate therebetween.

909 CONTROLLED ATMOSPHERE:
Art collection involving use of a regulated gaseous environment (e.g., inert gases, specifically proportioned mixtures, etc.).

910 CONTROLLING CHARGING STATE AT SEMICONDUCTOR-INSULATOR INTERFACE:
Art collection involving adjusting the charge state where the semiconductor and insulator surfaces meet.

911 DIFFERENTIAL OXIDATION AND ETCHING:
Art collection involving differential oxidation combined with an etching process.

912 DISPLACING PN JUNCTION:
Art collection involving physical relocation of the P-N junction from its originally formed position.

913 DIVERSE TREATMENTS PERFORMED IN UNITARY CHAMBER:
Art collection involving diverse treatments performed upon a semiconductor substrate which are affected in a single processing chamber.

914 DOPING:
Art collection involving the doping of a semiconductor substrate with conductivity modifying impurities.

915 Amphoteric doping:
Art collection under 914 involving use of a dopant capable of functioning as a P- or N-type conductivity modifier depending on process conditions.

916 Autodoping control or utilization:
Art collection under 914 involving the regulation of self-induced impurity production in a semiconductor substrate.

917 Deep level dopants (e.g., gold (Au), chromium (Cr), iron (Fe), nickel (Ni), etc.):
Art collection under 914 involving the utilization of dopants serving to reduce minority carrier lifetime through the formation of energy levels located in the forbidden band of a semiconductor material that are not near the conduction or valence band edges.

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918 Special or nonstandard dopant:
Art collection under 914 involving use of a special or nonstandard dopant.

919 Compensation doping:
Art collection under 914 involving doping of over-lapping regions to convert first to one conductivity type and then to the other conductivity type.

920 Controlling diffusion profile by oxidation:
Art collection under 914 involving the regulation of a diffusion contour by an oxidation step.

921 Nonselective diffusion:
Art collection under 914 involving a random diffusion process (i.e., diffusion without a mask).

922 Diffusion along grain boundaries:
Art collection under 914 involving diffusion between the grains of nonsingle crystalline material along the physical interface of two layers.

923 Diffusion through a layer:
Art collection under 914 involving diffusing a dopant in a perpendicular manner through a layer of material.

924 To facilitate selective etching:
Art collection under 914 involving doping selected regions of the semiconductor substrate to alter the etchibility of the doped regions.

925 Fluid growth doping control (e.g., delta doping, etc.):
Art collection under 914 involving regulating the dopant concentration during the fluid growth of material upon the substrate.

926 DUMMY METALLIZATION:
Art collection involving the use of an electrically conductive layer during semiconductor manufacture which is not utilized for the carrying of electrical current.

927 ELECTROMIGRATION RESISTANT METALLIZATION:
Art collection directed to metallization constructed so as to prevent the mass transport of metal by momentum exchange between thermally activated metal ions and conduction charge carriers.

928 FRONT AND REAR SURFACE PROCESSING:
Art collection directed to processing both opposed major surfaces of a semiconductor substrate.

929 EUTECTIC SEMICONDUCTOR:
Art collection directed to semiconductor manufacture involving the use of a dual phase, cooperatively formed semiconductor.

930 TERNARY OR QUATERNARY SEMICONDUCTOR COMPRISED OF ELEMENTS FROM THREE DIFFERENT GROUPS (E.G., I-III-V, ETC.):
Art collection involving the use of a compound semiconductor composed of elements form three different groups of the Periodic Table.

931 SILICON CARBIDE SEMICONDUCTOR:
Art collection involving the use of semiconducting silicon carbide in semiconductor manufacture.

932 BORON NITRIDE SEMICONDUCTOR:
Art collection involving the use of semiconducting boron nitride in semiconductor manufacture.

933 GERMANIUM OR SILICON OR GE-SI ON III-V:
Art collection involving the formation of a hetero-interface between germanium or silicon or an alloy thereof with a III-V compound semiconductor.

934 SHEET RESISTANCE (I.E., DOPANT PARAMETERS):
Art collection directed to the electrical resistivity of a thin film of semiconductor material.

935 GAS FLOW CONTROL:
Art collection involving gas flow manipulation in conjunction with semiconductor manufacture.

936 GRADED ENERGY GAP:
Art collection involving sequential formation of layers of composition or dopant concentration which vary with position in the layer.

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937 HILLOCK PREVENTION:
Art collection involving the prevention of spikelike projections which protrude from a layer surface.

938 LATTICE STRAIN CONTROL OR UTILIZATION:
Art collection involving the regulation or utilization of lattice strain.

939 LANGMUIR-BLODGETT FILM UTILIZATION:
Art collection involving the use of an organic coating having both hydrophilic and hydrophobic ends in semiconductor manufacture.

940 LASER ABLATIVE MATERIAL REMOVAL:
Art collection involving the removal of material from a semiconductor substrate by laser ablation.

941 LOADING EFFECT MITIGATION:
Art collection involving the minimalization of localized variations in the processing behavior of the substrate due to variations in the density of features formed thereupon.

942 MASKING:
Art collection involving the use of a structure having openings therein to affect selective processing of underlying regions laid bare by said openings.

943 Movable:
Art collection under 942 involving the use of a mask movable with respect to the semiconductor substrate.

944 Shadow:
Art collection under 942 involving the use of a mask not in contact with the semiconductor substrate so as to cast a shadow thereupon.

945 Special (e.g., metal, etc.):
Art collection under 942 involving the use of a nonconventional mask.

946 Step and repeat:
Art collection under 942 wherein the processing of the semiconductor substrate is affected by the sequential treatment of laterally arranged regions.

947 Subphotolithos:graphic processing:
Art collection under 942 wherein the photolithos:graphic features formed on the substrate are of a dimension below the resolution limit of the photolithos:graphic process.

948 Radiation resist:
Art collection under 942 involving the use of a radiation resist in a masking operation.

949 Energy beam treating radiation resist on semiconductor:
Art collection under 948 involving the use of an energy beam to irradiate a radiation sensitive layer upon a semiconductor substrate.

950 Multilayer mask including nonradiation sensitive layer:
Art collection under 948 involving the use of a multilayer mask having both radiation sensitive and nonradiation sensitive components.

951 Lift-off
Art collection under 948 involving the selective removal of a deposited layer by striping off the radiation resist and portions of the deposited layer residing thereupon.

952 Utilizing antireflective layer
Art collection under 948 involving the use of an antireflective layer on the semiconductor substrate.

953 MAKING RADIATION RESISTANT DEVICE
Art collection involving the construction of a device resistant to radiant energy.

954 MAKING OXIDE-NITRIDE-OXIDE DEVICE
Art collection involving construction of a device having a layered dielectric structure composed of a nitride layer interposed between outer oxide layers.

955 MELT-BACK
Art collection directed to the utilization of molten material to dissolve semiconductor regions of the substrate, often preparatory to liquid phase epitaxy.

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956 MAKING MULTIPLE WAVELENGTH EMISSIVE DEVICE
Art collection involving the construction of a device emissive of radiation of plural wavelengths.

957 MAKING METAL-INSULATOR-METAL DEVICE
Art collection involving the construction of a metal-insulator-metal device (e.g., MOMOM, etc.).

958 PASSIVATION LAYER
Art collection involving protecting the semiconductor substrate surface with a passivating coating.

959 MECHANICAL POLISHING OF WAFER
Art collection involving mechanically abrading a semiconductor substrate.

960 POROUS SEMICONDUCTOR
Art collection involving the processing of the porous semiconductor region of the substrate.

961 ION BEAM SOURCE AND GENERATION
Art collection involving use of an ion source with the generation of ions therefrom.

962 QUANTUM DOTS AND LINES
Art collection involving the construction of a one- or two-dimensional quantum well structure.

963 REMOVING PROCESS RESIDUES FROM VERTICAL SUBSTRATE SURFACES
Art collection involving the removal of unwanted process residues from vertical surfaces of the substrate.

964 ROUGHENED SURFACE
Art collection involving the use of a nonsmooth surface in semiconductor manufacture.

965 SHAPED JUNCTION FORMATION
Art collection involving the formation of a barrier layer junction of a nonstandard shape.

966 SELECTIVE OXIDATION OF ION-AMORPHOUSIZED LAYER
Art collection involving enhancing the oxidation of predetermined substrate regions by ion amorphousization of the regions.

967 SEMICONDUCTOR ON SPECIFIED INSULATOR
Art collection involving a semiconductor layer formed upon a specified insulative sublayer or substrate.

968 SEMICONDUCTOR-METAL-SEMICONDUCTOR
Art collection involving the construction of a semiconductor-metal-semiconductor configuration.

969 SIMULTANEOUS FORMATION OF MONOCRYSTALLINE AND POLYCRYSTALLINE REGIONS
Art collection involving the simultaneous formation of single crystalline and polycrystalline regions.

970 SPECIFIED ETCH STOP MATERIAL
Art collection involving the use of a specified material as an etch stop.

971 STOICHIOMETRIC CONTROL OF HOST SUBSTRATE COMPOSITION
Art collection involving the regulation of the proportions of elements combined in a base substrate composition.

972 STORED CHARGE ERASURE
Art collection involving the removal of accumulated electrical charges from the semiconductor substrate.

973 SUBSTRATE ORIENTATION
Art collection involving the use of a substrate of specified or nonstandard orientation.

974 SUBSTRATE SURFACE PREPARATION
Art collection involving treatment of the surface of a substrate prior to an operation being affected thereupon.

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975 SUBSTRATE OR MASK ALIGNING FEATURE
Art collection involving the lining up of a mask or regions to be formed with structural features (e.g., indicia, marks, etc.) of the substrate.

976 TEMPORARY PROTECTIVE LAYER
Art collection involving the temporary use of a protective layer.

977 THINNING OR REMOVAL OF SUBSTRATE
Art collection involving the reduction in thickness of a substrate or the removal of the entirety thereof.

978 FORMING TAPERED EDGES ON SUBSTRATE OR ADJACENT LAYERS
Art collection involving the formation of non-perpendicular edges on the semiconductor substrate or layers residing thereupon.

979 TUNNEL DIODES
Art collection involving the construction of a semiconductor diode having a forward negative resistance wherein conduction occurs through a potential barrier and in which the electrons pass in either direction between the conduction band in the n-type region and the valance band of the p-type region.

980 UTILIZING PROCESS EQUIVALENTS OR OPTIONS
Art collection involving the substitution of an operation that will perform the same or similar function of the operation it replaces.

981 UTILIZING VARYING DIELECTRIC THICKNESS
Art collection involving the utilization of regions having dielectric layers of different thicknesses.

982 VARYING ORIENTATION OF DEVICES IN ARRAY
Art collection involving the construction of an array of devices of varying orientation with respect to one another.

983 ZENER DIODES
Art collection involving construction of a single PN junction, two terminal semiconductor diode reverse biased into breakdown caused by the field emission of charge carriers in the device"s depletion layer.

FOREIGN ART COLLECTIONS

The foreign patents/nonpatent literature from Class 156, subclasses 625.1 through 640.1, 642.1 through 657.1, 659.11, 661.11, and 662.1, and Class 437, subclasses 1 through 250 and Cross-Reference Art Collections 900 through 987, have been transferred directly to the foreign art collections below (art collections FOR 100 through FOR 498) which are intended only as a repository for foreign patents/nonpatent literature. See the Foreign Art Collections in the Class 438 schedule for specific correspondences. [Note: The titles and definitions for *indented* art collections include all the details of the one(s) that are hierarchically superior.] Please note, foreign art collections FOR 175 through FOR 184 and FOR 186 through FOR 201 correspond to unofficial subclasses formed by the examiners and as such do not have definitions associated with them.

FOR 100 Etching of semiconductor precursor, substrates, and devices used in an electrical function:
Foreign art collection for processes directed to contacting a solid semiconductive precursor, substrate, or device used in an electrical function, with a chemical reagent to remove only a portion or constituent part of the solid semiconductive precursor, substrate, or device.

FOR 101 Measuring, testing, or inspecting:
Foreign art collection for processes including the step of visually, chemically, or physically determining or measuring a variable condition or property of the substrate.

FOR 102 By electrical means or of electrical property:
Foreign art collection for processes where the measurement or test is performed electrically or determines an electrical property, e.g., resistance, etc.

FOR 103 Altering the etchability of a substrate by alloying, diffusing, or chemical reacting:
Foreign art collection for processes wherein the manner in which a substrate is effected by an etchant is altered by contacting the substrate prior to etching with a material which (a) forms an alloy with, (b) diffuses

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into, or (c) chemically reacts with the substrate.

FOR 104 With uniting of preforms (e.g., laminating, etc.):
Foreign art collection for processes including the step of adhesively uniting at least two self-sustaining preforms.

FOR 105 Prior to etching:
Foreign art collection for processes wherein a step of uniting of preforms is carried out prior to a step of etching.

FOR 106 Delamination subsequent to etching:
Foreign art collection for processes wherein a preform is detached from another preform by destruction of the bond therebetween subsequent to a step of etching.

FOR 107 With coating:
Foreign art collection for processes including the step of applying a layer in a fluent state which solidifies onto the substrate.

FOR 108 Differential etching:
Foreign art collection for processes wherein an etching material (a) contacts selected surface areas of the substrate to remove a constituent part of the substrate at the selected surface areas only, or (b) treats the substrate at different rates in different areas to produce a nonuniform surface.

FOR 109 Metal layer etched:
Foreign art collection for processes wherein a layer of the substrate etched contains metal atoms in elemental form, e.g., alloys, etc.

FOR 110 With in situ activation or combining of etching components on surface:
Foreign art collection for processes directed to (a) applying a chemical substance which is inert to the substrate and thereafter treating the chemical substrate to produce a chemical reagent which functions to etch the substrate, or (b) simultaneously applying two or more substances none of which will alone etch the substrate but which interact with each other to produce a chemical reagent which etches the substrate.

FOR 111 With thin film of etchant between relatively moving substrate and conforming surface (e.g., chemical lapping, etc.):
Foreign art collection for processes in which the etching occurs at a thin film of etchant present between the substrate and another conforming surface, the substrate and conforming surface being in relative motion to one another during the etching.

FOR 112 With relative movement between the substrate and a confined pool of etchant:
Foreign art collection for processes including the step of causing a relative motion between a substrate being etched and an etchant which is confined by a container and wherein the substrate being etched may serve as the container.

FOR 113 With removal of adhered reaction product from substrate:
Foreign art collection for processes directed to the formation of reaction products by reaction of the etching reagent with a constituent of the substrate and thereafter removing the reaction products from the substrate.

FOR 114 With substrate rotation, repeated dipping, or advanced movement:
Foreign art collection for processes wherein the substrate is (a) rotated with respect to the pool of etchant, (b) repeatedly dipped into and removed from a pool of etchant, or (c) moved through a pool of etchant.

FOR 115 Projection of etchant against a moving substrate or controlling the angle or pattern of projected etchant:
Foreign art collection for processes wherein an etchant is transported through space by mechanical force and (a) brought into contact with a substrate while the substrate is in motion, (b) the etchant is transported at a predetermined angle, or (c) the etchant is transported in a particular pattern.

FOR 116 Recycling or regenerating etchant:
Foreign art collection for processes which include the step of reconstituting or reusing an etchant or wherein, the etchant is removed from an etching bath and is returned to an etching bath for further use.

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FOR 117 With treatment by high energy radiation or plasma (e.g., ion beam, etc.):
Foreign art collection for processes wherein a substrate is subjected to bombardment by high energy radiation above that of the so-called ultraviolet range or is subjected to a plasma.

FOR 118 Forming or increasing the size of an aperture:
Foreign art collection for processes wherein an etchant is applied to a substrate in such a manner that (a) a relatively small passage or opening is formed completely through the substrate, or (b) a previously existing small passage or opening in an substrate is enlarged by the action of the etchant.

FOR 119 With mechanical deformation, severing, or abrading of a substrate:
Foreign art collection for processes wherein a substrate is subjected to a physical force of sufficient magnitude to cause permanent distortion thereof or removal of material therefrom.

FOR 120 Etchant is a gas:
Foreign art collection for processes wherein the etchant is in a state of molecular dispersion when it contacts the substrate.

FOR 121 Etching according to crystalline planes:
Foreign art collection for processes wherein the substrate is at least partially crystalline and the etchant selectively etches the crystals at different rates along different axes or planes of orientation.

FOR 122 Etching isolates or modifies a junction in a barrier layer:
Foreign art collection for processes wherein a substrate which includes a junction in a barrier layer is treated with an etchant which contacts and removes at least a portion of the junction or removes material to isolate or separate one junction from another.

FOR 123 Discrete junction isolated (e.g., mesa formation, etc.):
Foreign art collection for processes wherein a substrate containing a junction between contiguous layers of barrier layer material is etched in such a manner as to isolate multiple areas each containing a discrete junction.

FOR 124 Sequential application of etchant material:
Foreign art collection for processes wherein plural etching steps are carried out on the same substrate at different times.

FOR 125 Sequentially etching the same surface of a substrate:
Foreign art collection for processes wherein the plural etching steps are carried at the same location on the substrate at different times.

FOR 126 Each etching exposes surface of an adjacent layer:
Foreign art collection for processes wherein a layer or part of a substrate previously covered by a different layer or part of the substrate is exposed by each etching step.

FOR 127 Etched layer contains silicon (e.g., oxide, nitride, etc.):
Foreign art collection for processes wherein at least one layer etched contains atoms of silicon.

FOR 128 Differential etching of a substrate:
Foreign art collection for processes directed to (a) contacting only selected surface areas of the substrate with the etchant to remove a constituent part of the substrate at the selected surface areas only, or (b) cause the substrate to be treated at different rates in different areas to produce a nonuniform surface.

FOR 129 Composite substrate:
Foreign art collection for processes wherein a substrate which is plural-layered, multipart, or includes distinct areas made of diverse compositions, is subjected to an etchant which contacts more than one layer, part, or area of the substrate, and results in a differential etching of the substrate.

FOR 130 Substrate contains metallic element or compound:
Foreign art collection for processes wherein at least a portion of the composite includes a metal atom in elemental form or in chemical combination.

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FOR 131 Substrate contains silicon or silicon compound:
Foreign art collection for processes wherein at least a portion of the composite includes a silicon atom in elemental form or in chemical combination.

FOR 132 Resist coating:
Foreign art collection for processes wherein a coating is applied which has the sole function of protecting the substrate from the action of the etchant.

FOR 133 Plural resist coating:
Foreign art collection for processes wherein more than one coating, intended to protect at least a portion of the substrate from the action of an etchant, is applied.

FOR 134 Silicon, germanium, or gallium containing substrate:
Foreign art collection for processes wherein the substrate contains silicon, germanium, or gallium in elemental form or in chemical combination.

FOR 135 MAKING DEVICE HAVING ORGANIC SEMICONDUCTOR COMPONENT:
Foreign art collection for a process for making a semiconductor device having and organic material as at least one component.

FOR 136 MAKING DEVICE RESPONSIVE TO RADIATION:
Foreign art collection for a process for making a device which will react to being exposed to radiant energy to produce light, a signal, etc.

FOR 137 Radiation detectors, e.g., infrared, etc.:
Foreign art collection for a process for making a device which indicates the presence of radiation.

FOR 138 Composed of polycrystalline material:
Foreign art collection for a process wherein the device is made in the form of monolithic matter having plural crystals.

FOR 139 Having semiconductor compound:
Foreign art collection for a process wherein chemical compounds which are semiconductors are used, i.e., two different elements in stoichiometric proportions having an energy gap between conductor and valance bands (generally of the order of 1 ev), e.g., III-V, II-VI and substituted compositions thereof.

FOR 140 MAKING THYRISTOR, E.G., DIAC, TRIAC, ETC.:
Foreign art collection for a process for making a device having multiple stacked PN junctions.

FOR 141 INCLUDING CONTROL RESPONSIVE TO SENSED CONDITION:
Foreign art collection for a process including the step of regulating an operation as a result of a sensed (e.g., test, measurement, etc.) condition.

FOR 142 INCLUDING TESTING OR MEASURING:
Foreign art collection for a process having the step of measuring, or testing, a condition of the process or the device made thereby.

FOR 143 INCLUDING APPLICATION OF VIBRATORY FORCE:
Foreign art collection for a process including the step of applying periodic motion.

FOR 144 INCLUDING GETTERING:
Foreign art collection for a process having a step of treating a semiconductor substrate to reduce or remove deleterious (impurities) or micro defects therefrom by withdrawing the same e.g., into an adjacent layer, implanting internal localizing regions, or reacting the materials so as to produce volatile substances thereof, etc.

FOR 145 By ion implanting or irradiating:
Foreign art collection for subject matter wherein the substrate is exposed to ion beams or wave energy to create lattice defects which act as trapping sites or to enhance the movement of undesired impurities out of a given semiconductor area.

FOR 146 By layers which are coated, contacted, or diffused:
Foreign art collection for subject matter wherein the substrate is exposed to a specified material by (1) depositing a layer of the material on the substrate, (2) physically con-

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tacting the substrate with the material or (3) performing a diffusion operation to form a gettering layer in the substrate.

FOR 147 By vapor phase surface reaction:
Foreign art collection for subject matter in which the substrate is treated with a reactive gas mixture which preferentially forms volatile compounds with the undesired impurities.

FOR 148 THERMOMIGRATION:
Foreign art collection for subject matter wherein impurities are diffused in a substrate under a temperature gradient which causes impurities to diffuse toward the hotter end.

FOR 149 INCLUDING FORMING A SEMICONDUCTOR JUNCTION:
Foreign art collection for a process including the step of providing a region of transition between two types of material differing in impurity characteristics (e.g., p and n type) in a semiconductor.

FOR 150 Using energy beam to introduce dopant or modify dopant distribution:
Foreign art collection for a process wherein the substrate is subjected to specified energy beams which are the dopant carrier, dopant modifier, the source of energy for controlled drive-in of dopant or thermal treatment of the same.

FOR 151 Neutron, gamma ray or electron beam:
Foreign art collection for processes involving the use of beamed energy in the form of neutrons, gamma rays or electrons.

FOR 152 Ionized molecules:
Foreign art collection for processes involving the use of a beam constituted of ionized molecules possessing sufficient kinetic energy to penetrate a semiconductor substrate.

FOR 153 Coherent light beam:
Foreign art collection for a process involving use of coherent light in the range of ultraviolet (UV) to infrared in a pulsed or scanning mode to control defect density of dopant distribution in a doped semiconductor.

FOR 154 Ion beam implantation:
Foreign art collection for processes involving penetration of the surface of a semiconductor substrate with ion beams, i.e., charged negative or positive particles, functioning as a dopant carrier or dopant modifier possessing sufficient kinetic energy to form a junction region in the substrate, e.g., P+, P-, N+, N-, PN, NPN, etc., metal semiconductor junction exhibiting rectifying properties, etc.

FOR 155 Of semiconductor on insulating substrate:
Foreign art collection for a process wherein the substrate is composed of a material highly resistant to flow of current, e.g., sapphire, beryllium oxide, spinel, etc.

FOR 156 Of semiconductor compound:
Foreign art collection for processes wherein the substrate is a semiconductor composed of at least two different elements in a stoichiometric proportions having an energy gap between conduction and valence bands (generally of the order of 1 ev), e.g., III-V, II-VI and the substitute compositions thereof.

FOR 157 Light emitting diodes (LED):
Foreign art collection for a process wherein the semiconductor compound is made in the form of a PN junction which emits light when biased in the forward direction.

FOR 158 Providing nondopant ion including proton:
Foreign art collection for processes involving use of beam energy to introduce ions incapable of changing the conductivity type of the substrate, e.g., rare gas ions, halogen ions, group IV ions in Si/Ge, amorphosizing ions, i.e., oxygen/nitrogen ions, etc.

FOR 159 Providing auxiliary heating:
Foreign art collection for processes including the step of adding extra heat either from external source or in-situ generation.

FOR 160 Forming buried region:
Foreign art collection for processes including the step of producing ion implanted area

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which is not in contact with the surface of the device.

FOR 161 Including multiple implantations of same region:
Foreign art collection for processes including plural steps of implanting ions in the same area of the device.

FOR 162 Through insulating layer:
Foreign art collection for subject matter wherein the implantations pass through the same area which is an insulator.

FOR 163 Forming field effect transistor (FET) type devices:
Foreign art collection for subject matter for making field effect transistors type devices, e.g., IGFET, MOSFET, COMOS, etc.

FOR 164 Using same conductivity type dopant:
Foreign art collection for processes involving plural steps of implanting ions of the same conductivity type dopant either all P or N.

FOR 165 Forming bipolar transistor (NPN/PNP):
Foreign art collection for processes for making a region of an NPN/PNP transistor (e.g., base or emitter profiling).

FOR 166 Lateral bipolar transistor:
Foreign art collection for processes for forming a bipolar transistor of the lateral type.

FOR 167 Having dielectric isolation:
Foreign art collection for processes involving the incorporation of an insulating regions, e.g., air-gap, recessed oxide, etc., to separate adjacent areas.

FOR 168 Forming complementary MOS (metal oxide semiconductor):
Foreign art collection for processes for forming complementary metal oxide semiconductor device, e.g., forming source and drain regions in the implanted well-region, etc.

FOR 169 Using oblique beam:
Foreign art collection for processes involving implanting ions other than right angle with respect to plane of substrate.

FOR 170 Using shadow mask:
Foreign art collection for processes involving use of a mask positioned with respect to the energy beam and substrate in such a manner as to cast a shadow on the substrate.

FOR 171 Having projected range less than thickness of dielectrics on substrate:
Foreign art collection for processes include the step of limiting the projected range of the ion energy to be less than the combined thickness of the dielectric material on the substrate.

FOR 172 Into shaped or grooved semiconductor substrate:
Foreign art collection for processes for implanting ions in a channel of the semiconductor substrate.

FOR 173 Involving Schottky contact formation:
Foreign art collection for processes for forming a metal semiconductor junction which exhibits current rectifying characteristics, known as Schottky barrier effect wherein the current is mainly due to majority carriers rather than PN junction.

FOR 174 Forming pair of device regions separated by gate structure, i.e., FET:
Foreign art collection for processes for forming two regions, e.g., source and regions, etc. on a device separated by a gate composed of thin insulator and an electron (gate) layer formed thereon in such a manner that conductance between the device regions (channel regions) is modulated by varying the gate voltage, i.e., FET.

FOR 185 Self-aligned:
Foreign art collection for processes wherein a previously formed device feature is utilized in proper interrelationship (registration), with related device regions.

FOR 202 Gate structure constructed of diverse dielectrics:
Foreign art collection for processes wherein the gate structure is made from different dielectric materials.

FOR 203 Gate surrounded by dielectric layer, e.g., floating gate, etc.:

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Foreign art collection for processes wherein the gate structure is submerged in dielectric material.

FOR 204 Adjusting channel dimension:
Foreign art collection for processes involving controlling the geometric configuration of the conductivity profile of the channel region.

FOR 205 Active step for controlling threshold voltage:
Foreign art collection for processes involving the step of regulating the threshold voltage of the device.

FOR 206 Into polycrystalline or polyamorphous regions:
Foreign art collection for processes involving implanting ions into a polycrystalline or polyamorphous, i.e., noncrystalline substrate.

FOR 207 Integrating active with passive device:
Foreign art collection for processes for combing active device e.g, FET, Transistor, etc. with passive devices, e.g., resistor, capacitor, etc.

FOR 208 Forming plural active devices in grid/array, e.g., RAMS/ROMS, etc.:
Foreign art collection for processes for making multiple active devices, e.g., FETs, transistors, diodes, etc., arranged in grids/arrays, e.g., memory cells, etc.

FOR 209 Having multiple-level electrodes:
Foreign art collection for processes forming plural electrodes at various levels of the device.

FOR 210 Forming electrodes in laterally spaced relationships:
Foreign art collection for processes for forming electrodes spaced laterally one from the other.

FOR 211 Making assemblies of plural individual devices having community feature, e.g., integrated circuit, electrical connection, etc.:
Foreign art collection for processes for putting together multiple single devices having something in common, e.g., mounted in an integrated circuit, electrical interconnections, etc.

FOR 212 Memory devices:
Foreign art collection for processes wherein the devices produced are a means of storing information usually in a computer.

FOR 213 Charge coupled devices (CCD):
Foreign art collection for processes wherein the devices produced are charge coupled (CCD).

FOR 214 Diverse types:
Foreign art collection for processes wherein the devices produced are of different types.

FOR 215 Integrated injection logic (I2L) circuits:
Foreign art collection for processes wherein different types of integrated injection logic devices (I2L) are produced.

FOR 216 Plural field effect transistors (CMOS):
Foreign art collection for a process wherein different types of field effect transistors are produced.

FOR 217 Complimentary metal oxide having diverse conductivity source and drain regions: (437/57)
Foreign art collection for subject matter wherein complementary metal oxide semiconductor field effect transistors have source and drain regions of opposite conductivity.

FOR 218 Having like conductivity source and drain regions:
Foreign art collection for subject matter wherein the transistors have source and drain regions of the same conductivity.

FOR 219 Including field effect transistor:
Foreign art collection for processes wherein the diverse type devices produced is a field effect transistor.

FOR 220 Including passive device:
Foreign art collection for processes wherein one of the diverse type devices produced is a passive field effect transistor.

FOR 221 Including isolation step:
Foreign art collection for processes for separating devices or regions by providing

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means whereby electron flow will not be possible between such devices or regions, e.g., dielectric area, air-gap, intrinsic zone by counter doping, reversed biased PN junction or combinations thereof.

FOR 222 By forming total dielectric isolation:
Foreign art collection for processes for forming complete insulation of current flow surrounding the active regions, e.g., bathtub, waffle-wafer isolation, etc.

FOR 223 By forming vertical isolation combining dielectric and PN junction:
Foreign art collection for processes wherein an upright isolation is formed by joining an insulative area with a PN junction.

FOR 224 Using vertical dielectric (air-gap/insulator) and horizontal PN junction:
Foreign art collection for processes wherein isolation is performed by combining an upright insulator with a horizontal PN junction.

FOR 225 Grooved air gap only:
Foreign art collection for processes wherein the dielectric produced is a furrowed opening to air only.

FOR 226 V-groove:
Foreign art collection for processes wherein the geometry of the groove is V-shaped.

FOR 227 Grooved and refilled with insulator:
Foreign art collection for processes wherein the isolation is performed by a step of furrowing followed by refilling the furrow with a nonconductor.

FOR 228 V-groove:
Foreign art collection for processes wherein the groove has a V-shaped geometry.

FOR 229 Recessed oxide by localized oxidation:
Foreign art collection for processes for forming the recessed oxide by use of localized oxidation, e.g., using a mask, etc.

FOR 230 Preliminary formation of guard ring:
Foreign art collection for processes for forming a guard ring to prevent surface inversion beneath the recessed oxide.

FOR 231 Preliminary anodizing:
Foreign art collection for processes including a step electrochemical action preceding the formation of the recessed oxide.

FOR 232 Preliminary etching of groove:
Foreign art collection for processes including step of etching a farrow before forming the recessed oxide.

FOR 233 Using overhanging oxidation mask and pretreatment of recessed walls:
Foreign art collection for processes wherein the etching step produces an overhanging oxidation mask with a pretreatment of the recessed walls.

FOR 234 Isolation by PN junction only:
Foreign art collection for processes wherein only PN junction formation isolates the device regions.

FOR 235 By diffusion from upper surface only:
Foreign art collection for processes for forming the Pn junction by diffusion from only the topmost surface of the device.

FOR 236 By up-diffusion from substrate region and down diffusion into upper surface layer:
Foreign art collection for processes for forming the isolation by upward diffusion from the substrate into the upper region and downward diffusion from the upper region into the substrate.

FOR 237 Substrate and epitaxial region of same conductivity type, i.e., P or N:
Foreign art collection for processes wherein the substrate and the active epitaxial region are both either P or N type.

FOR 238 By etching and refilling with semiconductor material having diverse conductivity:
Foreign art collection for processes for forming the isolation by etching and filling the etched region with a semiconductor material of the opposite type conductivity of the material etched.

FOR 239 Using polycrystalline region:
Foreign art collection for processes wherein polycrystalline areas form isolation regions.

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FOR 240 Shadow masking:
Foreign art collection for processes involving the use of a mask positioned with respect to the radiation and the substrate in such a manner as to cast a shadow.

FOR 241 Doping during fluid growth of semiconductor material on substrate:
Foreign art collection for processes for growing a layer of semiconductor material from a liquid or gaseous medium and at the same time adding an impurity (p- or n-type).

FOR 242 Including heat to anneal:
Foreign art collection for processes providing a increased temperature modification to anneal.

FOR 243 Growing single crystal on amorphous substrate:
Foreign art collection for processes for growing only one crystalline material on a solid substance which does not crystalline and is without definite geometrical shape, i.e., amorphous.

FOR 244 Growing single crystal on single crystal insulator (SOS):
Foreign art collection for processes for growing only one crystalline material on only one other crystalline material, the latter being a poor electrical conductor.

FOR 245 Including purifying stage during growth:
Foreign art collection for processes wherein provision(s) is made to render the material more pure.

FOR 246 Using transitory substrate:
Foreign art collection for processes wherein the base material exist only temporarily.

FOR 247 Using inert atmosphere:
Foreign art collection for processes wherein a nonreactive gaseous medium is used.

FOR 248 Using catalyst to alter growth process:
Foreign art collection for processes wherein a reaction modifying material is used to change the growth rate.

FOR 249 Growth through opening:
Foreign art collection for processes wherein the crystal growth occurs in an open space in or on the device.

FOR 250 Forming recess in substrate and refilling:
Foreign art collection for processes for making a depression in the base material and placing a filling material in the same.

FOR 251 By liquid phase epitaxy:
Foreign art collection for processes for growing the same type crystal from a liquid.

FOR 252 By liquid phase epitaxy:
Foreign art collection for processes for growing the same type crystal from a liquid.

FOR 253 Specified crystal orientation other than (100) or (111) planes:
Foreign art collection for processes involving orienting crystals in a named plane other than (100) or (111) planes.

FOR 254 Introducing minority carrier life time reducing dopant during growth, i.e., deep level dopant Au (Gold), Cr (Chromium), Fe (Iron), Ni (Nickel), etc.:
Foreign art collection for processes involving the introduction of a less predominant dopant carrier functioning as a reducing dopant during the growth process, i.e., Au (Gold), Cr (Chromium), Fe (Iron), Ni (Nickel), etc.

FOR 255 Autodoping control:
Foreign art collection for processes involving the regulation of self-induced impurity production in a semiconductor material.

FOR 256 Compound formed from Group III and Group V elements:
Foreign art collection for processes wherein the material which forms the semiconductor is composed of elements from Group III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc. and Group V, N (Nitrogen), P (Phosphorus), As (Arsenic), Sb (Antimony), Si (Bismuth), etc.

FOR 257 Forming buried regions with outdiffusion control:
Foreign art collection for processes for making subsurface areas while regulating the diffusion from within towards the outside.

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FOR 258 Plural dopants simultaneously outdiffusioned:
Foreign art collection for processes for diffusing from within towards the outside multiple impurities at the same time.

FOR 259 Growing mono and polycrystalline regions simultaneously:
Foreign art collection for processes for growing at the same time materials wherein (1) crystallographic orientation of all the basic groups of atoms are the same and (2) monolithic matter containing plural crystals.

FOR 260 Growing silicon carbide (SiC):
Foreign art collection for processes for growing silicon carbide (SiC).

FOR 261 Growing amorphous semiconductor material:
Foreign art collection for processes for growing semiconductor material which is a solid substance that does not crystalline and is without definite geometric shape, i.e., amorphous.

FOR 262 Source and substrate in close-space relationship:
Foreign art collection for processes wherein the dopant material and the base material in a near touching relationship.

FOR 263 Group IV elements:
Foreign art collection for processes involving use of Group IV elements, e.g., C (Carbon), Si (Silicon), Ge (Germanium), Sn (Tin), Pb (Lead), etc.

FOR 264 Compound formed from Group III and Group V elements:
Foreign art collection for processes involving use of a compound made from elements of Groups III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc. and Group V, O (Oxygen), S (sulfur), Se (Selenium), Te (Tellurium), etc.

FOR 265 Vacuum growing using molecular beam, i.e., vacuum deposition:
Foreign art collection for processes for growing crystals under a vacuum using a molecular beam. This is sometimes known as molecular beam epitaxy (MBE).

FOR 266 Group IV elements:
Foreign art collection for processes involving Group IV elements, C (Carbon), Si (Silicon), Ge (Germanium), Sn (Tin), Pb (Lead), etc.

FOR 267 Compound formed from Group III and Group V elements:
Foreign art collection for processes wherein the material which forms the semiconductor is composed of elements from Group III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc. and Group V, N (Nitrogen), P (Phosphorus), As (Arsenic), Sb (Antimony), Be (Bismuth), etc.

FOR 268 Growing single layer in multi-steps:
Foreign art collection for processes for growing a layer of material in plural operations (steps).

FOR 269 Polycrystalline layers:
Foreign art collection for processes for growing plural layers having monolithic matter containing multiple crystals.

FOR 270 Using modulated dopants or materials, e.g., superlattice, etc.:
Foreign art collection for processes using modified materials or dopants, e.g., superlattice.

FOR 271 Using preliminary or intermediate metal layer:
Foreign art collection for processes wherein a first or mid-layer of metal material is provided.

FOR 272 Growing by varying rates:
Foreign art collection for processes for growing a layer of material at a nonuniform rate.

FOR 273 Using electric current, e.g., Peltier effect, glow discharge etc.:
Foreign art collection for processes involving use of electric current.

FOR 274 Using seed in liquid phase:
Foreign art collection for processes for using a solid starting material (seed) to grow a single crystal material from a liquid source.

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FOR 275 Pulling from melt:
Foreign art collection for processes wherein the seed is used to start formation of material from molten matter and is pulled therefrom.

FOR 276 And diffusing:
Foreign art collection for processes consisting of permeating an impurity into the semiconductor.

FOR 277 Liquid and vapor phase epitaxy in sequence:
Foreign art collection for processes wherein the material is formed either from a liquid or vapor sequentially.

FOR 278 Involving capillary action:
Foreign art collection for processes involving elevation or depression of the surface of a liquid in a fine tube, etc., due to surface tension and the forces of cohesion and adhesion.

FOR 279 Sliding liquid phase epitaxy:
Foreign art collection for processes wherein the material is deposited by a pool of material moving along and in continuous contact with a substrate.

FOR 280 Modifying melt composition:
Foreign art collection for processes wherein the composition of the melt is changed during the process.

FOR 281 Controlling volume or thickness of growth:
Foreign art collection for processes having the step of regulating the volume of the material deposited or the thickness of the deposited layer.

FOR 282 Preliminary dissolving substrate surface:
Foreign art collection for processes wherein the substrate surface is at least partially dissolved before the material is grown or deposited.

FOR 283 With nonlinear slide movement:
Foreign art collection for processes wherein the slide is operated in a manner other than linear.

FOR 284 One melt simultaneously contacting plural substrates:
Foreign art collection for processes wherein a single melt contacts multiple substrates at the same time.

FOR 285 Tipping liquid phase epitaxy:
Foreign art collection for processes wherein the formation of the material is made by a slanted or sloping position.

FOR 286 Heteroepitaxy:
Foreign art collection for processes for growing a single crystal material on a different single crystal material.

FOR 287 Multi-color light emitting diode (LED):
Foreign art collection for processes wherein a device is produced on a substrate capable of producing light in different wave lengths.

FOR 288 Graded composition:
Foreign art collection for processes wherein the composition of the material is gradually changed during the process.

FOR 289 Forming laser:
Foreign art collection for processes for making a laser.

FOR 290 By liquid phase epitaxy:
Foreign art collection for processes involving growth of a single crystal material from a liquid source.

FOR 291 Si(Silicon) on Ge(Germanium) or Ge(Germanium on Si(Silicon):
Foreign art collection for processes for depositing Si(Silicon on crystals on a Ge(Germanium) substrate or vice-versa.

FOR 292 Either Si(Silicon) or Ge(Germanium) layered with or on compound formed from Group III and Group V elements:
Foreign art collection for processes for growing either a Si(Silicon) or Ge(Germanium) layer with or on a compound formed from Group III B(Bron), Al(Aluminum), Ga(Gallium), In(Indium), etc. and Group V elements N(Nitrogen), P(Phosphorus), As(Arsenic), Sb(Antimony), Bi(Bismuth) etc.

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FOR 293 Compound formed from Group III and Group V elements on diverse Group III and Group V elements including substituted Group III and Group V compounds:
Foreign art collection for processes for growing a compound formed from Group III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc. and Group V, N (Nitrogen), S (Sulfur), Se (Selenium), Te (Tellurium), etc. elements on a compound composed of different Group III and Group V elements wherein the elements of the groups may be substituted.

FOR 294 By fusing dopant with substrate, e.g., alloying, etc.:
Foreign art collection for processes for incorporating an impurity into a semiconductor material by a melting operation.

FOR 295 Using flux:
Foreign art collection for processes including the step of using a material to promote the fusion of the materials.

FOR 296 Passing electric current through material:
Foreign art collection for processes wherein an electric current is applied to and through the material.

FOR 297 With application of pressure to material during fusion:
Foreign art collection for processes wherein pressure is applied during the fusion operation.

FOR 298 Including plural controlled heating or cooling steps:
Foreign art collection for processes including regulated multiple cooling or heating operations.

FOR 299 Including diffusion after fusing step:
Foreign art collection for processes including doping by diffusing after the fusing operation.

FOR 300 Including additional material to improve wettability or flow characteristics:
Foreign art collection for processes including the incorporation of a nonreactive agent to alter the melting and crystallization of the alloying substance.

FOR 301 Diffusing a dopant:
Foreign art collection for processes for permeating an impurity into the semiconductor.

FOR 302 To control carrier lifetime, i.e., deep level dopant Au(Gold), Cr(Chromium), Fe(Iron), Ni(Nickel), etc.:
Foreign art collection for processes involving the introduction of a less predominant carrier, e.g., Au(Gold), Cr(Chromium), Fe(Iron), Ni(Nickel), etc.

FOR 303 Al(Aluminum) dopant:
Foreign art collection for processes wherein the impurity is Al(Aluminum).

FOR 304 Li(Lithium) dopant:
Foreign art collection for processes wherein the impurity is Li(Lithium).

FOR 305 Including nonuniform heating:
Foreign art collection for processes including heating distinct areas as opposed to heating the entire area.

FOR 306 To solid state solubility concentration:
Foreign art collection for processes wherein the dopant is introduced to the maximum concentration which can be obtained before alloying takes place, i.e., degenerately doped.

FOR 307 Using multiple layered mask:
Foreign art collection for processes involving use of a mask composed of plural layers.

FOR 308 Having plural predetermined openings in master mask:
Foreign art collection for processes wherein the mask contains multiple desired openings.

FOR 309 Forming partially overlapping regions:
Foreign art collection for processes for permeating an impurity in localized areas which lap over each other in part.

FOR 310 Plural dopants in same region, e.g., through same mask opening, etc.:

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Foreign art collection for processes for applying multiply impurities in the same area.

FOR 311 Simultaneously:
Foreign art collection for processes wherein the multiple impurities are applied at the same time.

FOR 312 Plural dopants simultaneously in plural regions:
Foreign art collection for processes for permeating multiple impurities in multiple localized areas.

FOR 313 Single dopant forming plural diverse regions:
Foreign art collection for processes for permeating an impurity into multiple different localized areas.

FOR 314 Forming regions of different concentrations or different depths:
Foreign art collection for a process wherein the regions formed differ in amount of impurity or the distance the impurity has to travel inwardly from the surface.

FOR 315 Using metal mask:
Foreign art collection for processes involving use of a mask made from metal.

FOR 316 Outwardly:
Foreign art collection for processes wherein the impurities moves from an internal location to an outward direction.

FOR 317 Laterally under mask:
Foreign art collection for processes wherein the diffusion is carried out on a slanted angle under the mask.

FOR 318 Edge diffusion by using edge portion of structure other than masking layer to mask:
Foreign art collection for processes using and edge portion of the device (other than masking layer) functioning as a mask.

FOR 319 From melt:
Foreign art collection for processes wherein the source of the impurity is molten material.

FOR 320 From solid dopant source in contact with substrate:
Foreign art collection for processes wherein the impurity is produced by a solid substance which is touching the semiconductor to be doped.

FOR 321 Using capping layer over dopant source to prevent outdiffusion of dopant:
Foreign art collection for processes using a layer of material to prevent the diffusion of the impurity (located within the device) outside of same.

FOR 322 Polycrystalline semiconductor source:
Foreign art collection for processes wherein the solid material is composed of multicrystals.

FOR 323 Organic source:
Foreign art collection for processes wherein the solid material is composed of other than inorganic matter.

FOR 324 Glassy source or doped oxide:
Foreign art collection for processes wherein the solid material is composed of a glass type material or an oxide which has been doped.

FOR 325 From vapor phase:
Foreign art collection for processes wherein the impurity is produced by a gaseous substance.

FOR 326 In plural stages:
Foreign art collection for processes carried out in multiple stages.

FOR 327 Zn (Zinc) dopant:
Foreign art collection for processes wherein the impurity is Zn (Zinc).

FOR 328 Solid source is operative relation with semiconductor material:
Foreign art collection for processes wherein the dopant source material is in close proximity with the semiconductor material.

FOR 329 In a capsule type enclosure:
Foreign art collection for processes carried out in a small container like apparatus.

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FOR 330 DIRECTLY APPLYING ELECTRICAL CURRENT:
Foreign art collection for processes including the step having an electric current come in contact with the semiconductor material.

FOR 331 And regulating temperature:
Foreign art collection for processes including the step of controlling the degree of hotness or coldness.

FOR 332 Alternating or pulsed current:
Foreign art collection for processes wherein the electric current reverses its direction periodically or is presented in periodic surges.

FOR 333 APPLYING CORPUSCULAR OR ELECTROMAGNETIC ENERGY:
Foreign art collection for processes including the step of applying energy in the form of electromagnetic radiation or corpuscular emissions, e.g., alpha, beta, cosmic, etc.

FOR 334 To anneal:
Foreign art collection for processes for heat treating the material to obtain a desired result.

FOR 335 FORMING SCHOTTKY CONTACT:
Foreign art collection for processes for making a simple metal-to-semiconductor interface that exhibits a nonlinear impedance.

FOR 336 On semiconductor compound:
Foreign art collection for processes wherein the contact is formed on a compound which is a semiconductor.

FOR 337 Multi-layer electrode:
Foreign art collection for processes wherein the contact is composed of plural layers.

FOR 338 Using Platinum Group silicide, i.e., silicide of Pt (Platinum), Pd (Palladium), Rh (Rhodium), Ru (Ruthenium), Ir (Iridium), Os (Osmium):
Foreign art collection for processes for forming a contact using the chemical combination of Si (Silicon) with one of the platinum group elements, e.g., Pt (Platinum), Pd (Palladium), Rh (Rhodium), Ru (Ruthenium), Ir (Iridium), Os (Osmium).

FOR 339 Using metal, i.e., Pt(Platinum, Pd(Palladium), Rh(Rhodium), Ru(Ruthenium), Ir(Iridium), Os(Osmium), Au(Gold), Ag(Silver):
Foreign art collection for processes for forming the contact using precious metal, i.e., Pt(Platinum), Pd(Palladium), Rh(Rhodium), Ru(Ruthenium), Ir(Iridium), Os(Osmium), Au(Gold), Ag(Silver).

FOR 340 MAKING OR ATTACHING ELECTRODE ON OR TO SEMICONDUCTOR, OR SECURING COMPLETED SEMICONDUCTOR TO MOUNTING OR HOUSING:
Foreign art collection for processes for forming or connecting an electrode on or to a semiconductor body. Also securing a finished semiconductor to a mount or housing structure.

FOR 341 Forming transparent electrode:
Foreign art collection for processes for making a contact that can be seen through.

FOR 342 Forming beam electrode:
Foreign art collection for processes for making a contact in the shape of a beam.

FOR 343 Forming bump electrode:
Foreign art collection for processes for making a contact in the shape of a bump.

FOR 344 Electrode formed on substrate composed of elements of Group III and Group V semiconductor compound:
Foreign art collection for processes wherein the contact is placed on a base material made from Group III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc., and Group V, N (Nitrogen), P (Phosphorus), As (Arsenic), Sb (Antimony), Bi (Bismuth), etc., elements in the form of compounds which function as semiconductors.

FOR 345 Electrode formed on substrate composed of elements of Group II and Group VI semiconductor compound:
Foreign art collection for processes wherein the contact is placed on a base material made from Group II, Zn (Zinc), Cd (Cadium), Hg (Mercury), etc. and Group VI, O (Oxygen), S (Sulfur), Se (Selenium), Te

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(Tellurium) in the form of compounds which function as semiconductors.

FOR 346 Single polycrystalline electrode layer on substrate:
Foreign art collection for processes wherein the contact is composed of single layer of multicrystalline material on a base material.

FOR 347 Single metal layer electrode on substrate:
Foreign art collection for processes wherein a single metal layer serves as a contact on a base material.

FOR 348 Subsequently fusing, e.g., alloying, sintering, etc.:
Foreign art collection for processes wherein the metal contact is after treated to combine the materials at point of contact, e.g, by melting, etc.

FOR 349 Forming plural layered electrode:
Foreign art collection for processes for making the electrode in multiply layers.

FOR 350 Including central layer acting as barrier between outer layers:
Foreign art collection for processes involving a device having a middle layer located between outer layers and functioning as a barrier between the outer layers.

FOR 351 Of polysilicon only:
Foreign art collection for processes wherein the contact is composed of multiple layers of polysilicon crystals only.

FOR 352 Including refractory metal layer of Ti (Titanium), Zr (Zirconium), Hf (Hafnium), V (Vanadium), Nb (Niobium), Ta (Tantalum), Cr (Chronium), Mo (Molybdenum), W (Tungsten):
Foreign art collection for processes wherein one of the layers is composed of a refractory metal Ti (Titanium), Zr (Zirconium), Hf (Hafnium), V (Vanadium), Nb (Niobium), Ta (Tantalum), Cr (Chronium), Mo (Molybdenum), W (Tungsten).

FOR 353 Including polycrystalline silicon layer:
Foreign art collection for processes wherein at least one layer is composed of polycrystalline silicon.

FOR 354 Including Al (Aluminum) layer:
Foreign art collection for processes wherein one layer is composed of Al (Aluminum).

FOR 355 Including layer separated by insulator:
Foreign art collection for processes wherein a nonconductive layer separates at least one other layer.

FOR 356 Forming electrode of alloy or electrode of a compound of Si (Silicon):
Foreign art collection for processes for making a contact from a mixture of metals or a chemical compound of Si (Silicon).

FOR 357 Al (Aluminium) alloy:
Foreign art collection for processes wherein the contact is composed of a mixture of metals one being Al (Aluminum).

FOR 358 Including Cu (Copper):
Foreign art collection for processes wherein the mixture of metals includes Cu (Copper).

FOR 359 Including Si (Silicon):
Foreign art collection for processes wherein the contact contains Si (Silicon).

FOR 360 Silicide of Ti(Titanium), Zr(Zirconium), Hf(Hafnium), V(Vanadium), Nb(Niobium), Ta(Tantalum), Cr(Chromium), Mo(Molybdenum), W(Tungsten),:
Foreign art collection for processes for forming contact using chemical combinations of Si(Silicon) and anyone of Ti(Titanium), Zr(Zirconium), Hf(Hafnium), V(Vanadium), Nb(Niobium), Ta(Tantalum), Cr(Chromium), Mo(Molybdenum), W(Tungsten).

FOR 361 Of platinum metal group Ru (Ruthenium), Rh (Rhodium), Pd (Palladium), Os (Osmium), Ir (Iridium), Pt (Platinum):
Foreign art collection for processes for forming the contact from a platinum metal group Ru (Ruthenium), Rh (Rhodium, Pd (Palladium), Os (Osmium), Ir (Iridium), Pt (Platinum).

FOR 362 By fusing metal with semiconductor (alloying):
Foreign art collection for processes wherein the contact is formed by heat treating the

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materials to cause them to combine at point of contact.

FOR 363 Depositing electrode in preformed recess in substrate:
Foreign art collection for processes for applying electrode material in a preformed recess in the base material.

FOR 364 Including positioning of point contact:
Foreign art collection for processes including the step of placing an electrode of small cross sectional or contacting area into touching relationship with a substantially larger area on part of the device.

FOR 365 Making plural devices:
Foreign art collection for processes for making multiple devices.

FOR 366 Using strip lead frame:
Foreign art collection for processes wherein the formed contacts are formed on a continuous length or strip of material.

FOR 367 And encapsulating:
Foreign art collection for processes for enclosing the device in a coating material.

FOR 368 Stacked array, e.g., rectifier:
Foreign art collection for processes wherein the plural devices are configured one on top of the other.

FOR 369 Securing completed semiconductor to mounting, housing or external lead:
Foreign art collection for processes for attaching an operable semiconductor to a support, e.g., mounting, housing or external lead.

FOR 370 Including contaminant removal:
Foreign art collection for processes having the step of removing undesirable material.

FOR 371 Utilizing potting or encapsulating material only to surround leads and device to maintain position, i.e., without housing:
Foreign art collection for processes wherein the leads are held in position on the device by only encapsulating material.

FOR 372 Including application of pressure:
Foreign art collection for processes wherein pressure is applied sometimes during the operation.

FOR 373 Glass material:
Foreign art collection for processes wherein the potting material is a glass.

FOR 374 Utilizing header (molding surface means):
Foreign art collection for processes subclass 209 wherein a shape imparting means is used.

FOR 375 Insulating housing:
Foreign art collection for processes including a nonconducting housing.

FOR 376 Including application of pressure:
Foreign art collection for processes including the use of pressure during some stage of the operation.

FOR 377 And lead frame:
Foreign art collection for processes including use of a conductive frame that holds leads of a plastic encapsulated package in place before encapsulation and is cut away after encapsulation.

FOR 378 Ceramic housing:
Foreign art collection for processes wherein the housing is made from a clay-like material, consisting primarily of magnesium and aluminum.

FOR 379 Including encapsulating:
Foreign art collection for processes wherein the housing is enclosed in a coating material.

FOR 380 Lead frame:
Foreign art collection for processes wherein the support usually is in the form of a strip having leads depending therefrom.

FOR 381 Metallic housing:
Foreign art collection for processes wherein the housing is composed of a material that has high electrical and thermal conductivity at normal temperatures.

FOR 382 Including application of pressure:

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Foreign art collection for processes including the application of pressure during some stage of the operation.

FOR 383 Including glass support base:
Foreign art collection for processes including the use of a support base made of glass.

FOR 384 Including encapsulating:
Foreign art collection for processes including placing a material on or around the housing to provide protection from the surrounding environment.

FOR 385 INCLUDING COATING OR MATERIAL REMOVAL, E.G., ETCHING, GRINDING, ETC.:
Foreign art collection for processes having the step of (1) covering or impregnating, or (2) wearing away of a portion of (as by acid, abrasion, etc.) a semiconductor.

FOR 386 Substrate dicing:
Foreign art collection for processes including the step cutting the substrate by any manner, e.g., sawing, etching, etc.

FOR 387 With a perfecting coating:
Foreign art collection for processes including the step of coating during the dicing which coating enhances the dicing.

FOR 388 Coating and etching:
Foreign art collection for processes having both the step of coating and etching regardless of the order of occurrence of the steps.

FOR 389 Of radiation resist layer:
Foreign art collection for processes including coating or etching, or both steps of a resist layer which is affected by electromagnetic radiation.

FOR 390 By immersion metal plating from solution, i.e., electroless plating:
Foreign art collection for processes wherein a metal coating is applied by immersion in a solution of a metallic compound without the use of electricity.

FOR 391 By spinning:
Foreign art collection for processes wherein the operation is carried out by a rotatory motion.

FOR 392 Elemental (Se) Selenium substrate or coating:
Foreign art collection for processes wherein the element selenium (Se) constitutes either the base or the coating.

FOR 393 Of polycrystalline semiconductor material on substrate:
Foreign art collection for processes wherein a multicrystalline semiconductor material e.g., Si, Ge, GaAs, etc., is coated on a base.

FOR 394 Semiconductor compound or mixed semiconductor material:
Foreign art collection for processes wherein the semiconductor material is a compound or mixture.

FOR 395 Of a dielectric or insulative material:
Foreign art collection for processes wherein the coating or etchant is applied to a nonconducting substrate.

FOR 396 Containing Group III atom:
Foreign art collection for processes wherein the nonconductor substrate contains a Group III, B (Boron), Al (Aluminum), Ga (Gallium), In (Indium), etc., atom.

FOR 397 By reacting with substrate:
Foreign art collection for processes wherein the coating or etchant reacts with substrate.

FOR 398 Monoxide or dioxide of Ge (Germanium) or Si (Silicon):
Foreign art collection for processes wherein the nonconductive substrate is composed of either germanium monoxide (GeO) or germanium dioxide (GeO1) or silicon monoxide (SiO) or silicon dioxide (SiO2).

FOR 399 By reacting with substrate:
Foreign art collection for processes wherein the coating or etchant reacts with the base.

FOR 400 Doped with impurities:
Foreign art collection for processes wherein impurities are added to the substrate.

FOR 401 Si (Silicon) and N (Nitrogen):
Foreign art collection for processes wherein the nonconductive substrate is composed of silicon (Si) and nitrogen (N).

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FOR 402 By chemical reaction with substrate:
Foreign art collection for processes wherein the coating or etchant chemically reacts with the base.

FOR 403 Directly on semiconductor substrate:
Foreign art collection for processes wherein the coating or etchant is applied to the non-conducting substrate which is located on a semiconductor substrate.

FOR 404 By chemical conversion of substrate:
Foreign art collection for processes wherein the coating or etchant chemically converts the base.

FOR 405 Comprising metal layer:
Foreign art collection for processes wherein the coating consists of a metal layer.

FOR 406 On metal:
Foreign art collection for processes wherein the substrate is metal.

FOR 407 TEMPERATURE TREATMENT MODIFYING PROPERTIES OF SEMICONDUCTOR, E.G., ANNEALING, SINTERING, ETC.:
Foreign art collection for processes for treating a semiconductor with other than ambient temperature to change some characteristic of the same.

FOR 408 Heating and cooling:
Foreign art collection for processes including the steps of either increasing the temperature above the ambient environment and then lowering the temperature or lowering the temperature below the ambient environment and then increasing the temperature.

FOR 409 INCLUDING SHAPING:
Foreign art collection for processes having the step of imparting an intentional shape of the semiconductor or part thereof.

FOR 410 MISCELLANEOUS:
Foreign art collection for processes not provided for above.

FOR 411 UTILIZING PROCESS EQUIVALENTS OR OPTIONS:
Foreign art collection involving the substitution of an operation that will perform the same or similar function of the operation it replaces.

FOR 412 MAKING PRESSURE SENSITIVE DEVICE:
Foreign art collection involving the construction of a device which is sensitive to pressure.

FOR 413 MAKING DEVICE HAVING HEAT SINK:
Foreign art collection involving the construction of a device having means to control heat in a determined area of the device.

FOR 414 MAKING THERMOPILE:
Foreign art collection involving the construction of a group of thermocouples connected in series used to measure radiant power of energy, also a source of electric energy.

FOR 415 MAKING DIODE:
Foreign art collection involving the construction of an electronic device having a cathode and an anode.

FOR 416 Light emitting diode:
Foreign art collection wherein the device constructed gives off light.

FOR 417 Mounting and contact:
Foreign art collection involving the details of the mountings and contacts of the device.

FOR 418 LASER PROCESSING OF FIELD EFFECT TRANSISTOR (FET):
Foreign art collection involving the use of a laser in the construction of a field effect transistor.

FOR 419 LASER PROCESSING OF TRANSISTOR:
Foreign art collection involving the use of a laser in the construction of a transistor.

FOR 420 MAKING TRANSISTOR ONLY):
Foreign art collection limited to the construction of a transistor, by relatively non-conventional techniques.

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FOR 421 MAKING JOSEPHSON JUNCTION DEVICE:
Foreign art collection involving the construction of a device having a Josephson junction.

FOR 422 MAKING JUNCTION-FIELD EFFECT TRANSISTOR (J-FET) OR STATIC INDUCTION TRANSISTOR (SIT) DEVICE:
Foreign art collection involving the construction of a junction-field effect transistor or static induction transistor (SIT).

FOR 423 MAKING METAL SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MESFET) DEVICE ONLY:
Foreign art collection limited to the construction of a metal semiconductor field effect transistor.

FOR 424 MAKING METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFET) DEVICE:
Foreign art collection involving the construction of a metal oxide semiconductor field effect transistor device by relatively nonconvention techniques.

FOR 425 MAKING NONEPITAXIAL DEVICE:
Foreign art collection involving the construction of a semiconductor device by a process other than by growth of crystalline material.

FOR 426 MAKING VERTICALLY STACKED DEVICES (3-DIMENSIONAL STRUCTURE):
Foreign art collection involving the construction of a 3-dimensional device which is vertically stacked.

FOR 427 MAKING PHOTOCATHODE OR VIDICON:
Foreign art collection involving the construction of a photocathode or vidicon tube.

FOR 428 MAKING LATERAL TRANSISTOR:
Foreign art collection involving the construction of a lateral transistor, i.e., the emitter, base, and collector being formed horizontally displaced from each other.

FOR 429 MAKING RESISTOR:
Foreign art collection involving the construction of a resistor, either individually or in combination with other device regions.

FOR 430 MAKING CAPACITOR:
Foreign art collection involving the construction of a capacitor, either individually or in combination with other device regions.

FOR 431 MAKING SILICON-OXIDE-NITRIDE-OXIDE OR SILICON (SONOS) DEVICE:
Foreign art collection involving the construction of a layered gate dielectric of oxide-nitride on a silicon substrate and with silicon as the gate material.

FOR 432 MAKING STRAIN GAGE:
Foreign art collection involving the construction of a strain measuring device.

FOR 433 MAKING FUSE OR FUSABLE DEVICE:
Foreign art collection involving the construction of a device containing a means switchable between a conducting and nonconducting condition.

FOR 434 WITH REPAIR OR RECOVERY OF DEVICE:
Foreign art collection involving renovating a device by repairing or recovering the same.

FOR 435 HAVING SUBSTRATE OR MASK ALIGNING FEATURE:
Foreign art collection involving novel lining up a base or mask with other structure features of the device.

FOR 436 SUBSTRATE SUPPORT OR CAPSULE CONSTRUCTION:
Foreign art collection involving novel construction of a support for a substrate or a capsule, per se.

FOR 437 CONTINUOUS PROCESSING:
Foreign art collection involving carrying out the process steps in a continual manner.

FOR 438 FORMING HOLLOW BODIES AND ENCLOSED CAVITIES:

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Foreign art collection involving use of hollow structures and cavities having material surrounding the same.

FOR 439 ENERGY BEAM TREATING RADIATION RESIST ON SEMICONDUCTOR:
Foreign art collection involving use of energy beam to irradiate a resist responsive thereto located on a semiconductor.

FOR 440 RADIATION ENHANCED DIFFUSION (R.E.D.):
Foreign art collection involving a diffusion process assisted by use of radiation.

FOR 441 ION BEAM SOURCE AND GENERATION:
Foreign art collection involving use of a source and generation of ion beams.

FOR 442 IMPLANTATION THROUGH MASK:
Foreign art collection involving the passage of particles (ions) or of energy through a protection masking material.

FOR 443 RECOIL IMPLANTATION:
Foreign art collection involving the use of energy for implanting whereby at least a portion of the energy travels in other than a straight path (bounces back and forth).

FOR 444 DUAL SPECIES IMPLANTING OF SEMICONDUCTOR:
Foreign art collection involving the use of two dopant sources during implantation so as to simultaneously implant both dopants.

FOR 445 DOPANT ACTIVATION PROCESS:
Foreign art collection involving steps taken to activate a dopant.

FOR 446 BEAM WRITING OF PATTERNS:
Foreign art collection involving use of beam energy to create patterns.

FOR 447 BEAM PROCESSING OF COMPOUND SEMICONDUCTOR DEVICE:
Foreign art collection involving use of beam energy to treat a device made from semiconductor compounds.

FOR 448 HYDROGEN PLASMA TREATMENT OF SEMICONDUCTOR DEVICE:
Foreign art collection involving use of hydrogen plasma to treat the semiconductor device.

FOR 449 MAKING RADIATION RESISTANT DEVICE:
Foreign art collection involving the construction of a device resistant to radiant energy.

FOR 450 DEFECT CONTROL OF SEMICONDUCTOR WAFER (PRETREATMENT):
Foreign art collection involving steps, involving pretreating ones, for the control of defects in a semiconductor wafer.

FOR 451 SELECTIVE OXIDATION OF ION AMORPHOUSIZED LAYERS:
Foreign art collection involving enhancing the oxidizability of predetermined regions by ion amorphousization of the regions.

FOR 452 CONTROLLING CHARGE STATE AT SEMICONDUCTOR-INSULATOR INTERFACE:
Foreign art collection involving adjusting the charge state where the semiconductor and insulator surfaces meet.

FOR 453 INCOHERENT LIGHT PROCESSING:
Foreign art collection involving use of multifrequency light.

FOR 454 THERMALLY ASSISTED BEAM PROCESSING:
Foreign art collection involving use of heat other than that provided by (or in addition to) a beam.

FOR 455 UTILIZING LIFT-OFF:
Foreign art collection involving use of the lift-off technique associated with coating operations.

FOR 456 STOICHIOMETRIC CONTROL OF HOST SUBSTRATE COMPOSITION:
Foreign art collection involving the regulation of the proportions of elements combined in a base substrate composition.

FOR 457 SUBSTRATE SURFACE PREPARATION:

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Foreign art collection involving steps for treating the surface of a substrate prior to deposition of a layer or junction formation.

FOR 458 FORMING TAPERED EDGES ON SUBSTRATE OR ADJACENT LAYERS:
Foreign art collection involving the formation of slanted edges on either the substrate or layers on same or both.

FOR 459 MOVABLE MASK:
Foreign art collection involving use of a mask which can be moved and is not in contact with the substrate.

FOR 460 CONTROLLED ATMOSPHERE:
Foreign art collection involving use of a regulated gaseous environment, e.g., inert gases, specifically proportioned mixtures, etc.

FOR 461 SHALLOW DIFFUSION:
Foreign art collection involving formation of regions of very small depth in the surface of the substrate.

FOR 462 AMPHOTERIC DOPING:
Foreign art collection involving use of a dopant capable of functioning as a P or N type depending on process conditions.

FOR 463 CONTROLLING DIFFUSION PROFILE BY OXIDATION:
Foreign art collection involving the regulation of a diffusion contour by an oxidation step.

FOR 464 DIFFUSION OF OVERLAPPING REGIONS (COMPENSATION):
Foreign art collection involving diffusing at least partially one area over the other.

FOR 465 VERTICAL DIFFUSION THROUGH A LAYER:
Foreign art collection involving diffusion in a perpendicular manner through a layer of material.

FOR 466 NONSELECTIVE DIFFUSION:
Foreign art collection involving a random diffusion process, i.e., diffusion without a mask.

FOR 467 DISPLACING P-N JUNCTION:
Art collection involving physical relocation of the P-N junction from its originally formed position.

FOR 468 ELECTROMIGRATION:
Foreign art collection involving movement of atoms (usually dopant atoms) through a material under the influence of an electric field.

FOR 469 SHAPED JUNCTION FORMATION:
Foreign art collection involving the formation of a junction of a nonstandard configuration.

FOR 470 USING NONSTANDARD DOPANT:
Foreign art collection involving use of a material as a dopant which is not normally used as such.

FOR 471 WASHED EMITTER PROCESS:
Foreign art collection involving the cleaning of the surface of an emitter region by a nonstandard dip-etching or washing step.

FOR 472 EMITTER DIP PREVENTION (OR UTILIZATION):
Foreign art collection involving the utilization of special diffusion techniques to eliminate the undesirable tendency of the base-collector junction to “bulge” downwardly during the emitter diffusion.

FOR 473 UTILIZING SPECIAL MASKS (CARBON, ETC.):
Foreign art collection involving use of nonconventional masks.

FOR 474 LOCALIZED HEATING CONTROL DURING FLUID GROWTH:
Foreign art collection involving the regulation of heat in a desired area during gaseous or liquid deposition of material.

FOR 475 FLUID GROWTH INVOLVING VAPOR-LIQUID-SOLID STAGES:
Foreign art collection involving deposition of material from a vapor into a liquid solvent then precipitating the material from solution onto a substrate.

FOR 476 FLUID GROWTH OF COMPOUNDS OF GROUPS II, IV, OR VI ELEMENTS:

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Foreign art collection involving the liquid of vapor deposition of compounds formed from Group II, IV, or VI elements.

FOR 477 FORMING THIN SHEETS:
Foreign art collection involving the construction of thin sheets or free standing layers.

FOR 478 PRODUCING POLYCRYSTALLINE SEMICONDUCTOR MATERIAL:
Foreign art collection involving the formation of nonsingular crystalline semiconductor material.

FOR 479 SELECTIVE OXIDATION OF POLYCRYSTALLINE LAYER:
Foreign art collection involving controlled oxidation of a polycrystalline layer.

FOR 480 FORMING GRADED ENERGY GAP LAYERS:
Foreign art collection involving sequential formation of layers of composition or dopant concentration which vary in a uniform manner.

FOR 481 DIFFERENTIAL CRYSTAL GROWTH:
Foreign art collection involving use of growth conditions so as to produce (anisotropic) nonuniform growth.

FOR 482 FLUID GROWTH DOPING CONTROL:
Foreign art collection involving regulation of the doping process during fluid deposition.

FOR 483 UTILIZING MELT BACK:
Foreign art collection involving liquid phase epitaxial deposition wherein a thin surface layer of the substrate is dissolved prior to the start of the deposition process.

FOR 484 SOLID PHASE EPITAXIAL GROWTH:
Foreign art collection involving the deposition of material from solid to solid, e.g., migration of silicon through an aluminum layer on a silicon substrate.

FOR 485 THINNING OR REMOVAL OF SUBSTRATE:
Foreign art collection involving the selective removal of a portion of all of the base material.

FOR 486 DIFFUSION ALONG GRAIN BOUNDARIES:
Foreign art collection involving diffusion of material between the grains of nonsingle crystal material or along the physical junction of two layers.

FOR 487 CONTROLLING LATTICE STRAIN:
Foreign art collection involving regulating of strain in the lattice.

FOR 488 UTILIZING ROUGHENED SURFACE:
Foreign art collection involving use of a nonsmooth surface.

FOR 489 UTILIZING MULTIPLE DIELECTRIC LAYERS:
Foreign art collection involving use of multi-nonconducting layers.

FOR 490 UTILIZING THICK-THIN OXIDE FORMATION:
Foreign art collection involving formation of plural oxide areas having different thicknesses.

FOR 491 FORMING POLYCRYSTALLINE SEMICONDUCTOR PASSIVATION:
Foreign art collection involving protecting the surface P-N junction with nonsingle crystalline semiconductor coatings.

FOR 492 PRODUCING TAPERED ETCHING:
Foreign art collection involving the use of an etchant to form an angled surface.

FOR 493 REFLOW OF INSULATOR:
Foreign art collection involving the melting or softening to the point of flowing insulator material.

FOR 494 OXIDATION OF GATE OR GATE CONTACT LAYER:
Foreign art collection involving self-aligned masking by oxidation of either the gate or the gate contact layer.

FOR 495 SELF-ALIGNING FEATURE:

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Foreign art collection involving usually automatic, relative alignment of parts, materials, etc.

FOR 496 DIFFERENTIAL OXIDATION AND ETCHING:
Foreign art collection involving preferential oxidation accompanied by etching.

FOR 497 DIFFUSING LATERALLY AND ETCHING:
Foreign art collection involving carrying out a diffusion step in a lateral direction and etching.

FOR 498 DIFFUSING DOPANTS IN COMPOUND SEMICONDUCTOR:
Foreign art collection involving special conditions for diffusing a dopant in chemical compounds which function as a semiconductor.

END

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